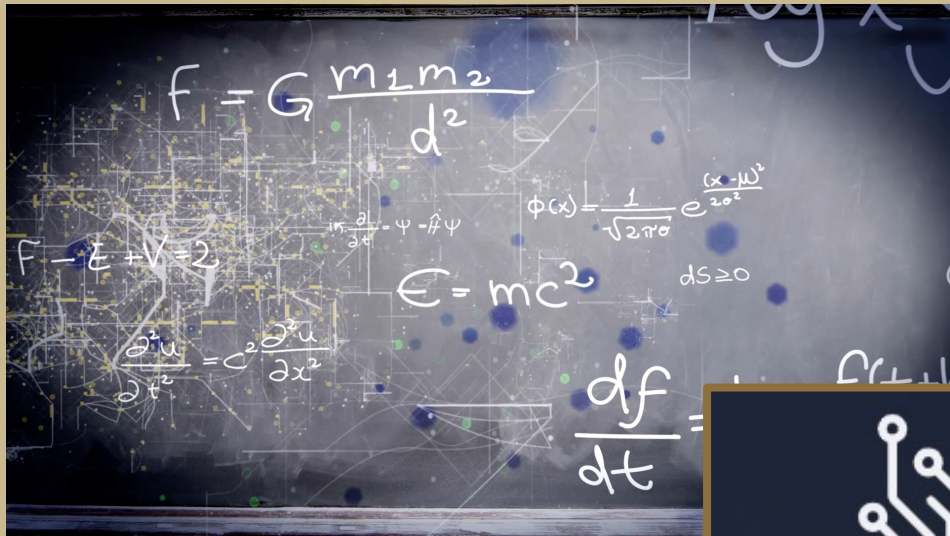


# Community Building: Global Translational Impact on Research and Education



**Gerhard Klimeck**

Director of nanoHUB

Deputy CIO for Academic IT

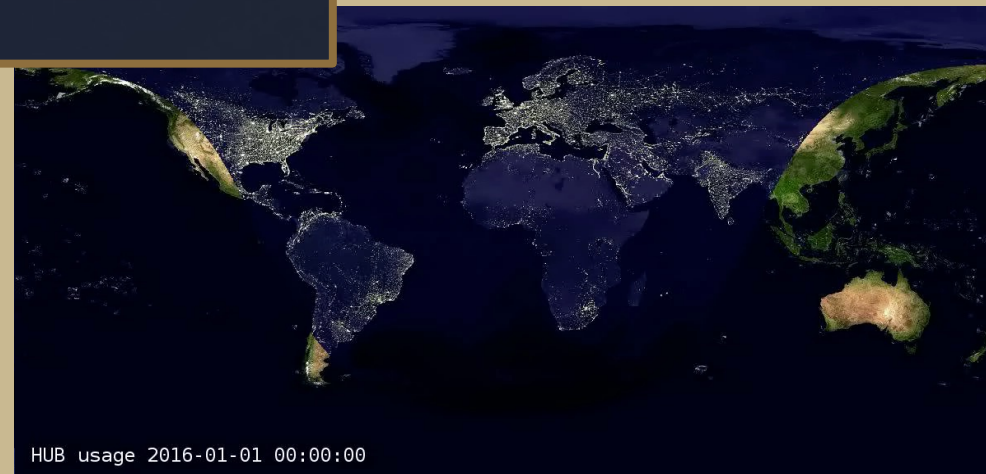
Fellow of APS, IOP, IEEE, AAAS

**Ale Strachan**

Co-Director of nanoHUB

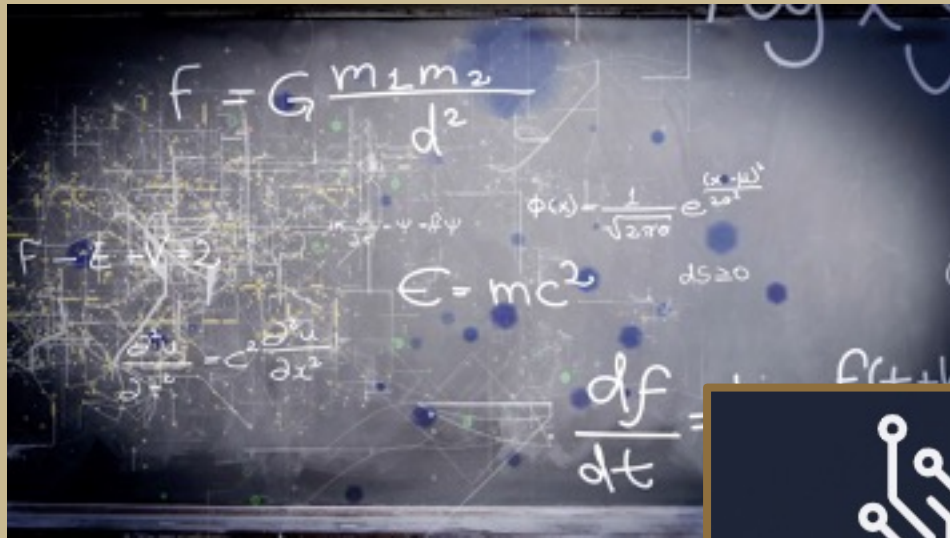
Reilly Prof. of Materials Engineering

20+ years of "cloud" service –  
Software as a Service



**From Theory to Immersive Learning to Design (to Fabs)**

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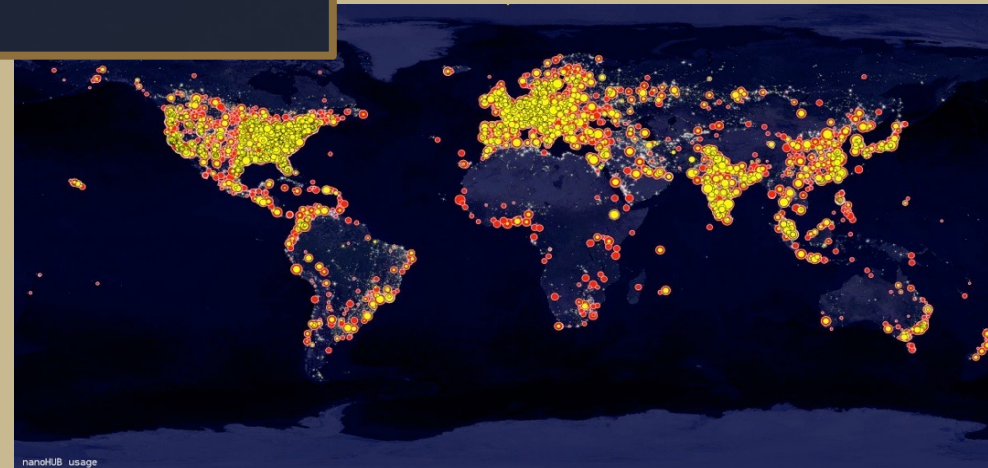
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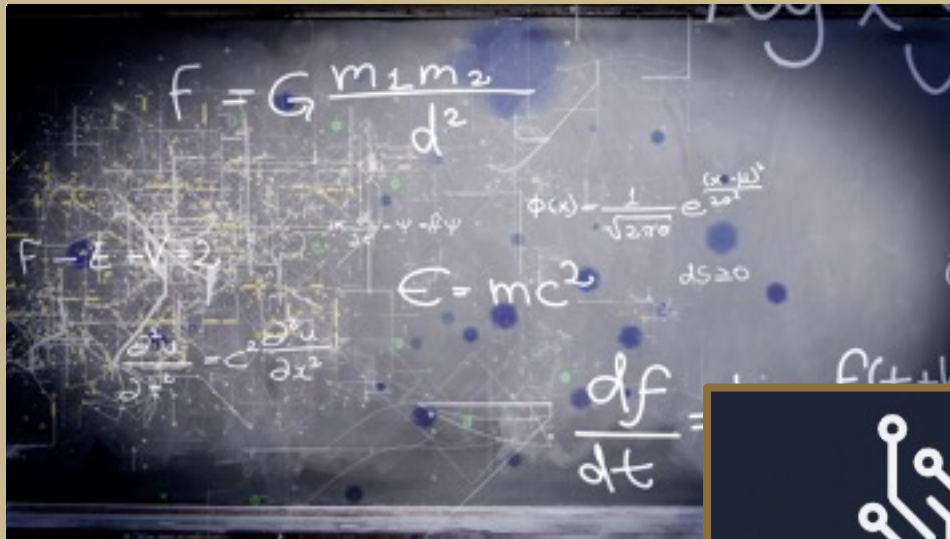
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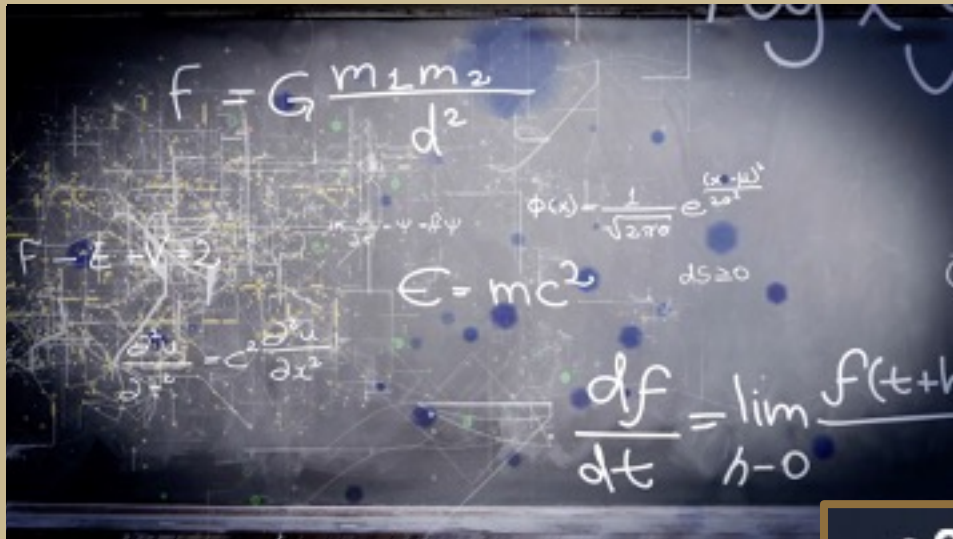
- ... empower faculty and students?
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a fundamental change in approach  
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Community Building!

Ease of Use!



**nanoHUB in a nutshell:**  
**170+ courses, 6500+ content items**  
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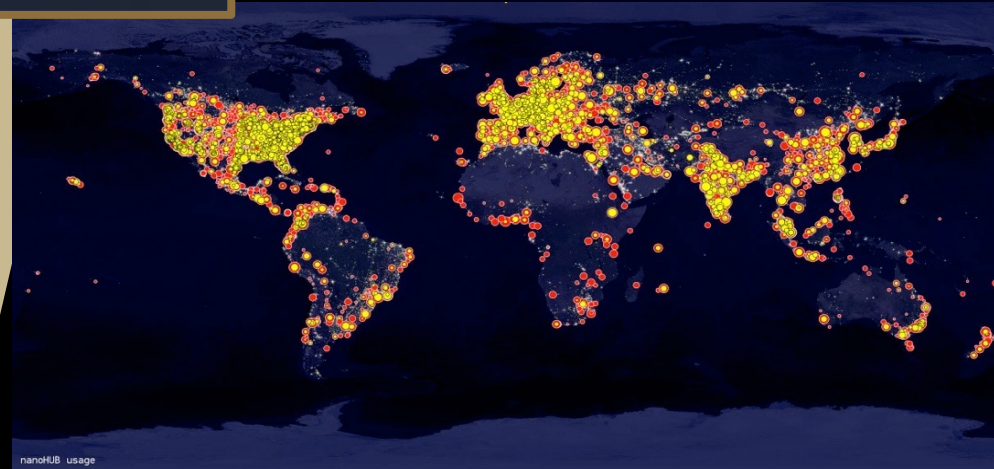
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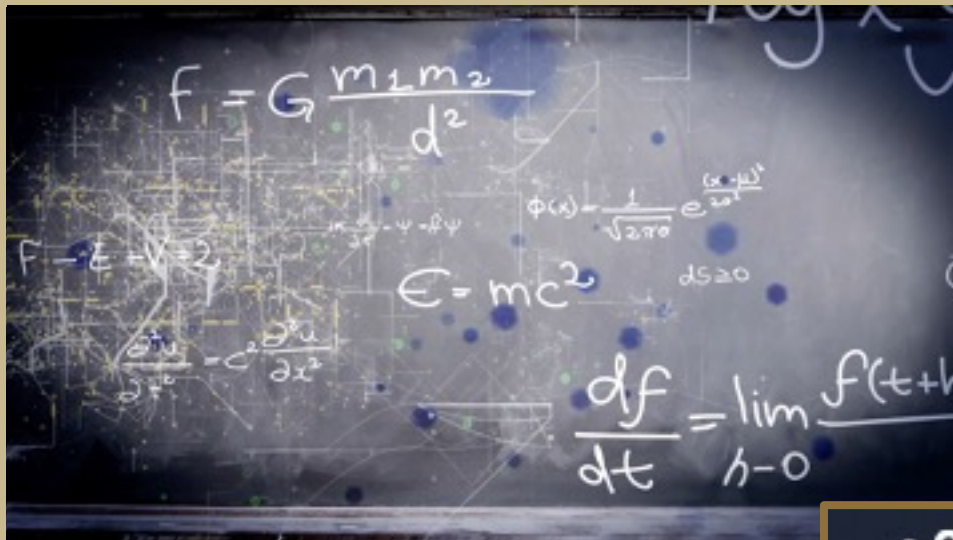
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"You have to write your own code  
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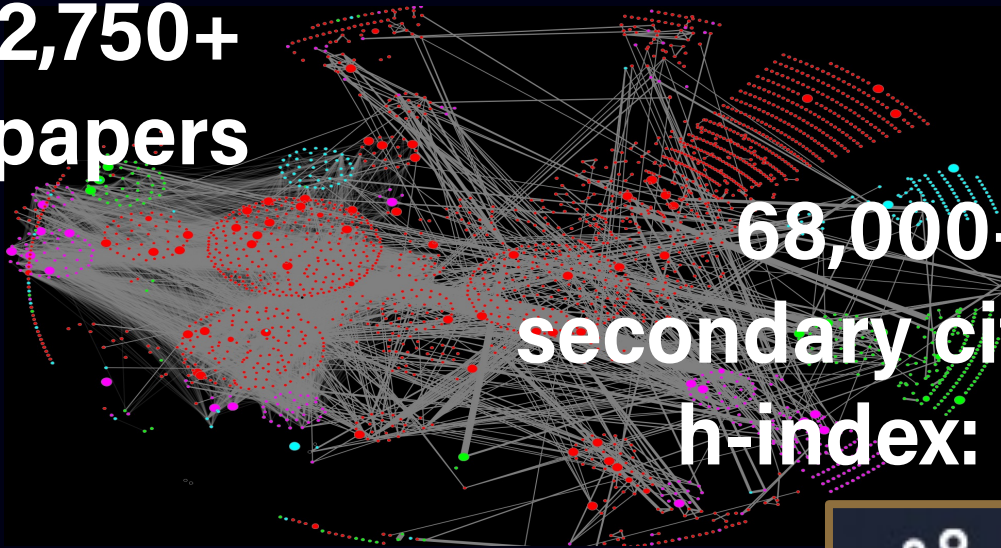
"No experimentalist  
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"You cannot provide all the  
computing that is needed!"

**Community Building!**

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**2,750+**  
**papers**



**68,000+**  
**secondary citations**  
**h-index: 121**

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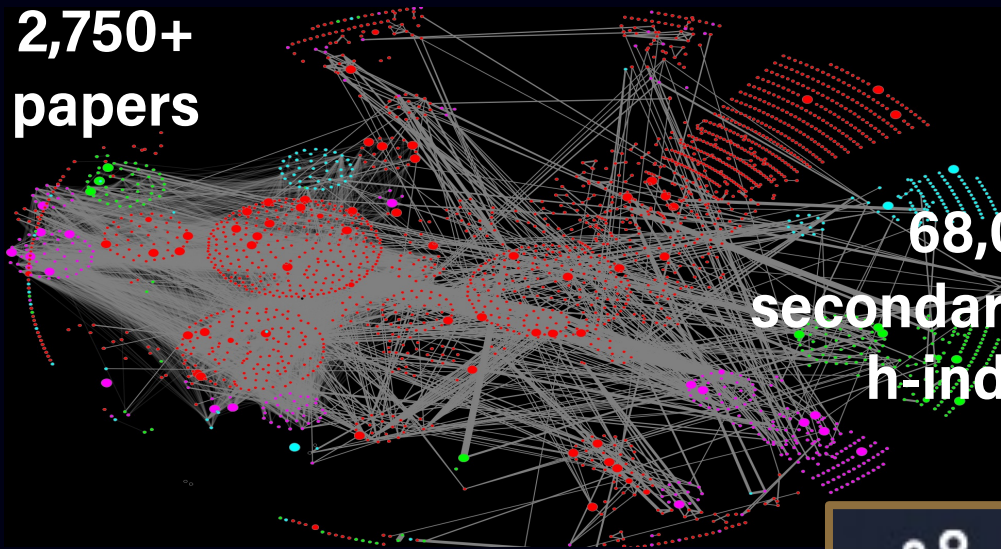
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**nanoHUB Questions:**  
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**450 papers w/ experimentalists**

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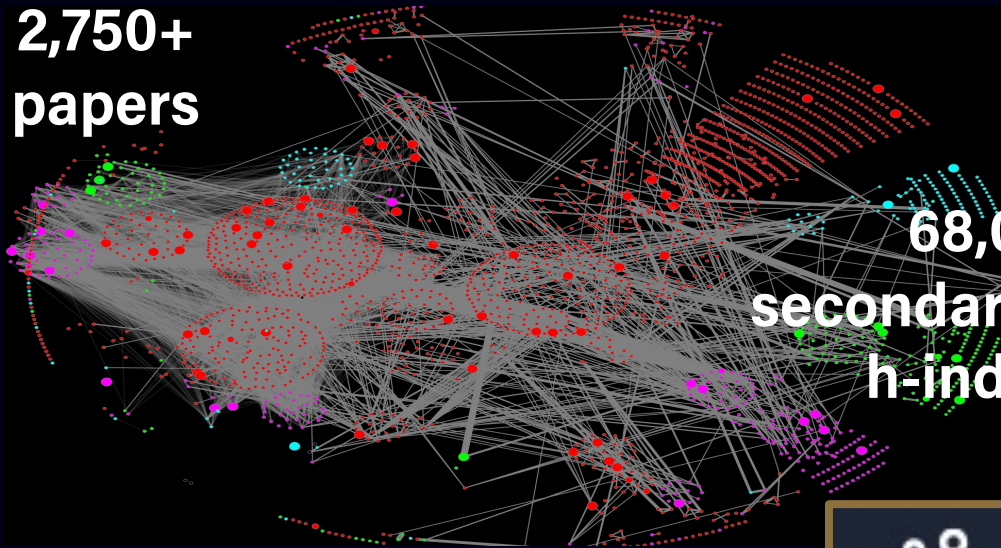
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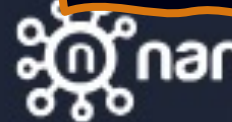
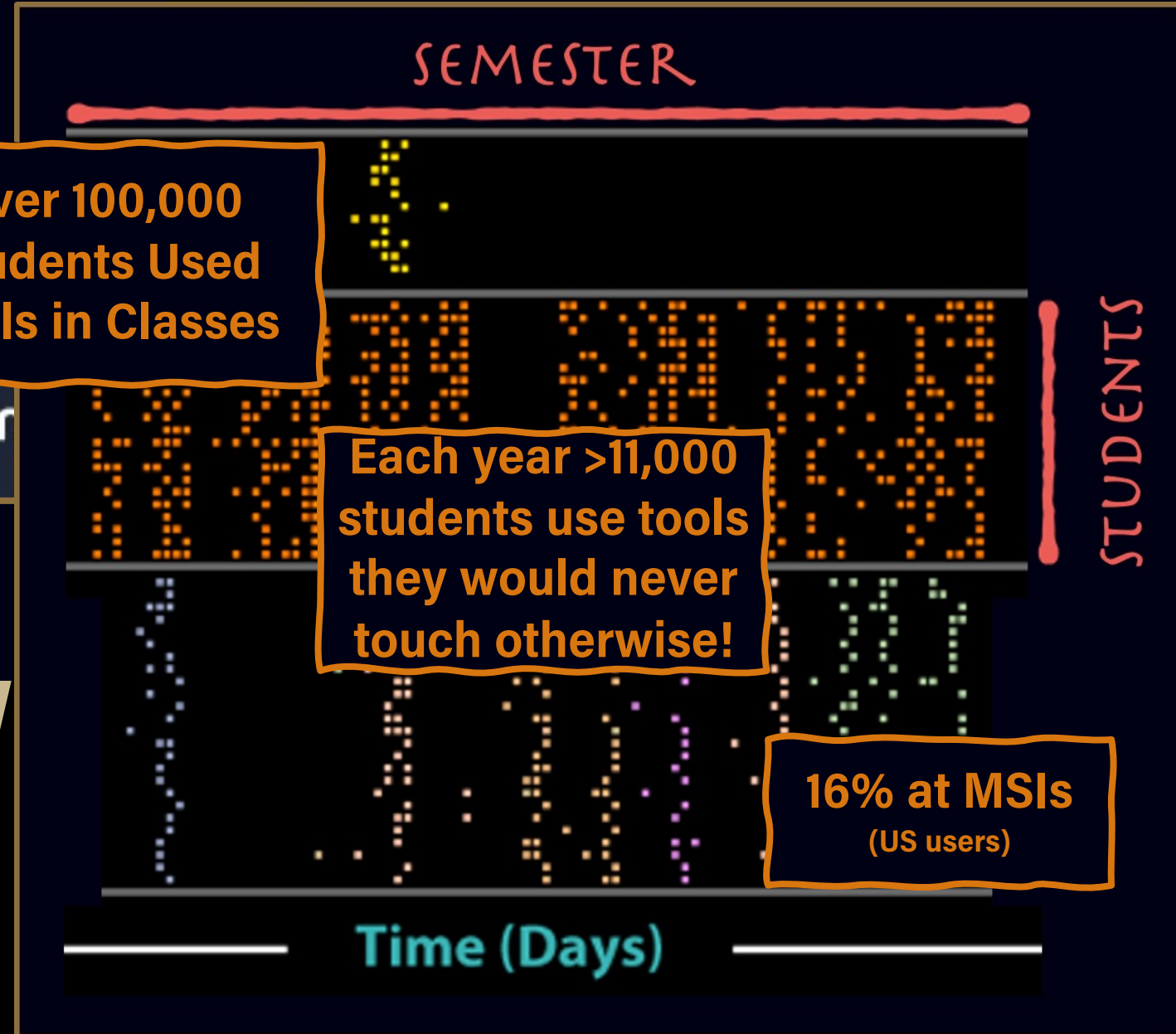
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Over 100,000 Students Used Tools in Classes

Each year >11,000 students use tools they would never touch otherwise!

16% at MSIs  
(US users)



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Research OR Education?  
You cannot be both!

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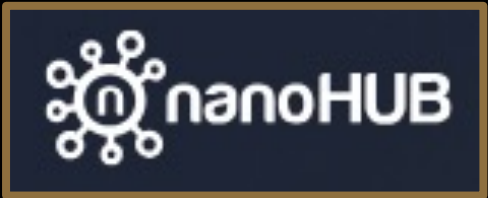
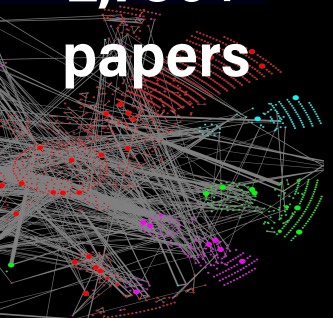
1 faculty => many students

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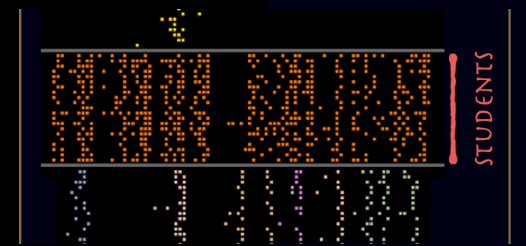
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## 24+ Years of Community Building!

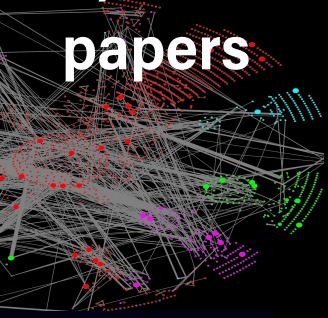
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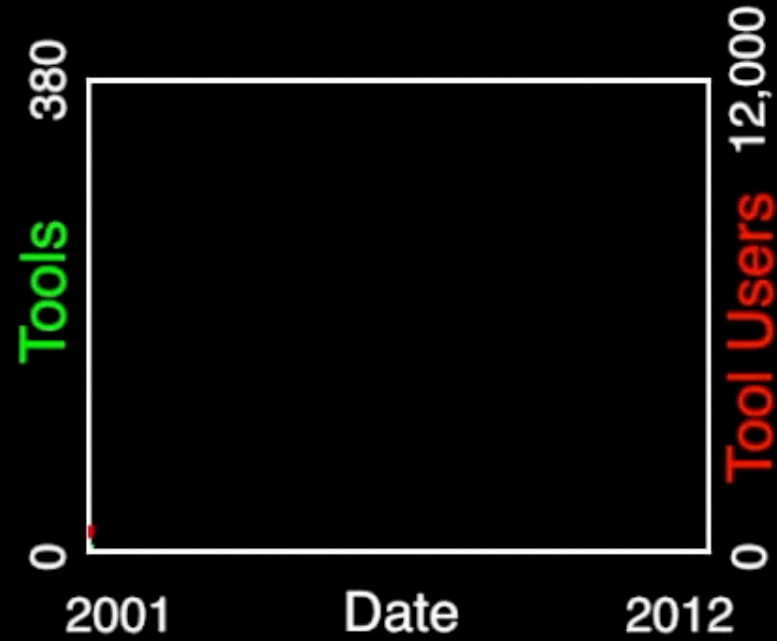
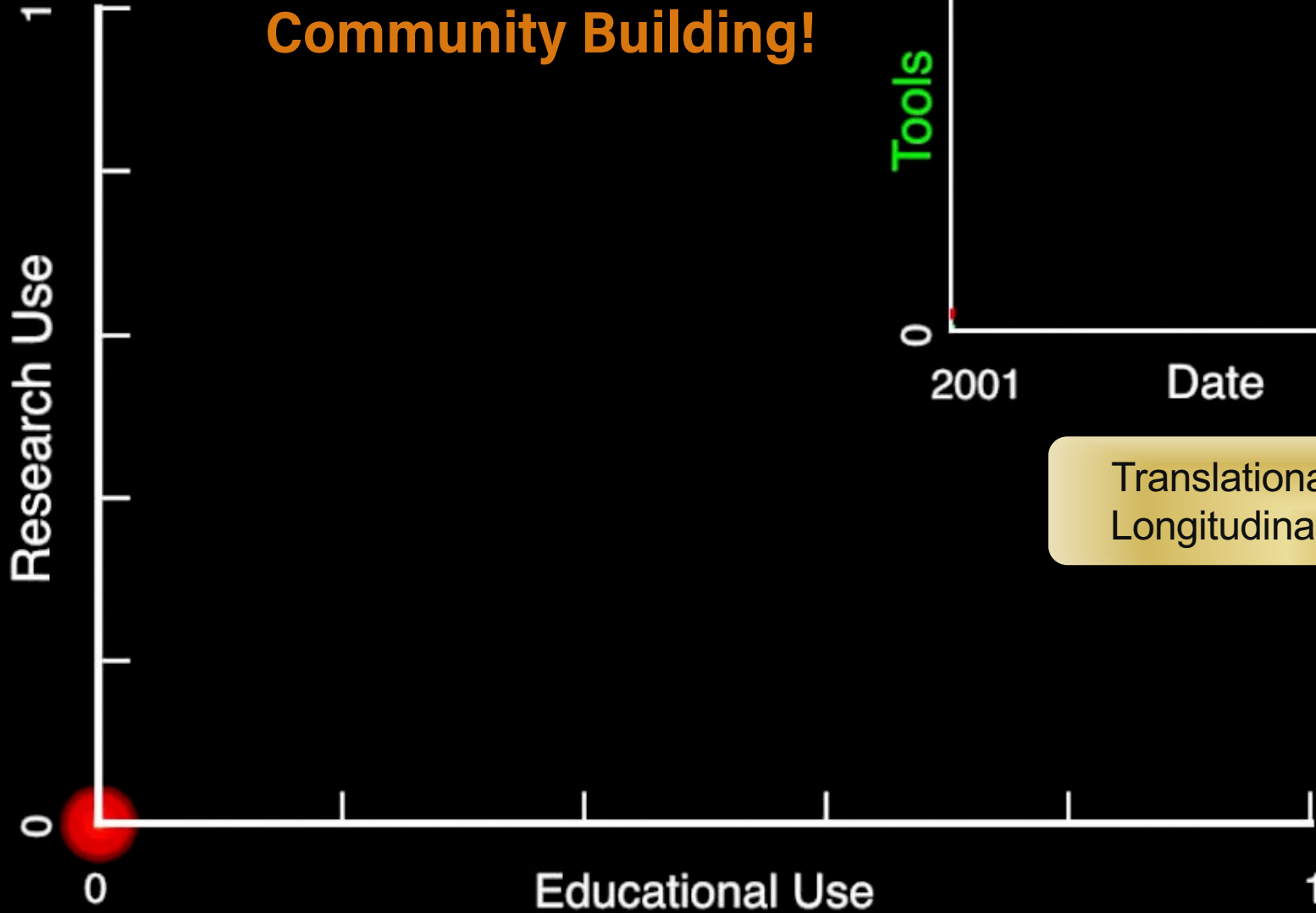


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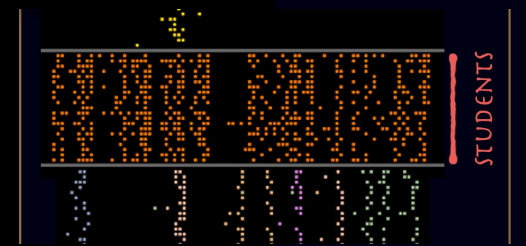
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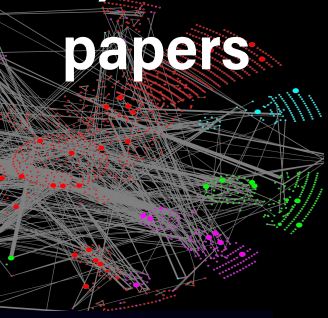


Translational with  
Longitudinal Data



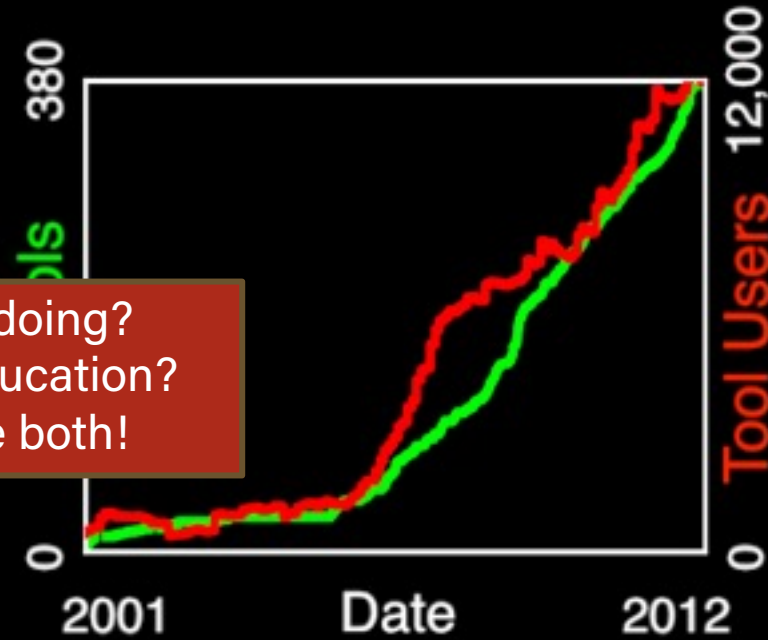
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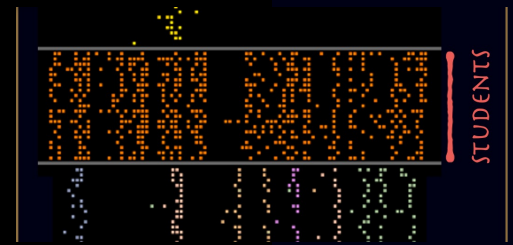
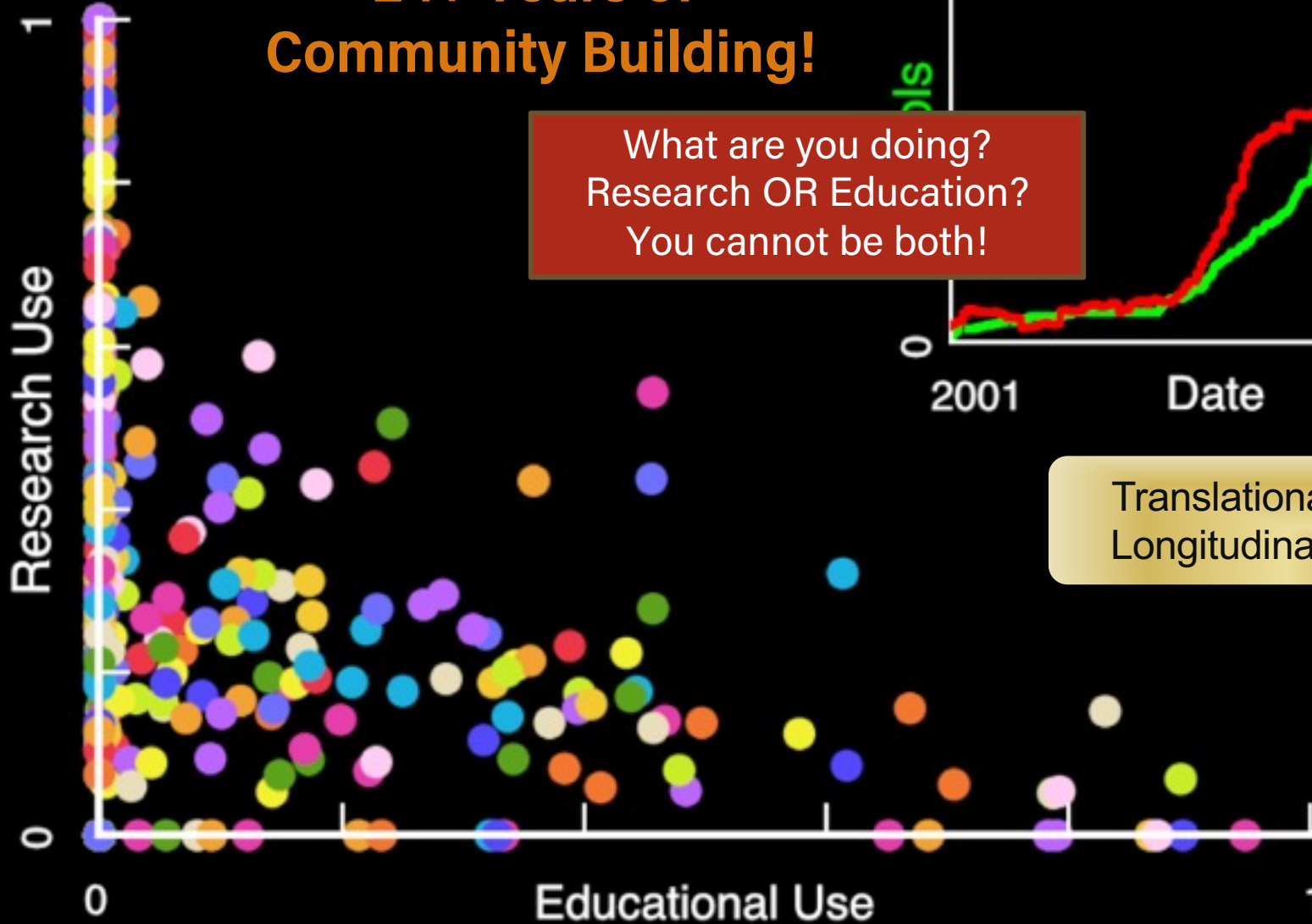


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**WEB OF SCIENCE**



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**Compact Models**

**FAIR Data**  
**findable, accessible, interoperable, reusable**

**Couple nH Data to AI**  
**We store all app-based simulation runs!**

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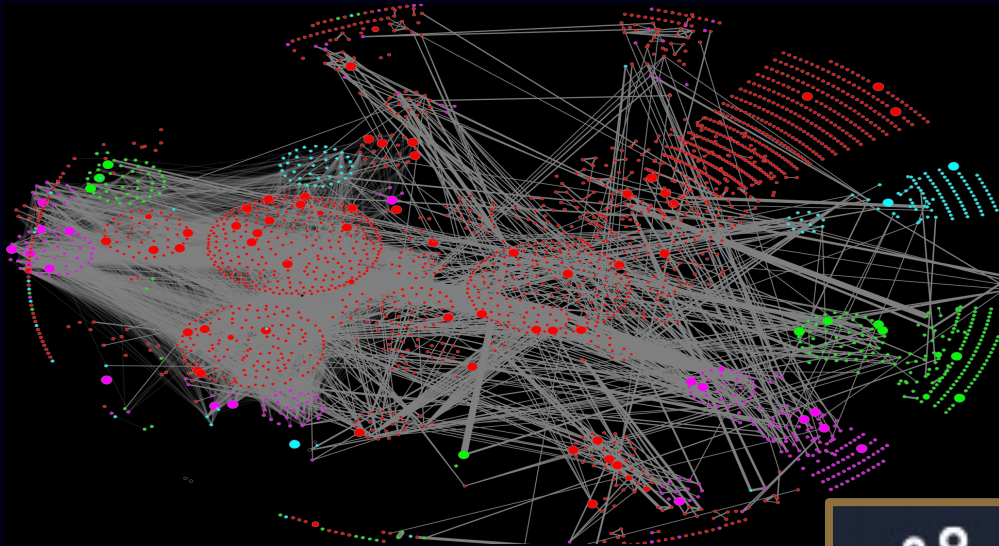
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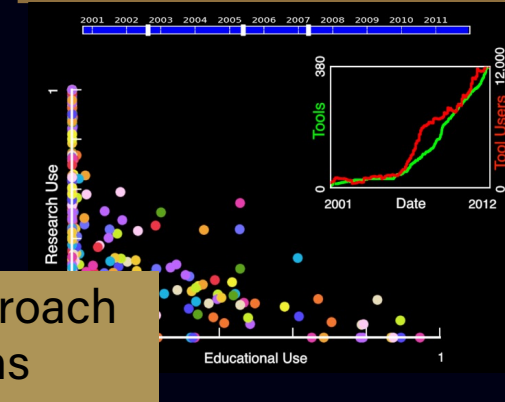
**250,000+ simulation users**

**2,750**

**citations**

**55%**

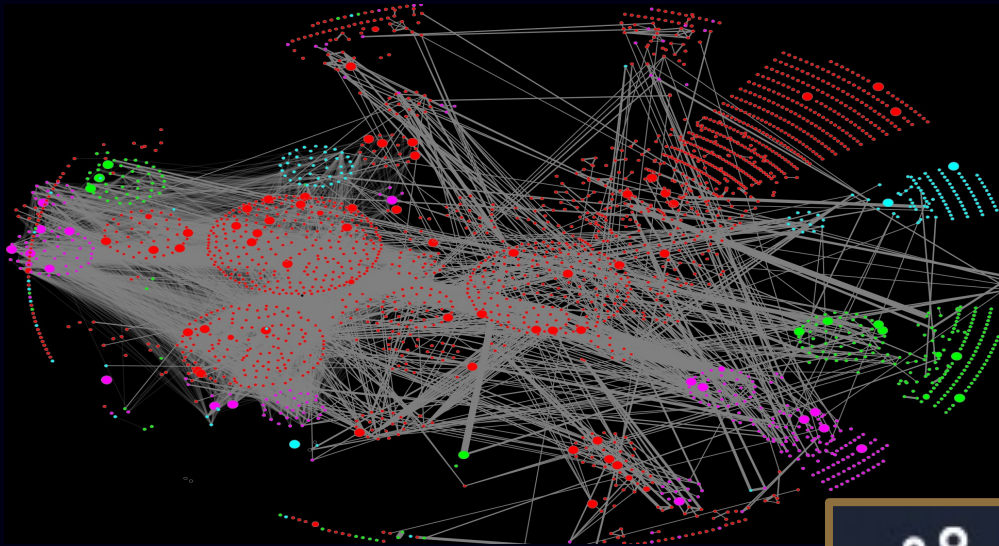
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a fundamental change in approach or underlying assumptions

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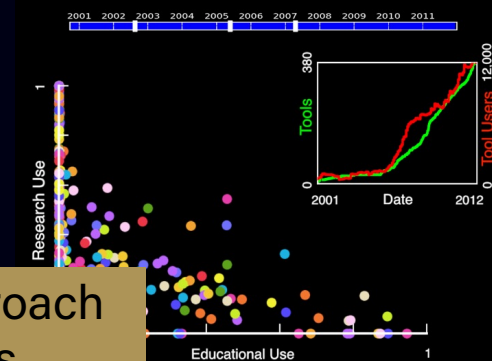
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Community Building!

**Ease of Use!**

# SILVACO

1,015 Users  
< 1 year!

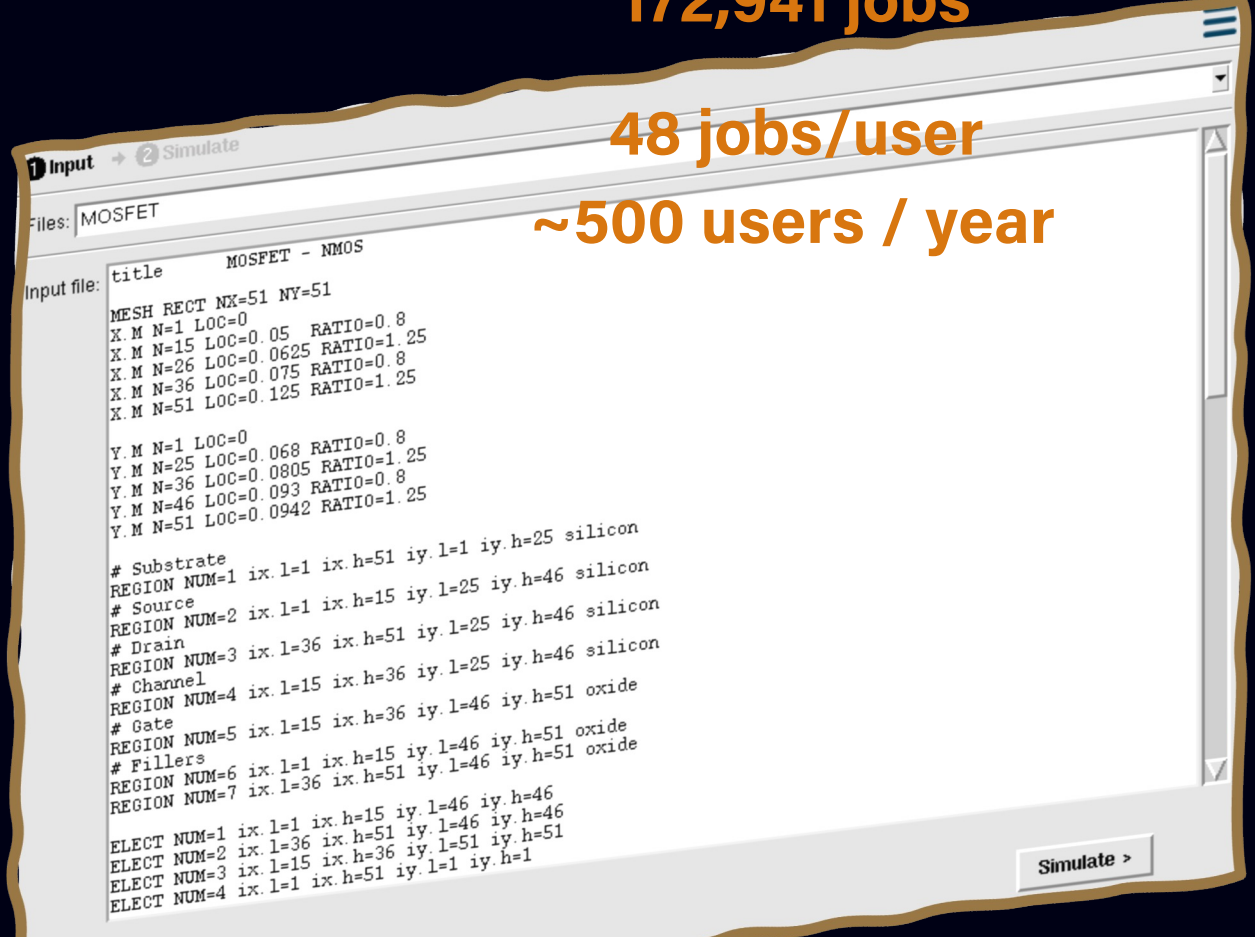
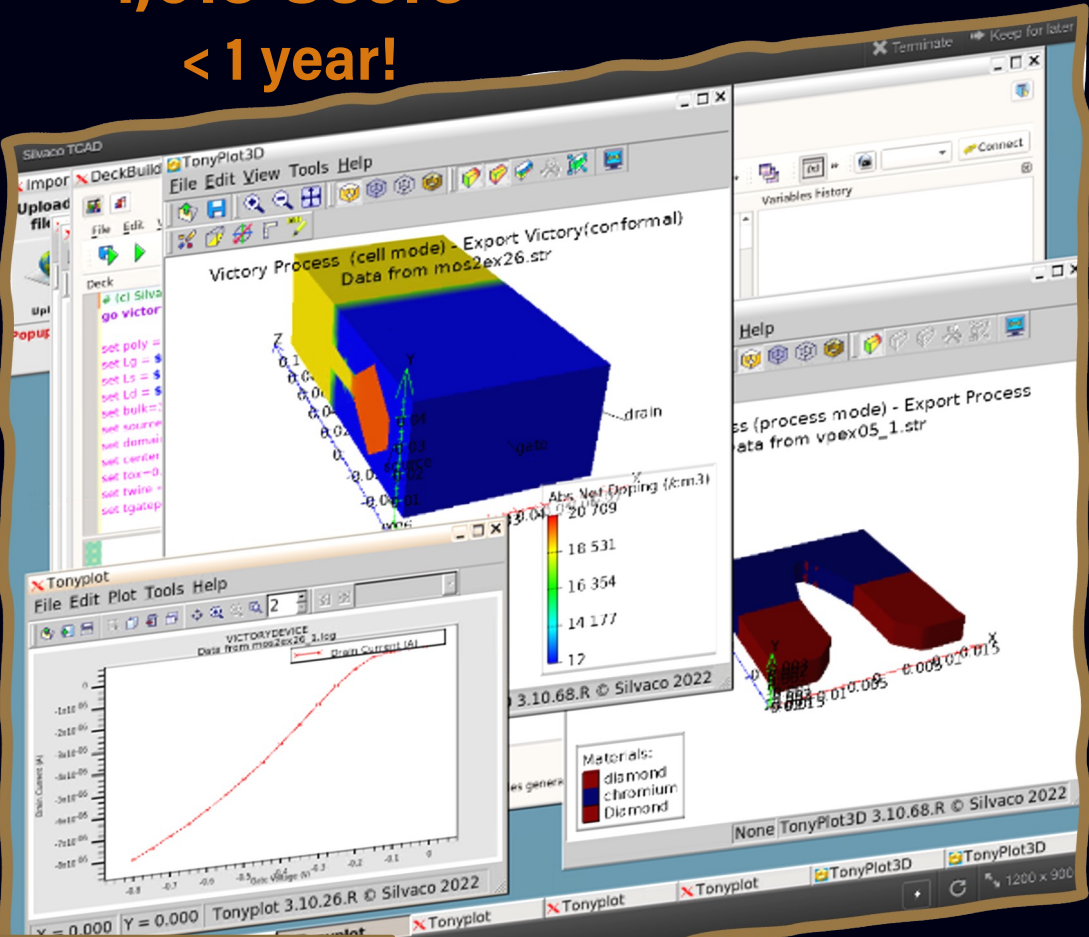
# Ease of Use!

PADRE / Bell Labs

3,566 Users,  
172,941 jobs

48 jobs/user

~500 users / year



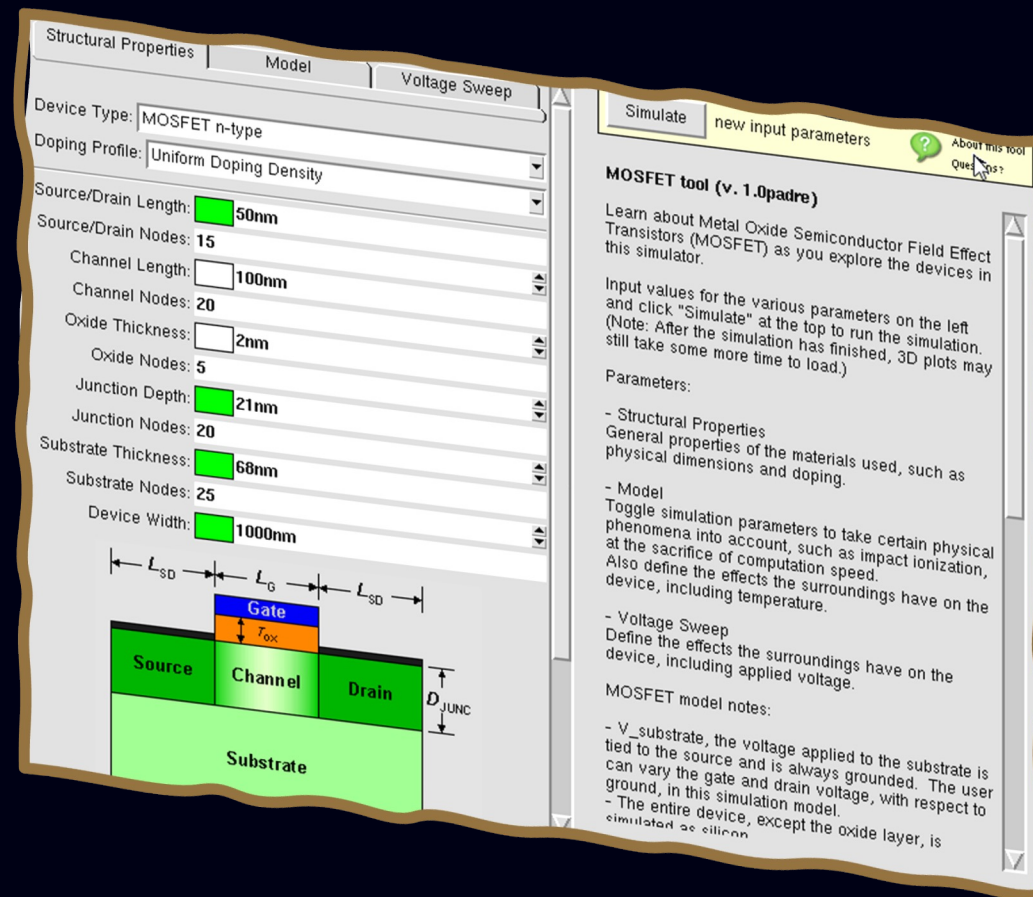
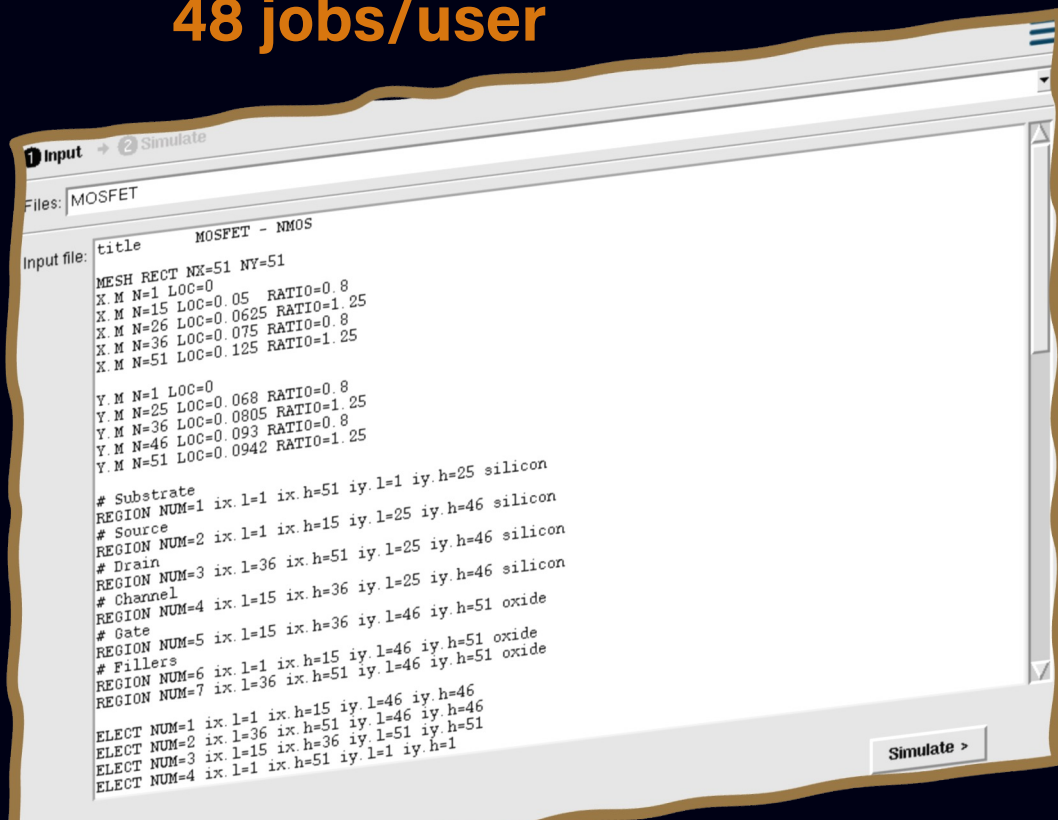
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**MOSFET:  
11,300 Users,  
227,000 jobs**



# Ease of Use!

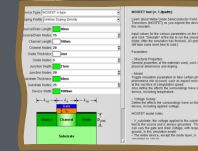
3,566 Users,  
172,941 jobs

17x  
4x

59,125 Users,  
770,462 jobs

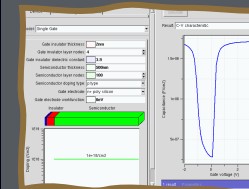
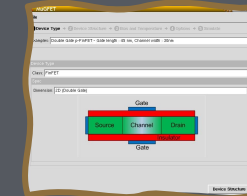
```
Input file: MOSFET
title MOSFET - NMOS
MESH RECT NX=51 NY=51
X M N=1 LOC=0
X M N=15 LOC=0.05 RATIO=0.8
X M N=26 LOC=0.0625 RATIO=1.25
X M N=36 LOC=0.075 RATIO=0.8
X M N=36 LOC=0.125 RATIO=1.25
Y M N=1 LOC=0
Y M N=25 LOC=0.068 RATIO=0.8
Y M N=36 LOC=0.0805 RATIO=1.25
Y M N=46 LOC=0.093 RATIO=0.8
Y M N=51 LOC=0.0942 RATIO=1.25
# Substrate
REGION NUM=1 ix.l=1 ix.h=51 iy.l=1 iy.h=25 silicon
# Source
REGION NUM=2 ix.l=1 ix.h=15 iy.l=25 iy.h=46 silicon
# Drain
REGION NUM=3 ix.l=36 ix.h=51 iy.l=25 iy.h=46 silicon
# Channel
REGION NUM=4 ix.l=15 ix.h=36 iy.l=25 iy.h=51 oxide
# Gate
REGION NUM=5 ix.l=15 ix.h=36 iy.l=46 iy.h=51 oxide
# Fillers
REGION NUM=6 ix.l=1 ix.h=15 iy.l=46 iy.h=51 oxide
REGION NUM=7 ix.l=36 ix.h=51 iy.l=46 iy.h=51 oxide
ELECT NUM=1 ix.l=1 ix.h=15 iy.l=46 iy.h=46
ELECT NUM=2 ix.l=36 ix.h=51 iy.l=46 iy.h=46
ELECT NUM=3 ix.l=15 ix.h=36 iy.l=51 iy.h=51
ELECT NUM=4 ix.l=1 ix.h=51 iy.l=1 iy.h=1
```

Simulate >



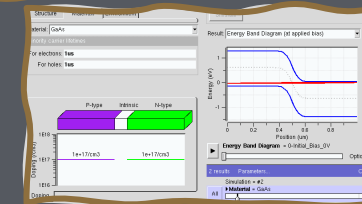
MOSFET:  
11,300 Users,  
227,000 jobs

MUGfet:  
3,846 Users,  
52,619 jobs

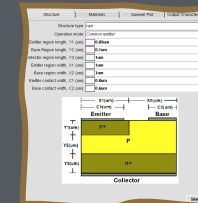


MOSCAP:  
9,010 Users,  
123,728 jobs

PN junction:  
24,012 Users,  
249,178 jobs



BJT:  
5,084 Users,  
41,433 jobs



Drift-Diffusion:  
5,873 Users,  
75,705 jobs

# Ease of Use!

3,566 Users,  
172,941 jobs

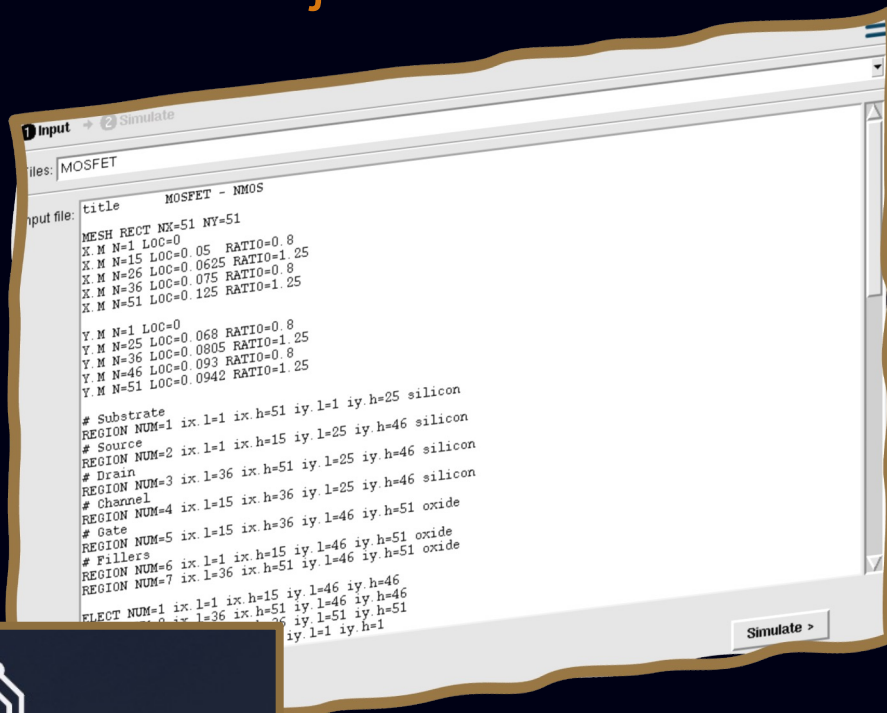
17x  
4x

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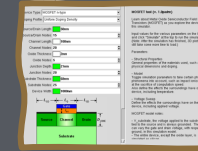
48 jobs/user

1/3.7x

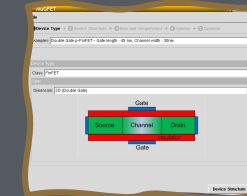
13 jobs/user



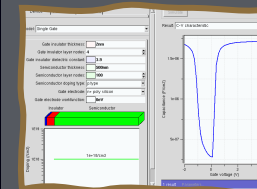
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REGION NUM=7 ix.l=36 ix.h=51 iy.l=51 iy.h=51
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ELECT NUM=2 ix.l=36 ix.h=51 iy.l=51 iy.h=51
```



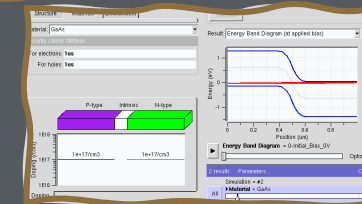
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11,300 Users,  
227,000 jobs



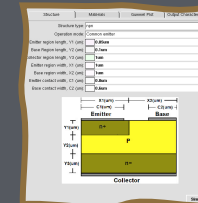
MUGfet:  
3,846 Users,  
52,619 jobs



MOSCAP:  
9,010 Users,  
123,728 jobs



PN junction:  
24,012 Users,  
249,178 jobs



BJT:  
5,084 Users,  
41,433 jobs



Drift-Diffusion:  
5,873 Users,  
75,705 jobs

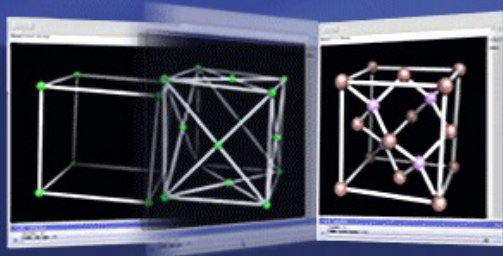
# Ease of Use!

What can you do,  
that no textbook does?

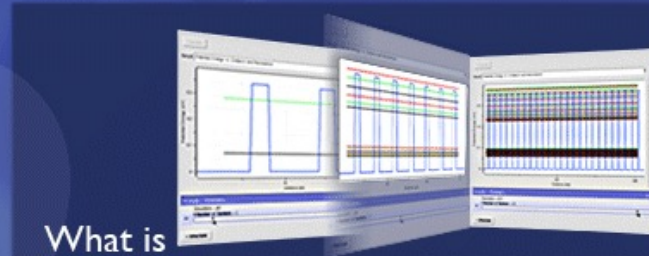
Introduction to semiconductor  
devices with **ABACUS**

nanoHUB.org

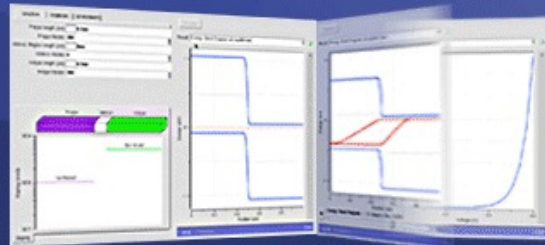
Assembly of Basic Applications for Coordinated Understanding of Semiconductors



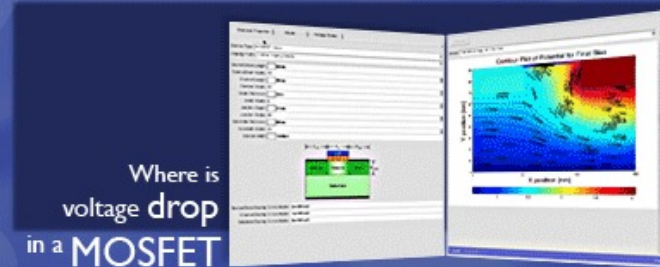
What is the  
silicon crystal structure



What is  
band structure



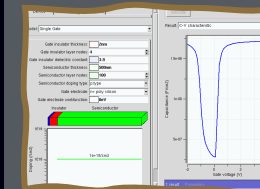
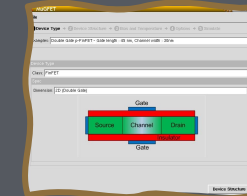
What are  
highly doped  
P/N-junctions



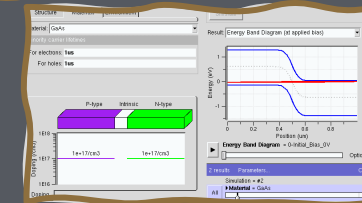
Where is  
voltage drop  
in a MOSFET

Homework and Project Assignments powered by Tools!

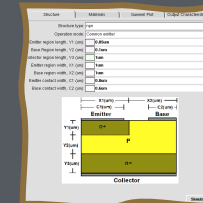
MUGfet:  
3,846 Users,  
52,619 jobs



MOSCAP:  
9,010 Users,  
123,728 jobs



PN junction:  
24,012 Users,  
249,178 jobs



BJT:  
5,084 Users,  
41,433 jobs



Drift-Diffusion:  
5,873 Users,  
75,705 jobs

What can you do,  
that no textbook does?

A Typical  
Textbook Page

### 5.1.4 The Built-In Potential ( $V_{bi}$ )

The voltage drop across the depletion region under equilibrium conditions, known as the built-in potential ( $V_{bi}$ ), is a junction parameter of sufficient importance to merit further consideration. We are particularly interested in establishing a computational relationship for  $V_{bi}$ . Working toward the stated goal, we consider a nondegenerately-doped pn junction maintained under equilibrium conditions with  $x = 0$  positioned at the metallurgical boundary. The ends of the equilibrium depletion region are taken to occur at  $-x_p$  and  $x_n$  on the p- and n-sides of the junction respectively (see Fig. 5.4b).

Proceeding with the derivation, we know

$$\mathcal{E} = -\frac{dV}{dx} \tag{5.4}$$

Integrating across the depletion region gives

$$V_{bi} = -\int_{-x_p}^{x_n} \mathcal{E} dx = \int_{V(-x_p)}^{V(x_n)} dV = V(x_n) - V(-x_p) = V_{bi} \tag{5.5}$$

Furthermore, under equilibrium conditions,

$$J_N = q\mu_n n \mathcal{E} + qD_N \frac{dn}{dx} = 0 \tag{5.6}$$

Solving for  $\mathcal{E}$  in Eq. (5.6) and making use of the Einstein relationship, we obtain

$$\mathcal{E} = -\frac{D_N}{\mu_n} \frac{dn/dx}{n} = -\frac{kT}{q} \frac{dn/dx}{n} \tag{5.7}$$

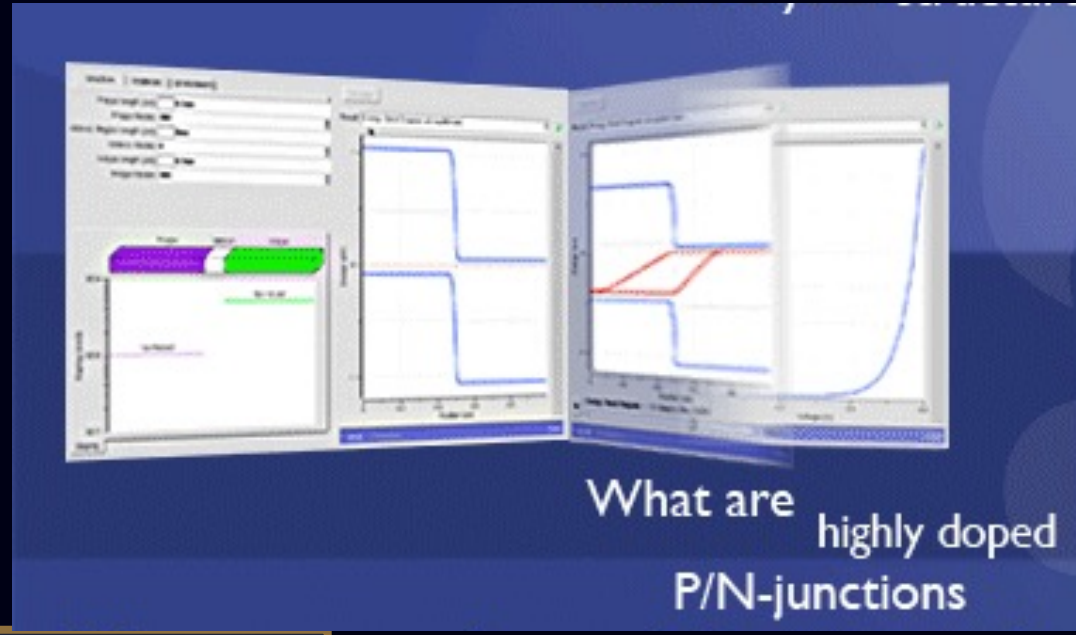
Substituting Eq. (5.7) into Eq. (5.5), and completing the integration then yields

$$V_{bi} = -\int_{-x_p}^{x_n} \mathcal{E} dx = \frac{kT}{q} \int_{n(-x_p)}^{n(x_n)} \frac{dn}{n} = \frac{kT}{q} \ln \left[ \frac{n(x_n)}{n(-x_p)} \right] \tag{5.8}$$

For the specific case of a nondegenerately doped step junction where  $N_D$  and  $N_A$  are the n- and p-side doping concentrations, one identifies

$$n(x_n) = N_D \tag{5.9a}$$

$$n(-x_p) = \frac{n_i^2}{N_A} \tag{5.9b}$$



R.F. Pierret



What can you do, that no textbook does?

Real devices are non-ideal!

5.1.4 The Built-In Potential ( $V_{bi}$ )

The voltage drop across the depletion region under equilibrium conditions, known as the built-in potential ( $V_{bi}$ ), is a junction parameter of sufficient importance to merit further consideration. We are particularly interested in establishing a computational relationship for  $V_{bi}$ . Working toward the stated goal, we consider a nondegenerately-doped pn junction maintained under equilibrium conditions with  $x = 0$  positioned at the metallurgical boundary. The ends of the equilibrium depletion region are taken to occur at  $-x_p$  and  $x_n$  on the p- and n-sides of the junction respectively (see Fig. 5.4b).

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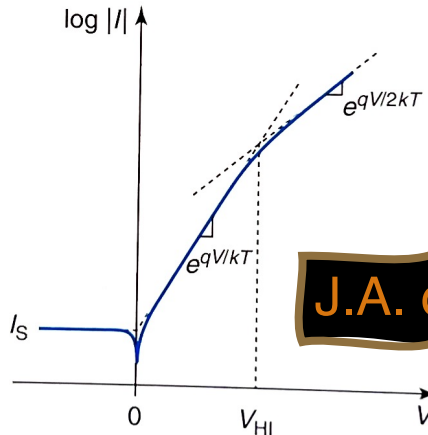
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$$V_{bi} = -\int_{-x_p}^{x_n} \mathcal{E} dx = \frac{kT}{q} \int_{n(-x_p)}^{n(x_n)} \frac{dn}{n} = \frac{kT}{q} \ln \left[ \frac{n(x_n)}{n(-x_p)} \right] \quad (5.8)$$

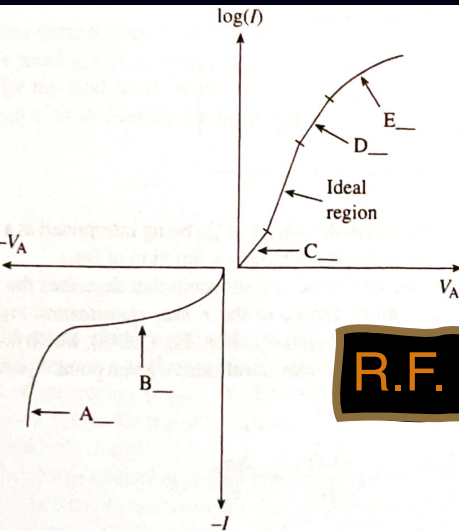
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$$n(x_n) = N_D \quad (5.9a)$$

$$n(-x_p) = \frac{n_i^2}{N_A} \quad (5.9b)$$



J.A. del Alamo



R.F. Pierret

FIGURE 6.40 Sketch of forward bias  $I$ - $V$  characteristics of a PN diode. For strong forward voltage, the diode can go into high-level injection and the current grows as  $e^{qV/2kT}$ .

Fig. 6.40 that, in fact, for strong forward voltage, the  $I$ - $V$  characteristics deviate from their ideal  $e^{qV/kT}$  behavior into what appears more to be  $e^{qV/2kT}$ . Let us discuss why this happens. First, let us estimate the voltage at which high-level injection occurs. This is simply considered here a P<sup>+</sup>N diode with a donor concentration  $N_D$  (an entirely equivalent concentration in a semilog scale) in the n region as the diode forward voltage increases. Figure 6.41 shows the evolution of the minority and majority carrier concentrations in the n region as the diode forward voltage increases. The figure clearly shows that the location that is driven first into high-level injection is the edge of the SCR. For small forward voltages, the minority carrier concentration is much less than the level and the majority carrier concentration is hence unaffected by minority carrier injection. For a high enough forward voltage, the minority carrier concentration at the edge of the SCR

The prose gets dense

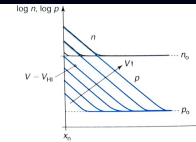


FIGURE 6.41 Minority and majority carrier concentrations in the n side of a P<sup>+</sup>N diode as a function of forward bias. At  $V_{HI}$ , the n region goes into high-level injection.

reaches a value equal to the doping level. At this voltage, the majority carrier concentration at the edge of the SCR is twice the doping level. Clearly, it is not possible to assume any longer that the majority carrier concentration is unaffected as this would violate quasi-neutrality. The n side of the QNR has become high-level injected. This is a reasonable definition for the onset of high-level injection. If we allow ourselves to "stretch" the low-level injection boundary condition, Eq. (6.29), up to this point, high-level injection occurs when

$$p(x_n) = \frac{n_i^2}{N_D} \exp \frac{qV_{HI}}{kT} = N_D \quad (6.124)$$

where  $V_{HI}$  refers to the voltage at the onset of high-level injection. Solving for  $V_{HI}$  in this equation, we get

$$V_{HI} = \frac{2kT}{q} \ln \frac{N_D}{n_i} \quad (6.125)$$

This result is reasonable. The higher the doping level (of the lowly doped side), the higher the voltage that it takes to drive the diode into high-level injection.

In microelectronic device operation, we are not interested in general in the high-level injection regime. This is something to be avoided. In PN junctions, for example, the  $I$ - $V$  characteristics grow more slowly, as sketched in Fig. 6.40, something that is undesirable for many applications. In bipolar transistors, for example, high-level injection of the base brings with it a drop in gain. Unless one is working with devices that have been designed to operate in high-level injection, such as power diodes or certain kinds of solar cells, high-level injection is a syndrome to avoid all together. For this reason, we will not treat it in detail here.

It is of value, nevertheless, to understand the origin of the  $e^{qV/2kT}$  dependence of the current in the high-level injection regime. This result can be easily derived from the expression of the  $n$ p product inside the SCR given by Eq. (6.47). This equation remains valid in the high-level injection regime because it simply states that electrons and holes are in equilibrium among each other due to the fact that the SCR is very thin. At the edge of the SCR that goes into high-level injection first,  $n \approx p$ , and

$$n \approx p \approx n_i \exp \frac{qV}{2kT} \quad (6.126)$$

The nature of the diode current is still carrier recombination in the QNRs. The boundary condition of Eq. (6.126) implies that the voltage dependence of the current will be of the form  $e^{qV/2kT}$ .

Physically, one can understand the origin of this result by examining the evolution of the energy band diagrams around the SCR as the voltage increases. This is sketched in Fig. 6.42. The key is to examine the dependence of the energy barrier that carriers face in crossing the junction. In the low-level injection regime, as the voltage increases, the energy barrier is reduced by exactly  $qV$ . This is because the majority carrier quasi-Fermi levels are "rigidly" tied up to the respective band edges. This results from the fact that in low-level injection, the majority carrier concentrations remain unchanged.

As one of the sides of the diode goes into high-level injection, this is not the case any longer. The large minority carrier injection forces an increase in the majority carrier concentration. As a consequence, in high-level injection, the majority carrier quasi-Fermi level on the high-level side gets closer and closer to the majority carrier band edge (conduction band for a p<sup>+</sup>-n diode). After this happens, the energy barrier presented by the junction is only reduced at half the rate of the quasi-Fermi level splitting (always  $qV$ ). This is sketched in Fig. 6.42.

References to "exact" solutions

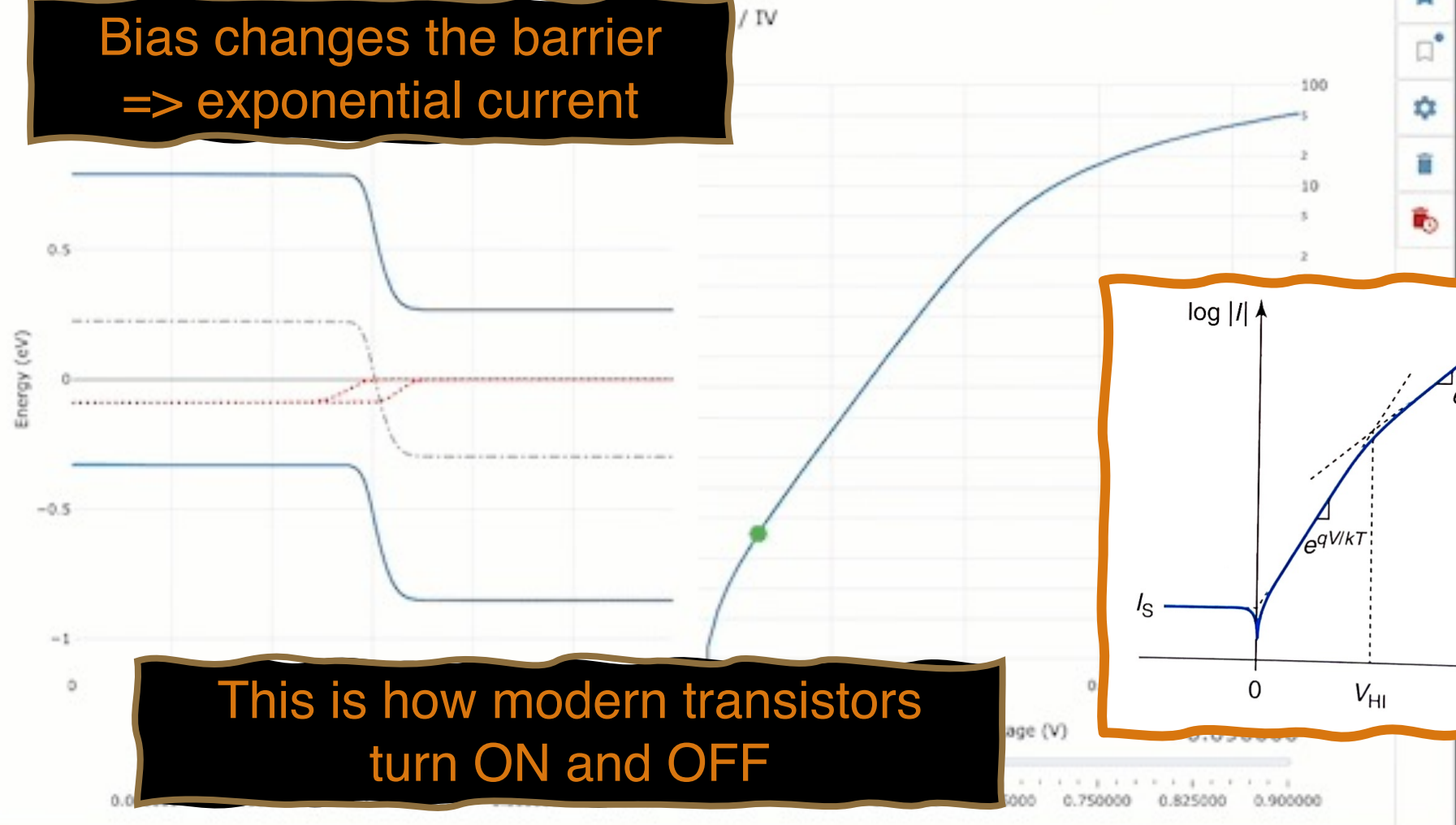


### PN-Junction Lab

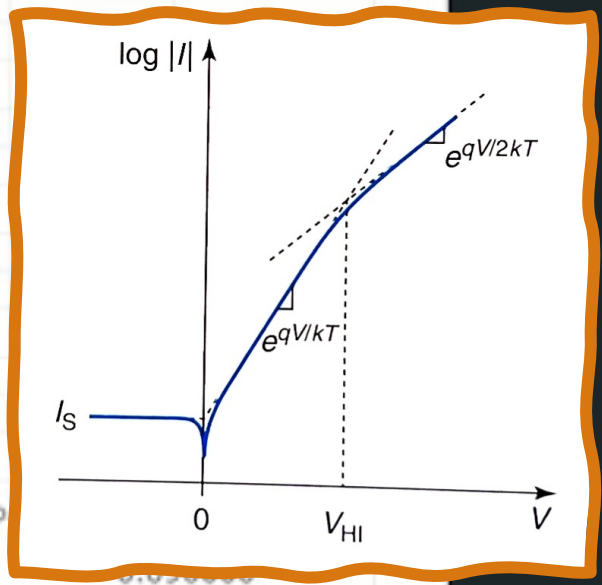
- Energy Bands (I-V)
- Energy Bands
- I-V Characteristics
- C-V Characteristics
- Total Current
- Total Density
- Electric Potential
- Electric Field
- Recombination
- Carrier Density
- Input Params
- Access FAIR Data
- Settings
- Compare

Parameters

Bias changes the barrier  
=> exponential current



This is how modern transistors  
turn ON and OFF





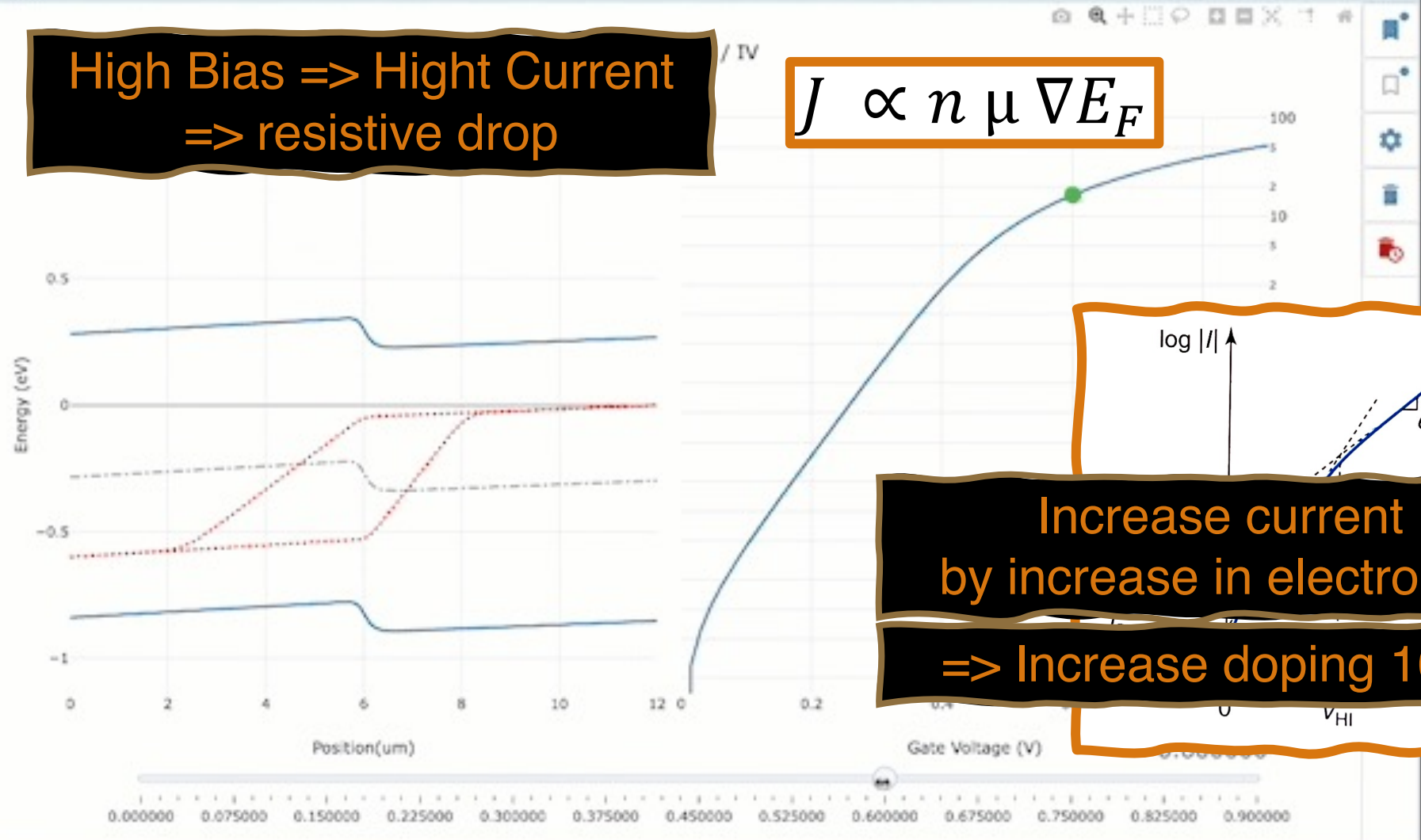
PN-Junction Lab

- Energy Bands (I-V)
- Energy Bands
- I-V Characteristics
- C-V Characteristics
- Total Current
- Total Density
- Electric Potential
- Electric Field
- Recombination
- Carrier Density
- Input Params
- Access FAIR Data
- Settings
- Compare

Parameters

High Bias => High Current  
=> resistive drop

$$J \propto n \mu \nabla E_F$$



log |J| ↑  
 $e q V / 2 k T$

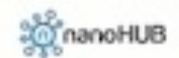
Increase current  
by increase in electrons?

=> Increase doping 100x



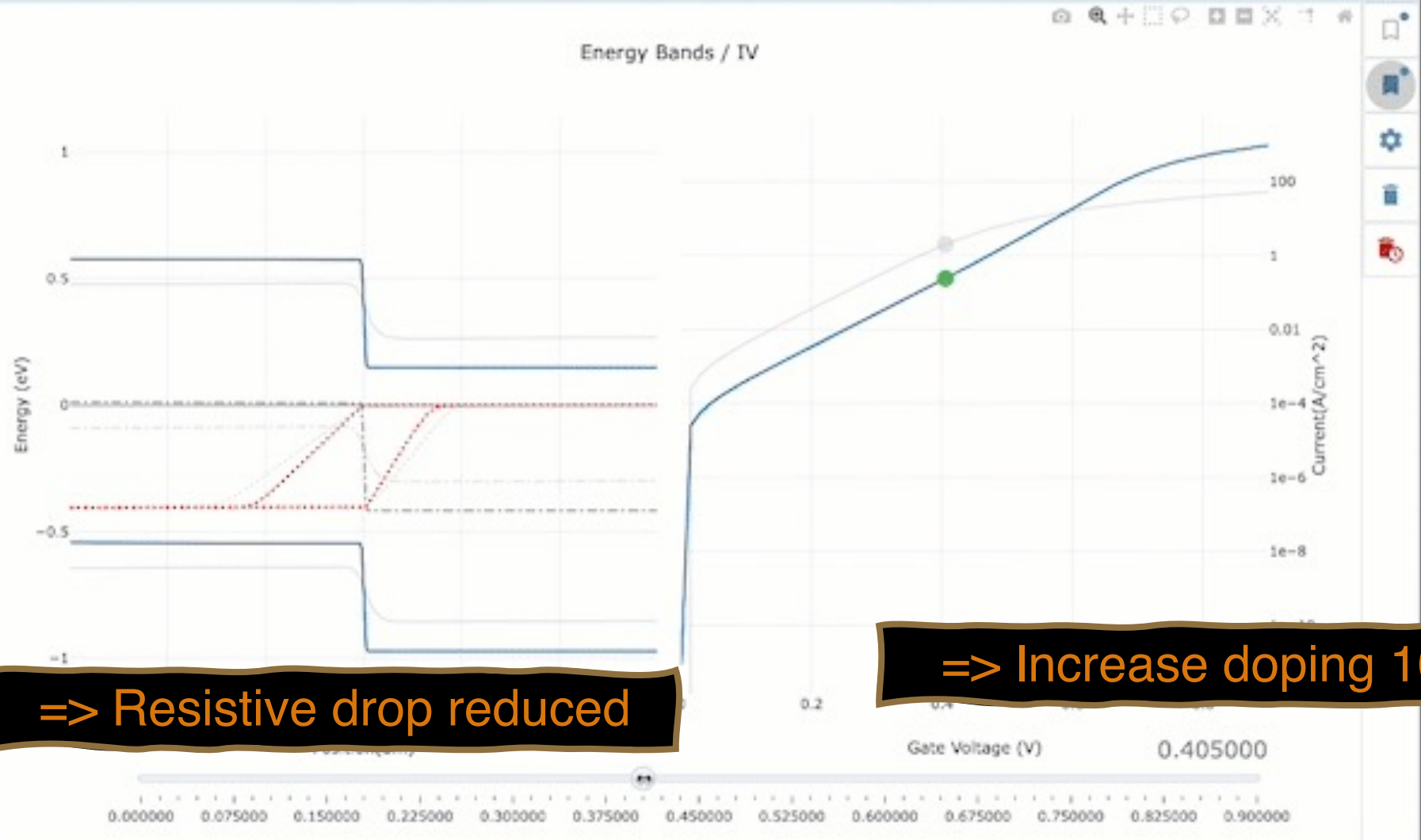
# PN-Junction Lab

Submit a ticket Terminate Session



- Energy Bands (I-V)
- Energy Bands
- I-V Characteristics
- C-V Characteristics
- Total Current
- Total Density
- Electric Potential
- Electric Field
- Recombination
- Carrier Density
- Input Params
- Access FAIR Data
- Settings
- Compare

Parameters



=> Resistive drop reduced

=> Increase doping 100x

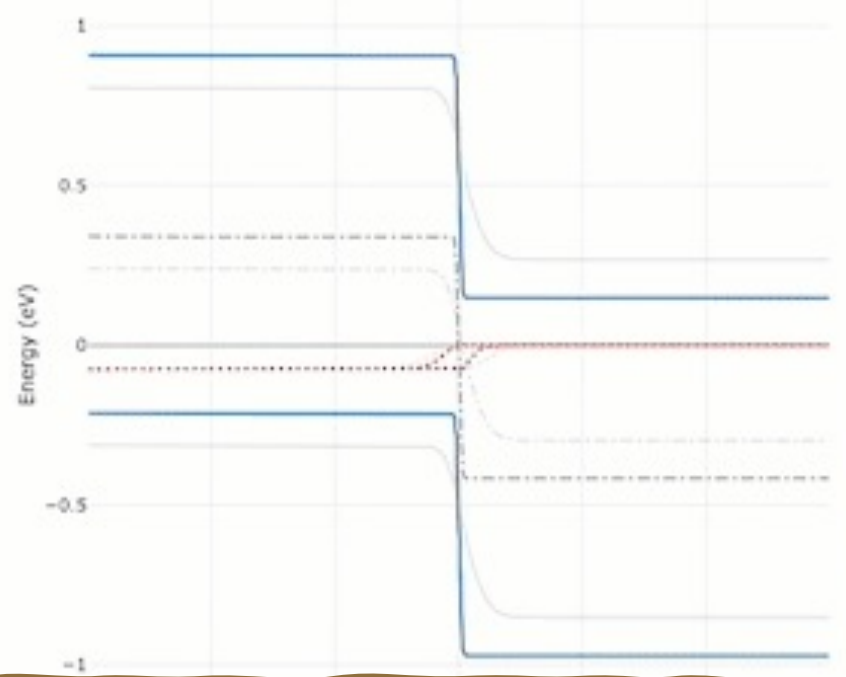


### PN-Junction Lab

- Energy Bands (I-V)
- Energy Bands
- I-V Characteristics
- C-V Characteristics
- Total Current
- Total Density
- Electric Potential
- Electric Field
- Recombination
- Carrier Density
- Input Params
- Access FAIR Data
- Settings
- Compare

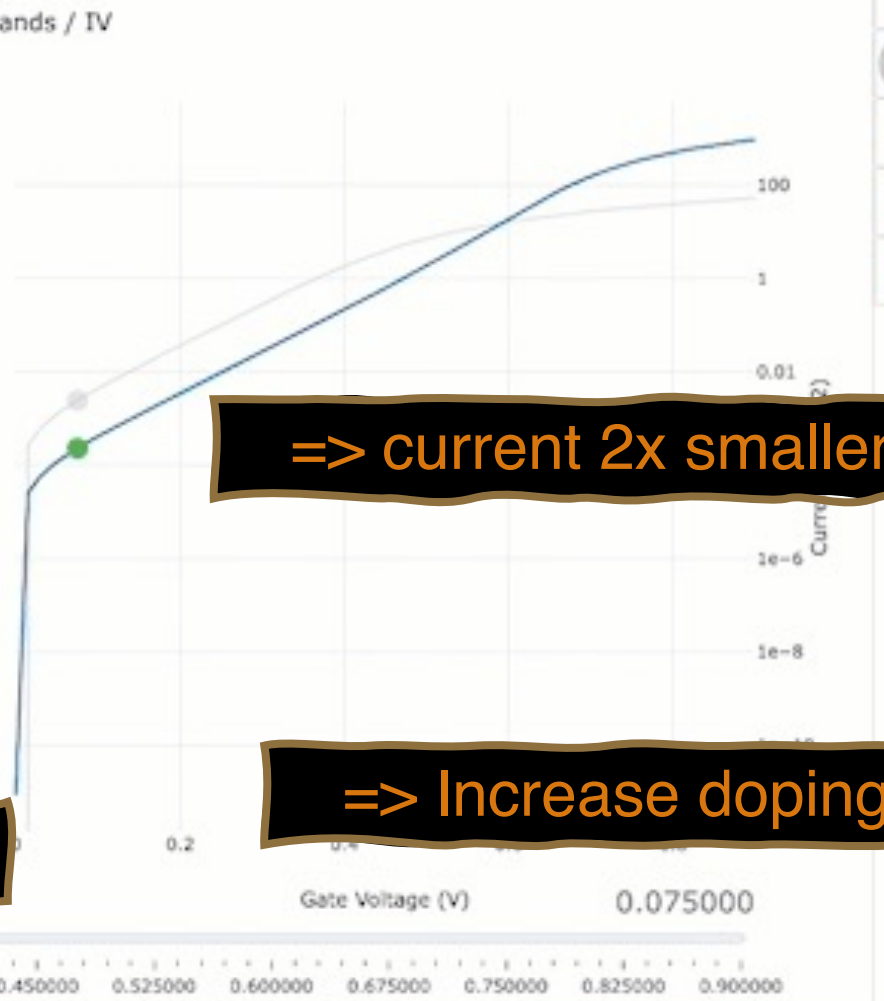
Parameters

The barrier got bigger!



=> Resistive drop reduced

Make the resistor shorter!



=> current 2x smaller!

=> Increase doping 100x



# PN-Junction Lab

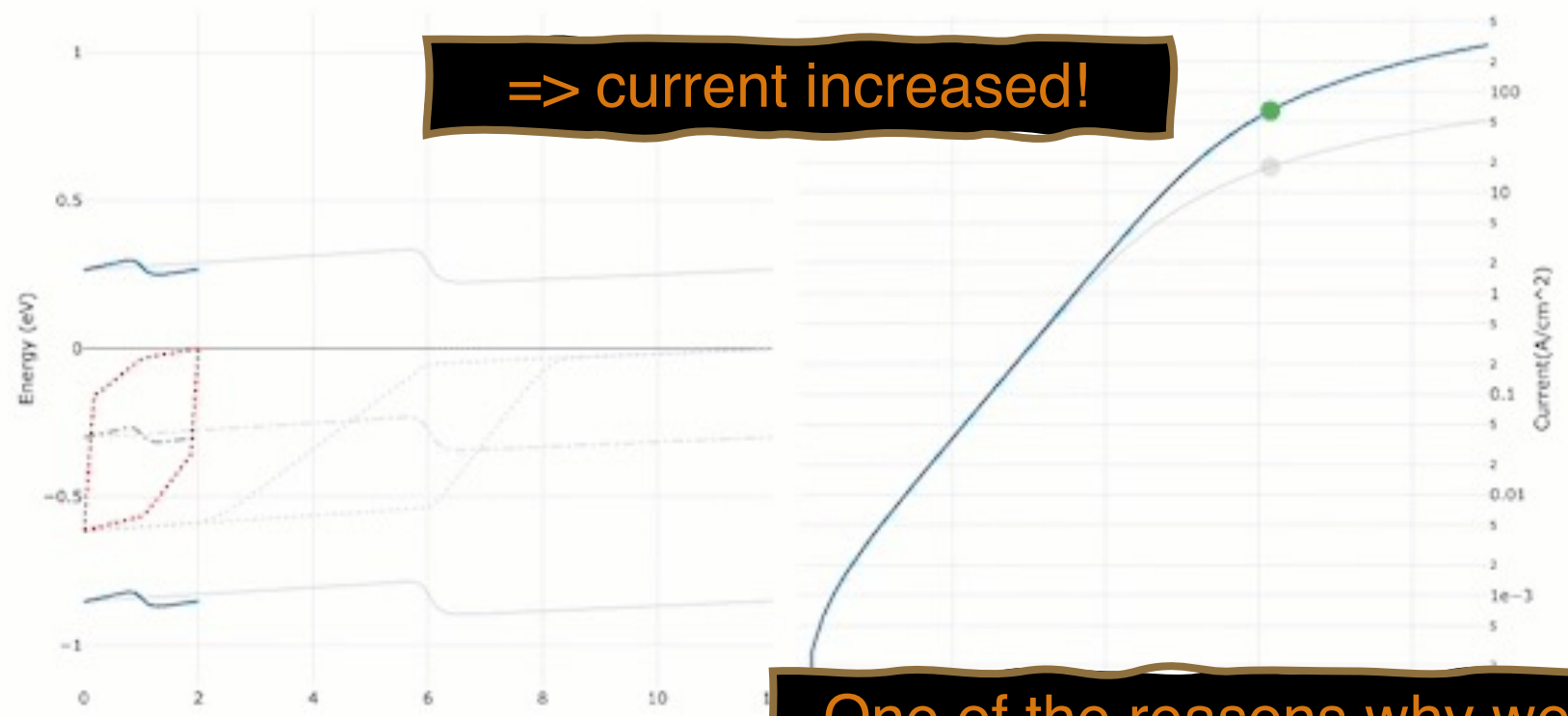
Submit a ticket Terminate Session



- Energy Bands (I-V)
- Energy Bands
- I-V Characteristics
- C-V Characteristics
- Total Current
- Total Density
- Electric Potential
- Electric Field
- Recombination
- Carrier Density
- Input Params
- Access FAIR Data
- Settings
- Compare

Parameters

Energy Bands / IV



=> current increased!

Make the resistor shorter!

One of the reasons why we make devices smaller



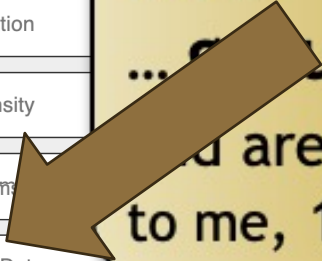
- Energy Bands (I-V)
- Energy Bands
- I-V Characteristics
- C-V Characteristics
- Total Current
- Total Density
- Electric Potential
- Electric Field
- Recombination
- Carrier Density
- Input Parameters
- Access FAIR Data
- Settings
- Compare

Parameters

**Student Discussions!  
Interactive - exploratory Learning!**

**=> current increased!**

Public on RateMyprofessor  
 ....I'm in the military so I have weird, long work hours  
 ... group projects--which were **HIGHLY** valuable,  
 and are why the class has been so meaningful  
 to me, 10/10 would recommend!



**Make the resistor shorter!**

**One of the reasons why we  
make devices smaller**



# Not just Devices!

## Materials, Photonics, Processing etc

Input Params

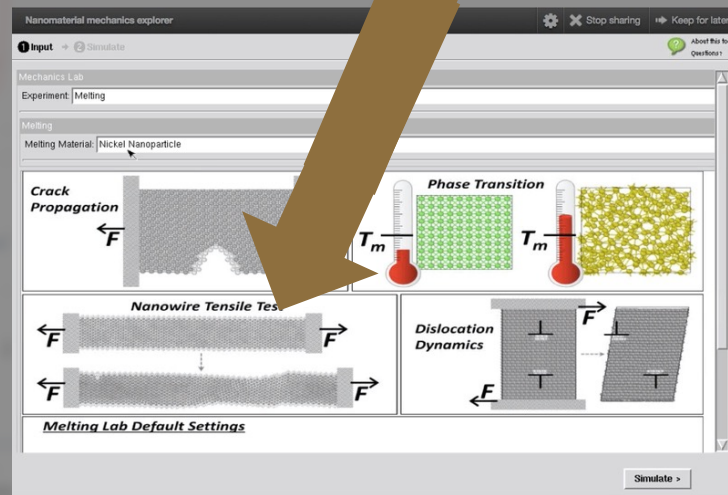
Access FAIR Data

Settings

ResultsDB

Findable,  
Accessible,  
Interoperable,  
Reusable

```
Projects — vi .//Semicond/MoTe2Crack/Crack/monolayer-MoTe2-hex.in — 104x45
units      real
atom_style full
boundary   p p s
|
box        tilt large
region    box prism 0 3.5562 0 3.0797 0 9.0000 -1.7781 0.0 0.0
create_box 2 box
lattice    custom 1.0 a1 3.5562 0.0 0.0 a2 1.7781 3.0797 0.0 a3 0.0 0.0 9.0 &
          basis 0.0 0.0 0.0
create_atoms 1 single 0.0 0.0 0.5 units lattice
create_atoms 2 single 0.3333 0.3333 0.7003 units lattice
create_atoms 2 single 0.3333 0.3333 0.2997 units lattice
|
mass       1 97.9055000
           2 129.9067000
|
replicate  30 30 1
|
pair_style reax/c lmp_control checkqeq yes
pair_coeff  * *ffield-MoTeCu Mo Te
|
timestep   0.5
thermo_style custom etotal pe ke temp evdwl press pxx pyy pzz pxy pxz pyz lx ly lz
thermo_modify flush yes
thermo     10
|
variable   ti equal 300.0
|
dump       1 all custom 100 traj.dump id type x y z q
|
fix        0 all qeq/reax 1 0.0 10.0 1.0e-6 reax/c
minimize   1.0e-8 1.0e-8 100 1000
|
velocity   all create ${ti} 4928459 mom yes rot yes dist gaussian
fix        1 all nvt/sllod temp ${ti} 500.0
fix        2 all deform 1 x erate 0.000002 remap v units box
run        100000
~
```





# FAIR Data

Input Params

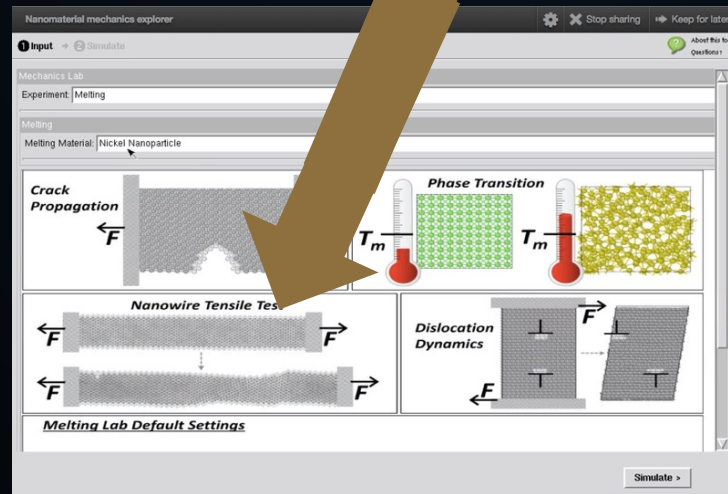
Access FAIR Data

Settings

ResultsDB

- ✓ Inputs
- ✓ Outputs
- ✓ Metadata
- DOIs for each dataset
- Unique identifier for each entry

```
Projects — vi .//Semicond/MoTe2Crack/Crack/monolayer-MoTe2-hex.in — 104x45
units      real
atom_style full
boundary   p p s
|
box        tilt large
region     box prism 0 3.5562 0 3.0797 0 9.0000 -1.7781 0.0 0.0
create_box 2 box
lattice    custom 1.0 a1 3.5562 0.0 0.0 a2 1.7781 3.0797 0.0 a3 0.0 0.0 9.0 &
basis      0.0 0.0 0.0
create_atoms 1 single 0.0 0.0 0.5 units lattice
create_atoms 2 single 0.3333 0.3333 0.7003 units lattice
create_atoms 2 single 0.3333 0.3333 0.2997 units lattice
|
mass       1 97.9055000
           2 129.9067000
|
replicate  30 30 1
|
pair_style reax/c lmp_control checkqeq yes
pair_coeff  * *ffield-MoTeCu Mo Te
|
timestep   0.5
thermo_style custom etotal pe ke temp evdwl press pxx pyy pzz pxy pxz pyz lx ly lz
thermo_modify line multi flush yes
thermo     10
|
variable   ti equal 300.0
|
dump       1 all custom 100 traj.dump id type x y z q
|
fix        0 all qeq/reax 1 0.0 10.0 1.0e-6 reax/c
minimize   1.0e-8 1.0e-8 100 1000
|
velocity   all create $(ti) 4928459 mom yes rot yes dist gaussian
fix        1 all nvt/sllod temp $(ti) $(ti) 100.0
fix        2 all deform 1 x erate 0.000002 remap v units box
run        100000
~
```



RESULTS: cellrelaxdft

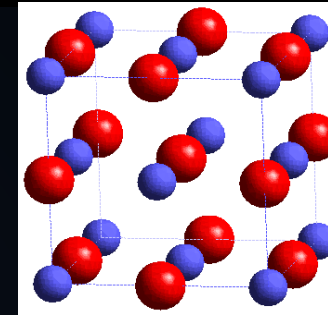
This is a live publication with the page and some content publicly available.

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Dataset Title		Cell Relax DFT													
REVISION															
Total records		23199													
VALUES		API													
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3	r45	cellrelaxdft/r45/c81...	1	21-02-2023	229	true	1624.9524080847	100	1	1	1	1	1	1	1
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8	r45	cellrelaxdft/r45/95b...	1	21-02-2023	221	false	2000	60	2	2	2	2	2	2	2
9	r42	cellrelaxdft/r42/31b...	1	21-02-2023	225	true	2000	200	10	10	10	10	10	10	10
10	r42	cellrelaxdft/r42/5a4...	1	21-02-2023	225	true	2000	200	10	10	10	10	10	10	10
11	r45	cellrelaxdft/r45/82d...	2	21-02-2023	221	false	1426.4467252425	60	6	6	6	6	6	6	6
12	r45	cellrelaxdft/r45/83e...	2	21-02-2023	225	false	1514.9743407545	60	1	1	1	1	1	1	1
13	r45	cellrelaxdft/r45/83e...	2	21-02-2023	225	false	1514.9743407545	60	7	7	7	7	7	7	7
14	r45	cellrelaxdft/r45/2fa...	2	21-02-2023	225	false	1514.9743407545	60	13	13	13	13	13	13	13
15	r45	cellrelaxdft/r45/37b...	2	21-02-2023	225	false	1514.9743407545	60	16	16	16	16	16	16	16
16	r45	cellrelaxdft/r45/37b...	2	21-02-2023	221	false	1426.4467252425	60	6	6	6	6	6	6	6
17	r45	cellrelaxdft/r45/675...	16	21-02-2023	166	false	2000	60	2	2	2	2	2	2	2
18	r45	cellrelaxdft/r45/46a...	1	21-02-2023	194	false	2000	100	7	7	7	7	7	7	7
19	r45	cellrelaxdft/r45/51f...	24	21-02-2023	194	false	2000	60	6	6	6	6	6	6	6
20	r45	cellrelaxdft/r45/51f...	24	21-02-2023	194	false	2000	60	8	8	8	8	8	8	8

# Not just Our Own Data!



The Materials Project  
ResultsDB



Ionic packing fraction:

$$IPF = \frac{\sum \frac{4}{3} \pi R_i^3}{(a \times b) \cdot c}$$

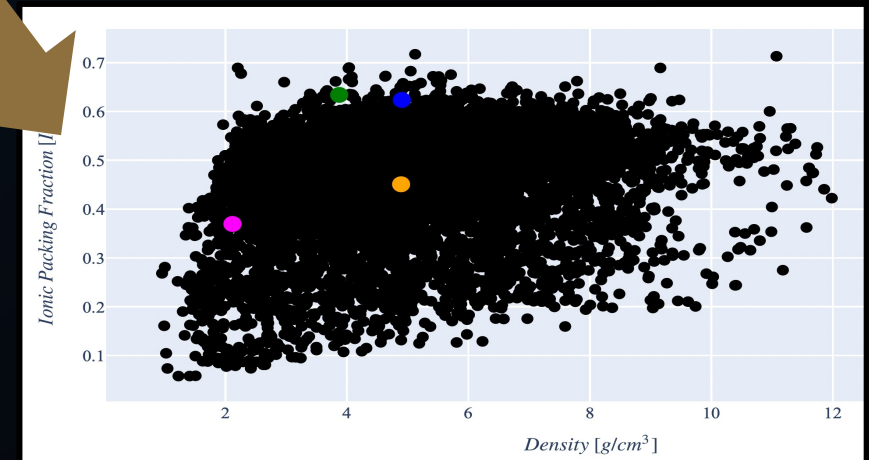
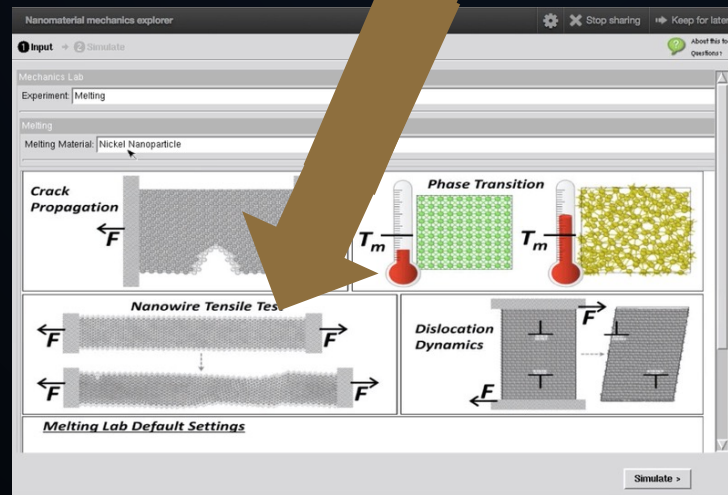
Sophomore-level class  
Compute and visualize  
properties for 65,000 oxides  
Materials discovery

Input Params

Access FAIR Data

Settings

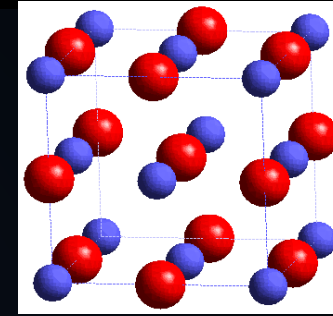
```
Projects — vi .//Semicond/MoTe2Crack/Crack/monolayer-MoTe2-hex.in — 104x45
units      real
atom_style full
boundary   p p s
box        tilt large
region    box prism 0 3.5562 0 3.0797 0 9.0000 -1.7781 0.0 0.0
create_box 2 box
lattice   custom 1.0 a1 3.5562 0.0 0.0 a2 1.7781 3.0797 0.0 a3 0.0 0.0 9.0 &
basis    0.0 0.0 0.0
create_atoms 1 single 0.0 0.0 0.5 units lattice
create_atoms 2 single 0.3333 0.3333 0.7003 units lattice
create_atoms 2 single 0.3333 0.3333 0.2997 units lattice
mass      1 97.9055000
           2 129.9067000
replicate 30 30 1
pair_style reax/c lmp_control checkqeq yes
pair_coeff * *ffield-MoTeCu Mo Te
timestep  0.5
thermo_style custom etotal pe ke temp evdwl press pxx ppy pzz pxy pxz pyz lx ly lz
thermo_modify flush yes
thermo    10
variable  ti equal 300.0
dump      1 all custom 100 traj.dump id type x y z q
fix       0 all qeq/reax 1 0.0 10.0 1.0e-6 reax/c
minimize  1.0e-8 1.0e-8 100 1000
velocity  all create $(ti) 4928459 mom yes rot yes dist gaussian
fix       1 all nvt/sllod temp $(ti) $(ti) 100.0
fix       2 all deform 1 x erate 0.000002 remap v units box
run       100000
```



# FAIR Data & AI

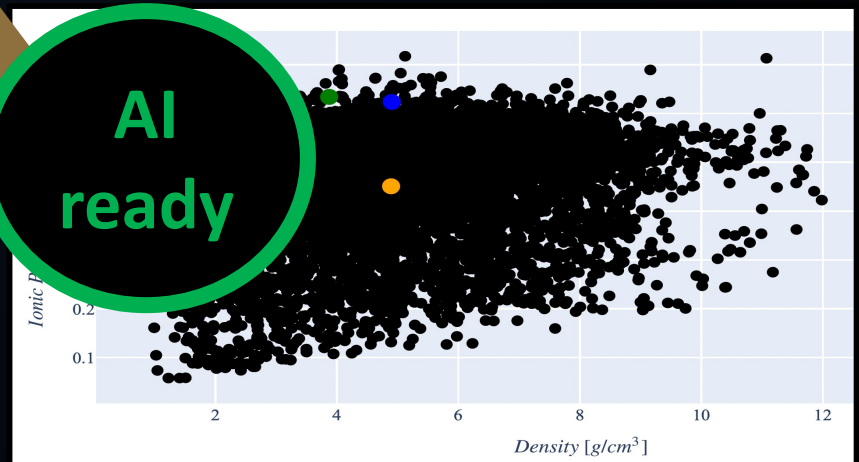
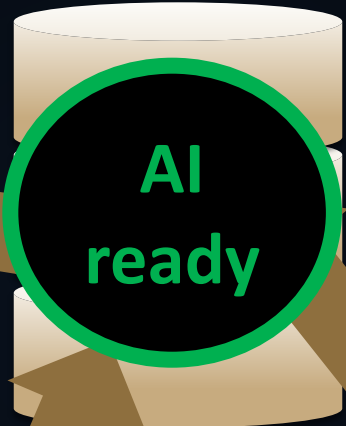
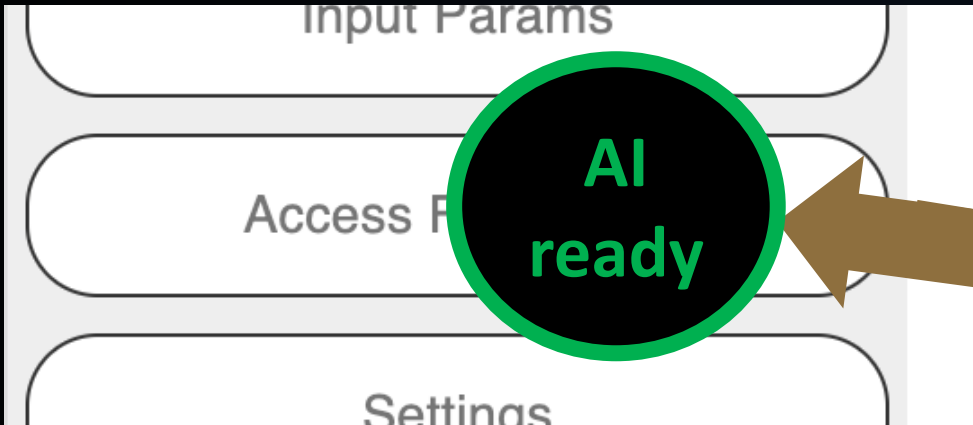


The Materials Project  
ResultsDB



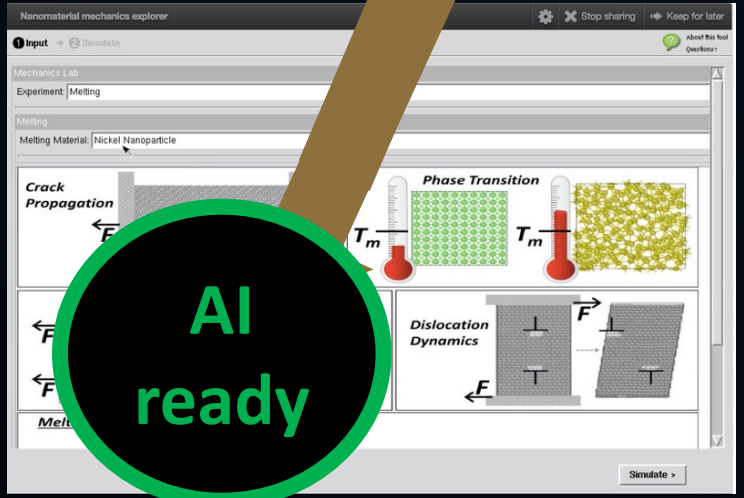
Ionic packing fraction:

$$IPF = \frac{\sum \frac{4}{3} \pi R_i^3}{(a \times b) \cdot c}$$

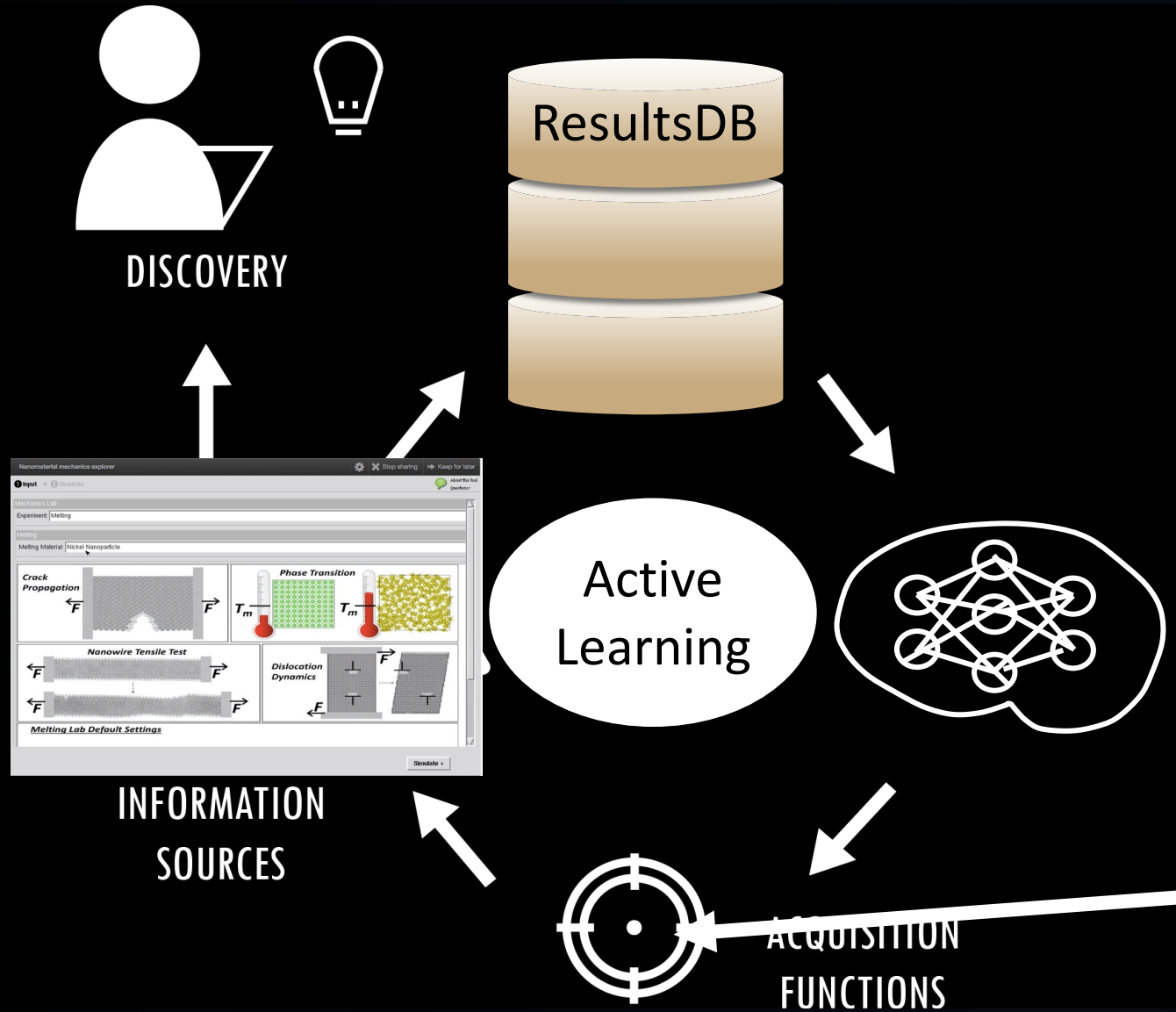


Sophomore-level class  
Compute and visualize  
properties for 65,000 oxides  
Materials discovery

```
Projects — vi .//Semicond/MoTe2Crack/Crack/monolayer-MoTe2-hex.in — 104x45
units      real
atom_style full
boundary   p p s
box
region
create_box 2 box
lattice
create_atoms 1 single 0.0 0.0 0.5 units lattice
create_atoms 2 single 0.3333 0.3333 0.7003 units lattice
create_atoms 2 single 0.3333 0.3333 0.2997 units lattice
mass       1 97.9055000
           2 129.9067000
replicate  30 30 1
pair_style reax/c lmp_control checkqeq yes
pair_coeff  * *ffield-MoTeCu Mo Te
timestep   0.5
thermo_style custom etotal pe ke temp evdwl press pxx pyy pzz pxy pxz pyz lx ly lz
thermo_modify flush yes
thermo     10
variable   ti equal 300.0
dump       1 all custom 100 traj.dump id type x y z q
fix        0 all qeq/reax 1 0.0 10.0 1.0e-6 reax/c
minimize   1.0e-8 1.0e-8 100 1000
velocity   all create $(ti) 4928459 mom yes rot yes dist gaussian
fix        1 all nvt/sllod temp $(ti) 5 $(ti) 100.0
fix        2 all deform 1 x erate 0.000002 remap v units box
run        100000
```

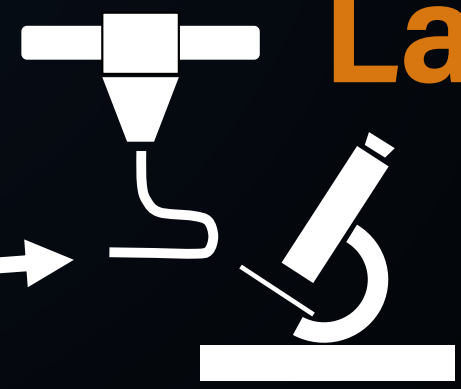


# FAIR Data & AI => the Lab of the Future



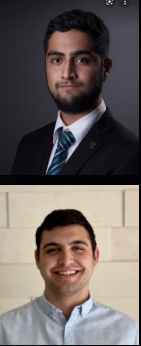
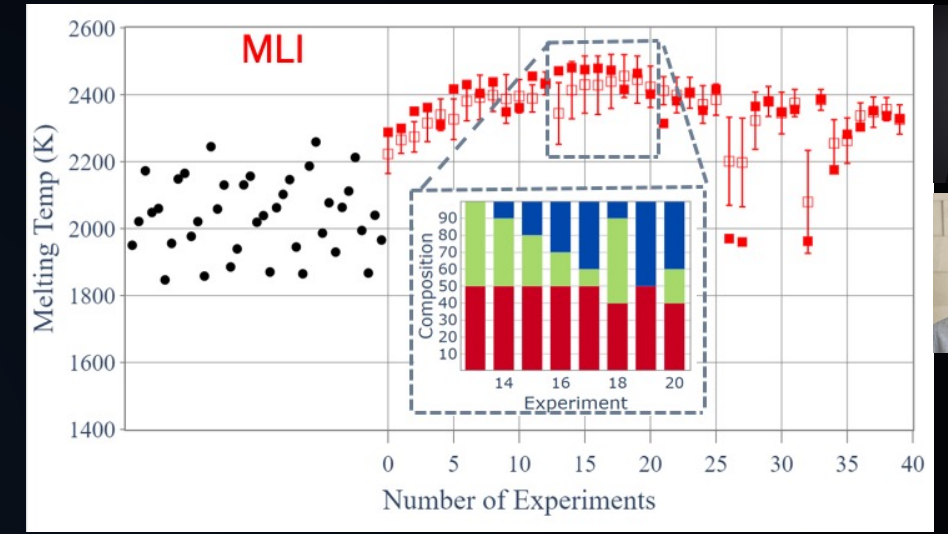
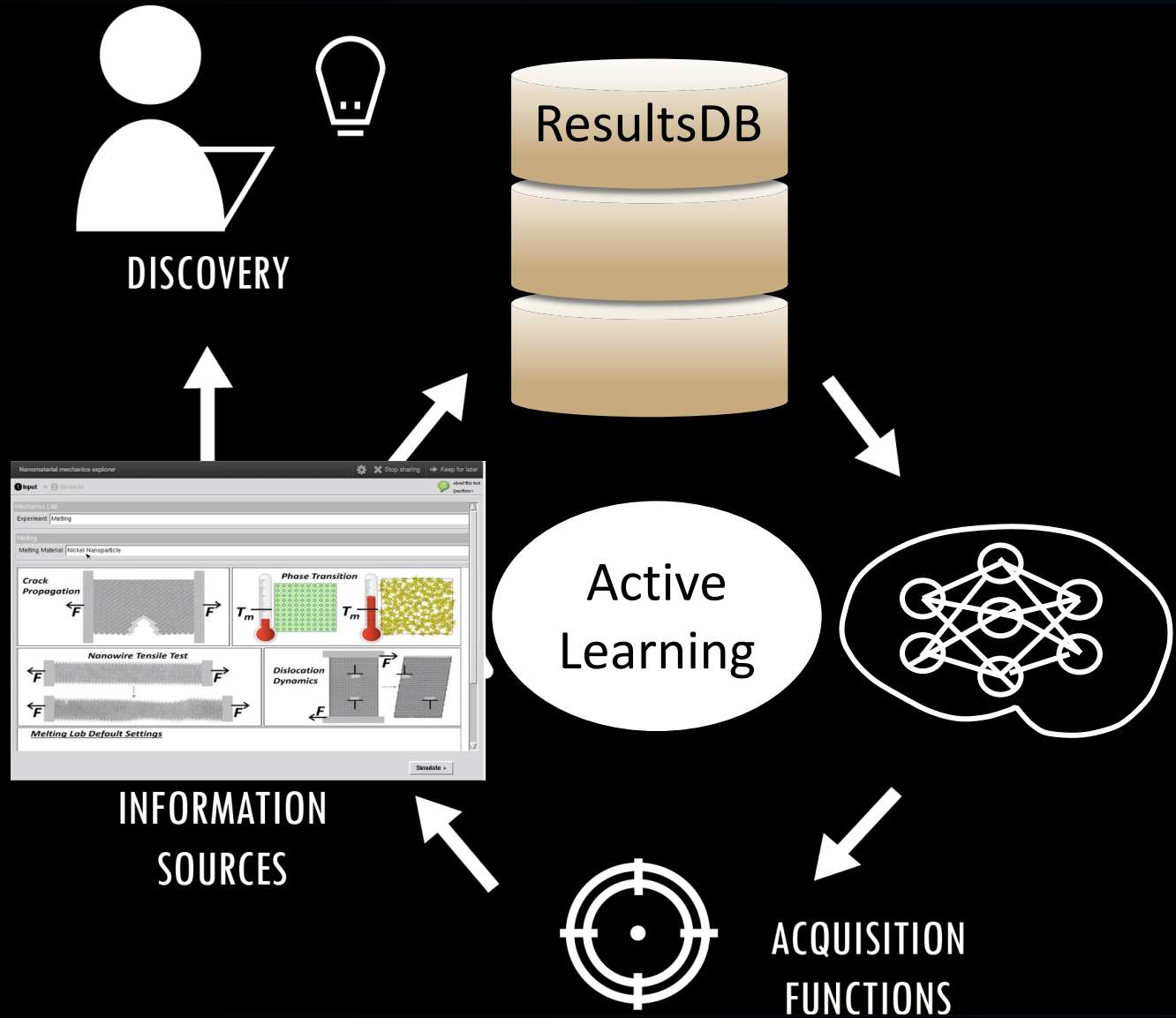
**Instrumented**

**Labs!**

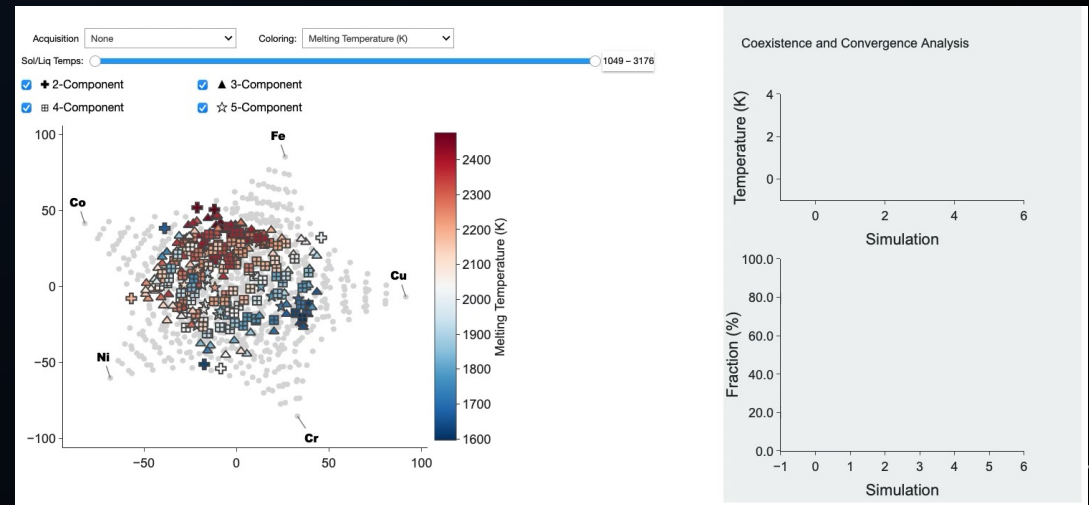


# FAIR Data & AI => the Lab of the Future

Discover the alloy with the highest melting temperature



Automatic FAIR data & data exploration tools



# Simple Access to Complex Tools



## Devices

20 to 1

MOSFET: 11,300 Users, 227,000 jobs

MUGfet: 3,846 Users, 52,619 jobs

MOSCAP: 9,010 Users, 123,728 jobs

PN junction: 24,012 Users, 249,178 jobs

BJT: 5,084 Users, 41,433 jobs

Drift-Diffusion: 5,873 Users, 75,705 jobs



## Simple Access & Exploration

xx.x #param1

yy.y #param2

zz.z #param3

... #ParamX

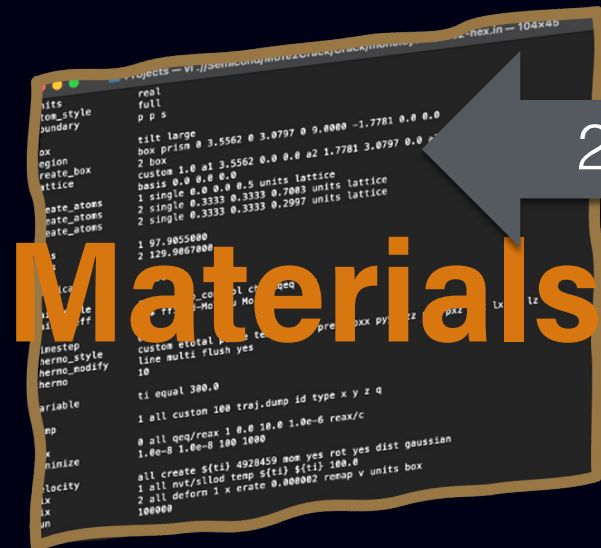
... #ParamX

... #ParamX

... #ParamX

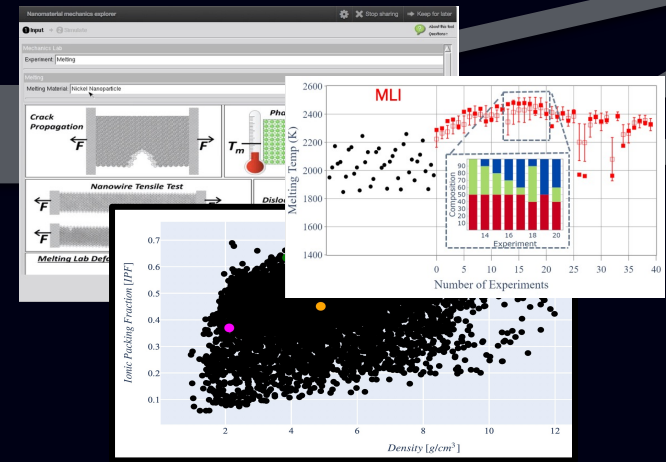
... #ParamX

ResultsDB



20 to 1

## Materials



# Simple Access to Complex Tools

Industrial Reality

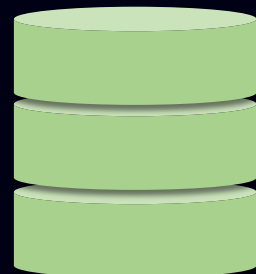
Simplified  
Optimization



Simple Access  
& Exploration

ResultsDB

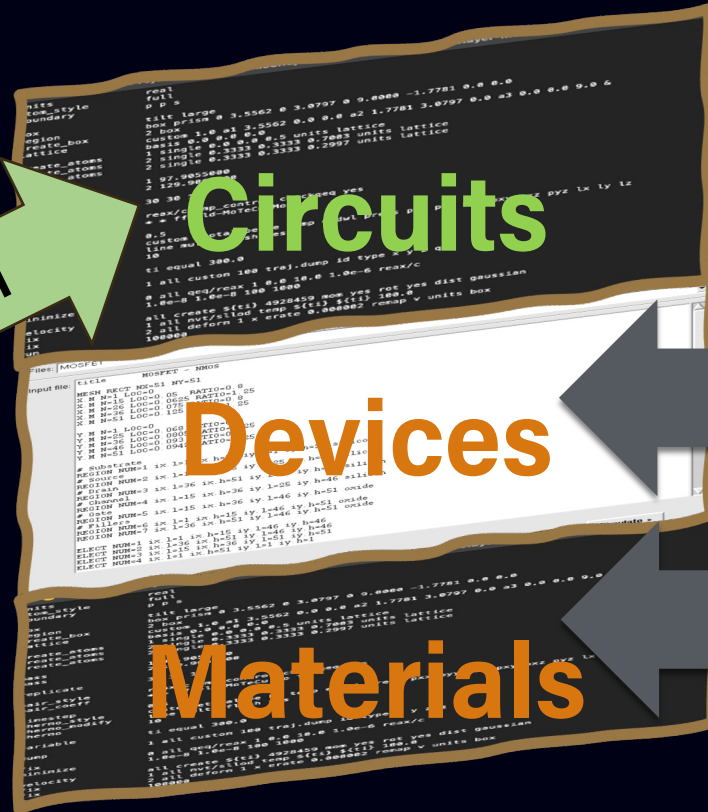
1 engineer  
designs a "flow"



```
45.0 #param1  
60.0 #param2  
1.0 #param3  
... #ParamX
```

20 engineers  
optimize

20 to 1



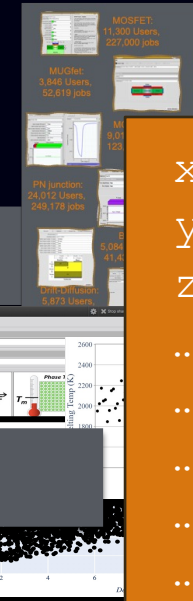
Circuits

Devices

Materials

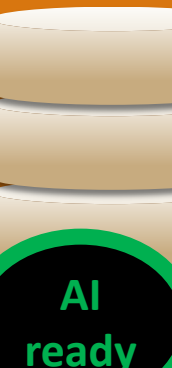
20 to 1

20 to 1



```
xx.x #param1  
yy.y #param2  
zz.z #param3  
... #ParamX  
... #ParamX  
... #ParamX  
... #ParamX  
... #ParamX
```

Results



AI  
ready

# Simple Access to Complex Tools

Industrial Reality

Simplified  
Optimization

**SILVACO** **SYNOPSYS**

**SIEMENS** **cadence**

Pack. / Syst.

Architecture

Circuits

Devices

Materials



Simple Access  
& Exploration

ResultsDB

1 engine

designs

20 to 1

20 to 1

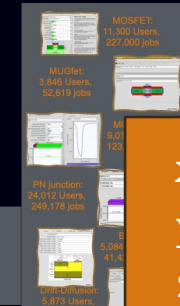
20 to 1

20 to 1

20 to 1

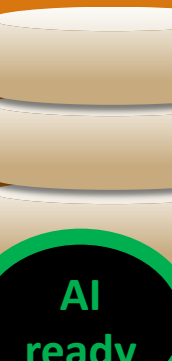
```
45.0 #param1
60.0 #param2
1.0 #param3
... #ParamX
```

20 engineers  
optimize



```
xx.x #param1
yy.y #param2
zz.z #param3
... #ParamX
... #ParamX
... #ParamX
... #ParamX
... #ParamX
```

Results



AI ready



# 50,000 more Engineers Needed!

All need to understand the whole stack!

Not everyone must be a full design expert!

Industrial Reality

1 engineer designs a "flow"

20 engineers optimize

Pack. / Syst.

Architecture

Circuits

Devices

Materials

SYNOPSYS

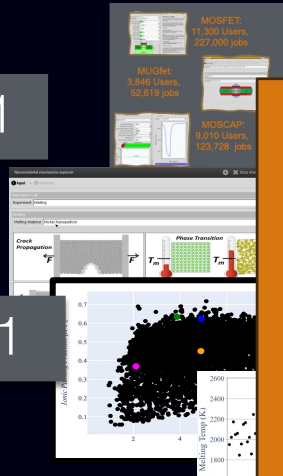
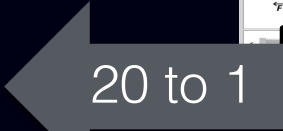
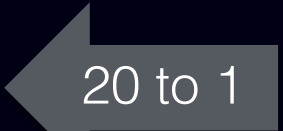
cadence

SIEMENS

SILVACO

nanoHUB

chipsHub



```
xx.x #param1  
yy.y #param2  
zz.z #param3  
... #ParamX  
... #ParamX  
... #ParamX  
... #ParamX
```

ResultsDB



AI ready

# 50,000 more Engineers Needed!

Industrial Reality

1 engineer designs a "flow"

20 engineers optimize

Pack.

Archite

Circu

Devi

Mate

SYNOPSYS

cadence

SIEMENS

SILVACO

Apps & Tools, & AI & Lectures

by nanoHUB

by chipshub

20 to 1

20 to 1

20 to 1

20 to 1

20 to 1

All need to understand the whole stack!

Apps & AI to teach: Concepts & Optimization

Not everyone must be a full design expert!

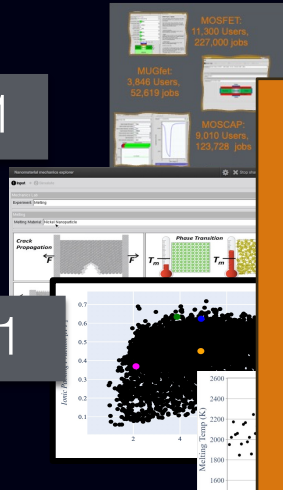
Tools to teach: Detailed Design

```
xx.x #param1  
yy.y #param2  
zz.z #param3  
... #ParamX  
... #ParamX  
... #ParamX  
... #ParamX
```

ResultsDB



AI ready



# Hands-on Data Science and Machine Learning Training Series

The screenshot shows the nanoHUB website header with navigation links: RESOURCES, EXPLORE, NANOHUB-U, PARTNERS, COMMUNITY, ABOUT, SUPPORT, DONATE, TAKE. Below the header, the breadcrumb trail reads 'Home > Groups > Hands-on Learning'. The main heading is 'Hands-on Learning Modules on Data Science and Machine Learning in Engineering'.

## Knowledge and Skills

### DATA HANDLING

Data collection, completeness, and provenance

Module 1

Module 2

Data storage and sharing

Module 1

Module 2

Data querying, organization, and filtering

Module 2

### PREDICTIVE MODELING

Data visualization

Module 2

Module 3

Digital representation and description for materials

Module 1

Module 4

### DECISION MAKING

Uncertainty quantification

Module 1

Module 2

Module 3

Module 4

**3,000+ students**

**Apps & Tools, & AI & Lectures**

**This week:  
AI & Schrodinger (commercial vendor)  
375 attendees!**

For undergraduate students

<https://nanohub.org/groups/mlmodules>

The screenshot shows the nanoHUB website header with navigation links: RESOURCES, EXPLORE, NANOHUB-U, PARTNERS. The main heading is 'Data Science and Machine Learning'.

## Summer 2021 Series

### 23. Debugging Neural Networks

August 11th 2021, 1:30 PM - 2:30 PM EST

Rishi Gurnani, PhD student, Ramprasad Group, Georgia Institute of Technology,

[Access resource](#)

### 22. A Machine Learning aided hierarchical screening strategy for materials discovery

June 21st 2021, 1:30 PM - 2:30 PM EST

Anjana Talapatra, Postdoctoral Fellow, Los Alamos National Laboratory, Online.

[Access resource](#)

### 20. Batch Reification Fusion Optimization (BAREFOOT) Framework

June 16th 2021, 1:30 PM - 2:30 PM EST

A. Doan and Garvit Agarwal, Argonne National Laboratory, Online.

[Abstract >](#)

[Access resource](#)

### 20. Batch Reification Fusion Optimization (BAREFOOT) Framework

June 2nd 2021, 1:30 PM - 2:30 PM EST

Richard Couperthwaite, Texas A&M University, Online.

[Abstract >](#)

[Access resource](#)

For researchers


<https://nanohub.org/groups/ml/handsontaining>

# nanoHUB partners in workforce development

POWERED BY nanoHUB

Register Login Request Membership Help

Home About Internships Research Opportunities Lecture Series Courses Simulation and CAD Tools Calendar



## SCALE (Scalable Asymmetric Lifecycle Engagement)

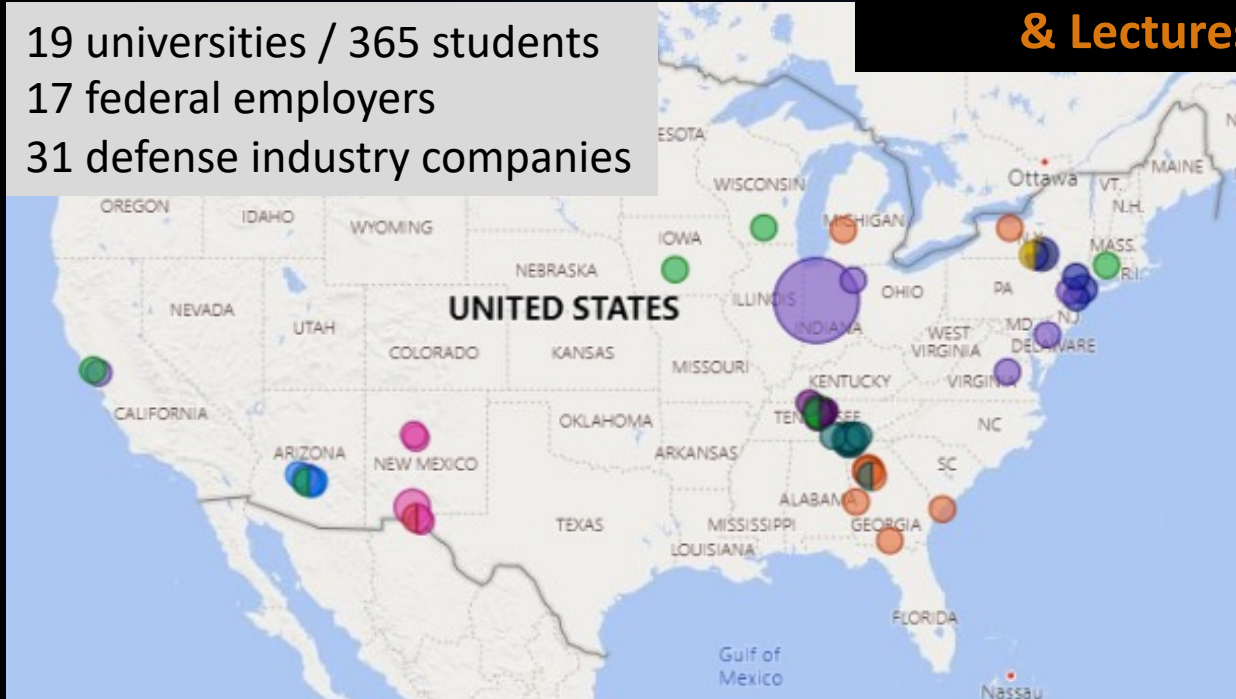
SCALE is the preeminent U.S. program for semiconductor workforce development in the defense sector.

Led by Purdue University, funded by the Department of Defense and managed by NSWC Crane, SCALE facilitates a different approach to training highly-skilled U.S. microelectronics engineers, hardware designers, and manufacturing experts, ensuring U.S. leadership in this important area.

300+ students have been impacted by SCALE.

**Apps & Tools, & AI & Lectures**

19 universities / 365 students  
17 federal employers  
31 defense industry companies



## Undergraduate students + K-12

-  Learn more about SCALE
-  Industry and National Lab Internships
-  Research Opportunities
-  Lecture Series
-  Courses
-  Simulation and CAD Tools
-  Teaching Materials
-  For SCALE PIs

# nanoHUB partners in workforce development

## SCALE: Undergraduate students + K-12

**Apps & Tools, & AI & Lectures**

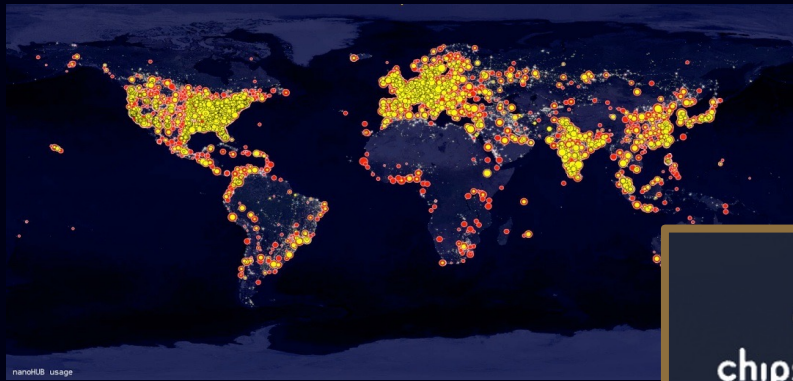
## MEST: working professionals (government & contractors)

**Ease of Use!  
Community Building!**

## With our technology, content & community:

We ...

- ... enable new groups of researchers!
- ... use research tools in education!
- ... publish data & tools in a new way!
- ... changed expectations and approaches!
- ... built a global community!



**170+ courses, 6500+ content items**

**15+ million visitors**

**700+ tools and apps**

**250,000+ simulation users**

**2,750**

**citations**

**55%**

**in classes**

**WEB OF SCIENCE**



Chipshub Questions - Can we ...

- ... empower faculty and students?
- ... get from class to lab to fab?

**Chipshub approach:**

**Ease of Use!**

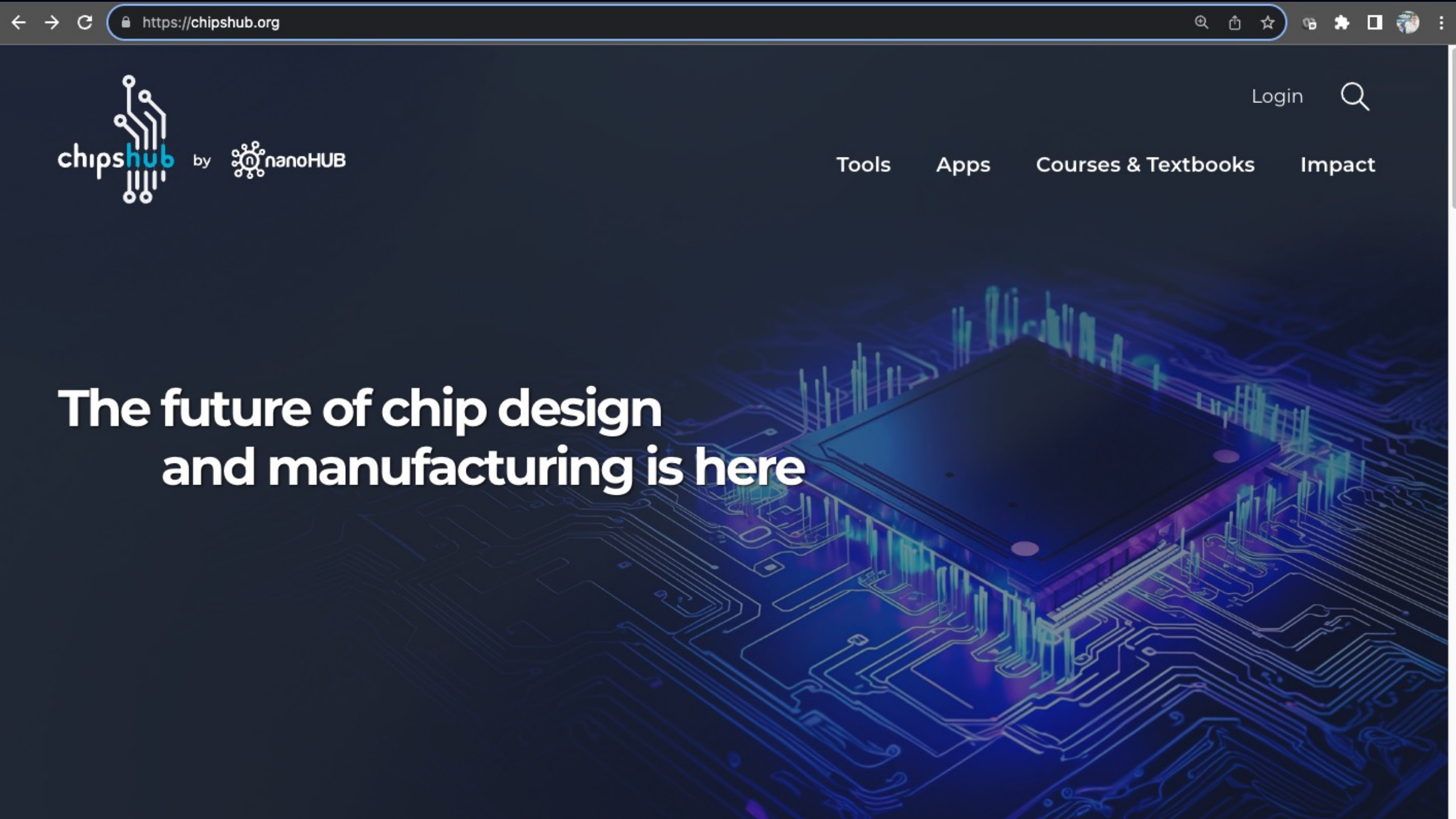
**Community Building!**



Login 🔍

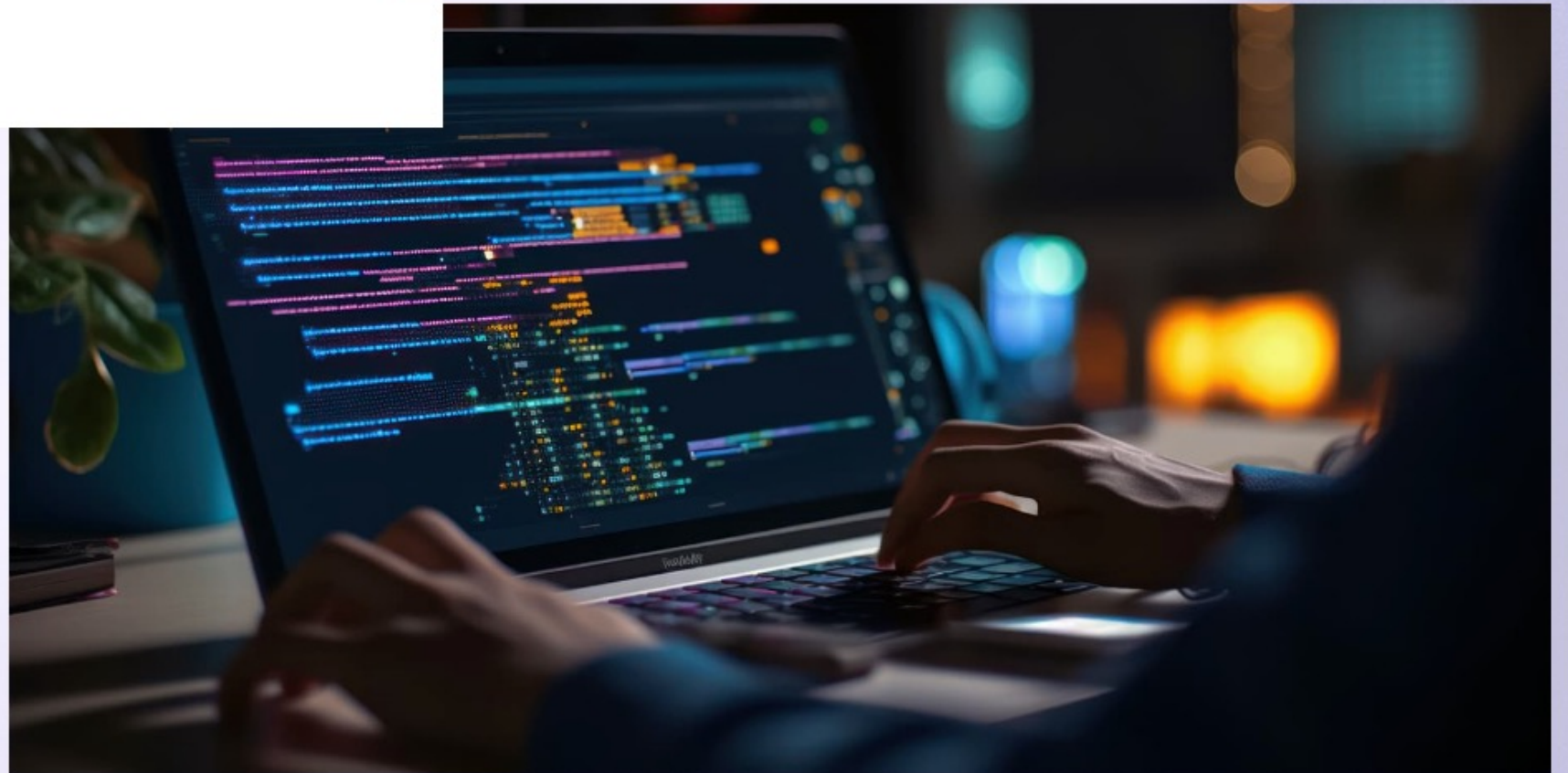
- Tools
- Apps
- Courses & Textbooks
- Impact

# The future of chip design and manufacturing is here

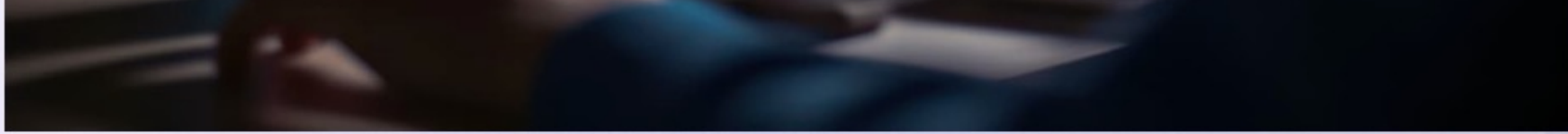


# Tools that transform ideas into chips

Browse tools [→](#)







# Easy to use apps to learn and explore

← Get started with apps



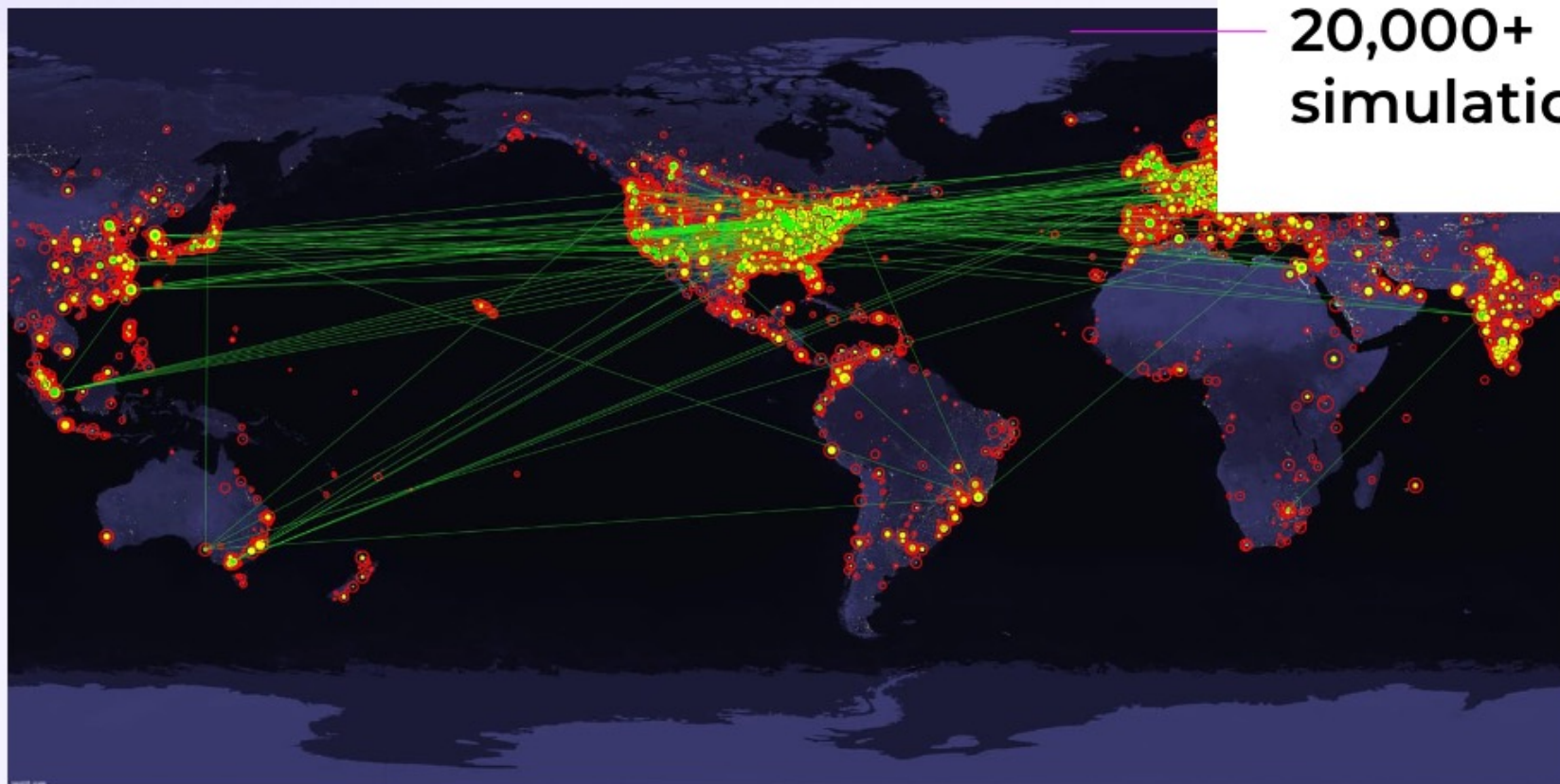
## Free courses and textbooks

Explore courses [→](#)





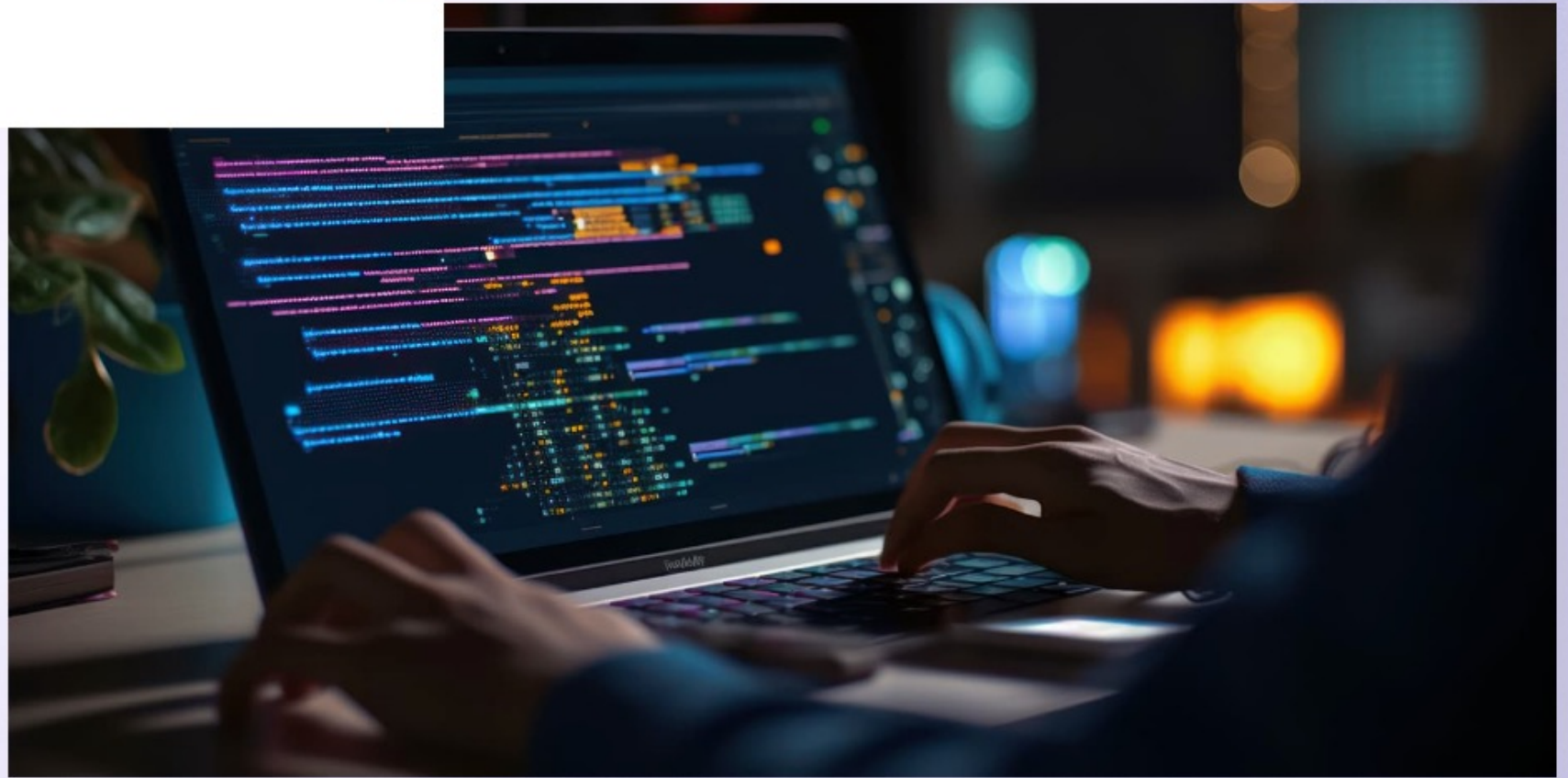
A global platform serving  
20,000+  
simulation users per year



← View our impact

## Tools that transform ideas into chips

Browse tools [→](#)



Easy to use apps



Login

Tools Apps Courses & Textbooks Impact

# Tools that transform ideas into chips

Chipshub is a central place with access to a variety of expert-level tools that can be used in the chip design process. Spend your time working rather than struggling with code installation.

## Available now:



SILVACO Semiconductor Process and Device Simulation for Educational Purposes Only



The Thermo-Calc Software Educational Package is intended for teaching and learning basic thermodynamics and kinetic theory at an undergraduate level. This is achieved through a cooperation with Professors Mats Hillert and Malin Selleby from the department of Materials Science and Engineering at KTH Royal Institute of Technology, Stockholm, Sweden and Thermo-Calc Software AB.



Schrödinger's Materials Science platform integrates predictive physics-based simulation with machine learning techniques to accelerate materials design and Schrödinger's AutoQSAR for Machine Learning educational tool is implemented on nanoHUB.

# SILVACO

SILVACO Semiconductor Process and Device Simulation  
for Educational Purposes Only



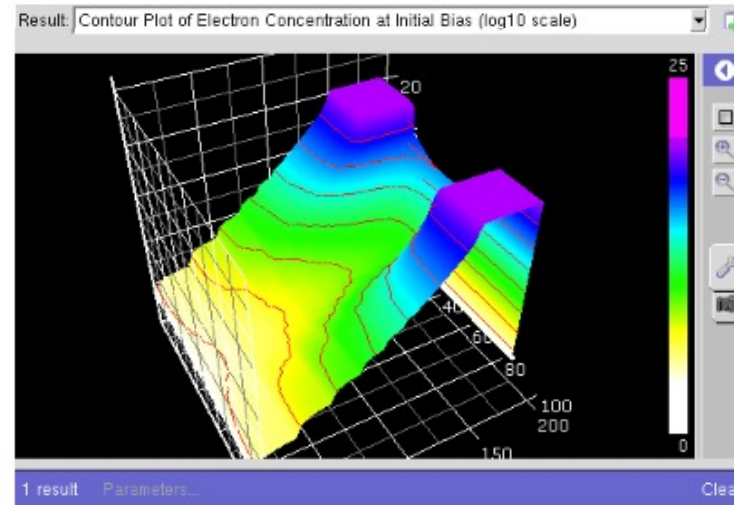
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Schrödinger's Materials Science platform integrates predictive physics-based simulation with machine learning techniques to accelerate materials design and Schrödinger's AutoQSAR for Machine Learning educational tool is implemented on nanoHUB.

## From Bell Labs -

- [Padre](#) is a 2D/3D simulator for electronic devices
- [Prophet](#) provides a framework to solve systems of partial differential equations (PDEs) in time and 1, 2, or 3 space dimensions



Forthcoming tools:

cādence®

CHIPYARD

efabless.com

SYNOPTIS®

# SILVACO

SILVACO Semiconductors  
for Educational Purposes



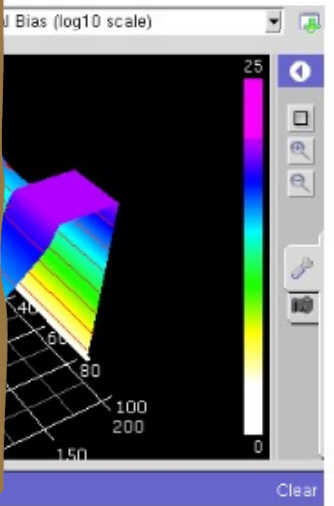
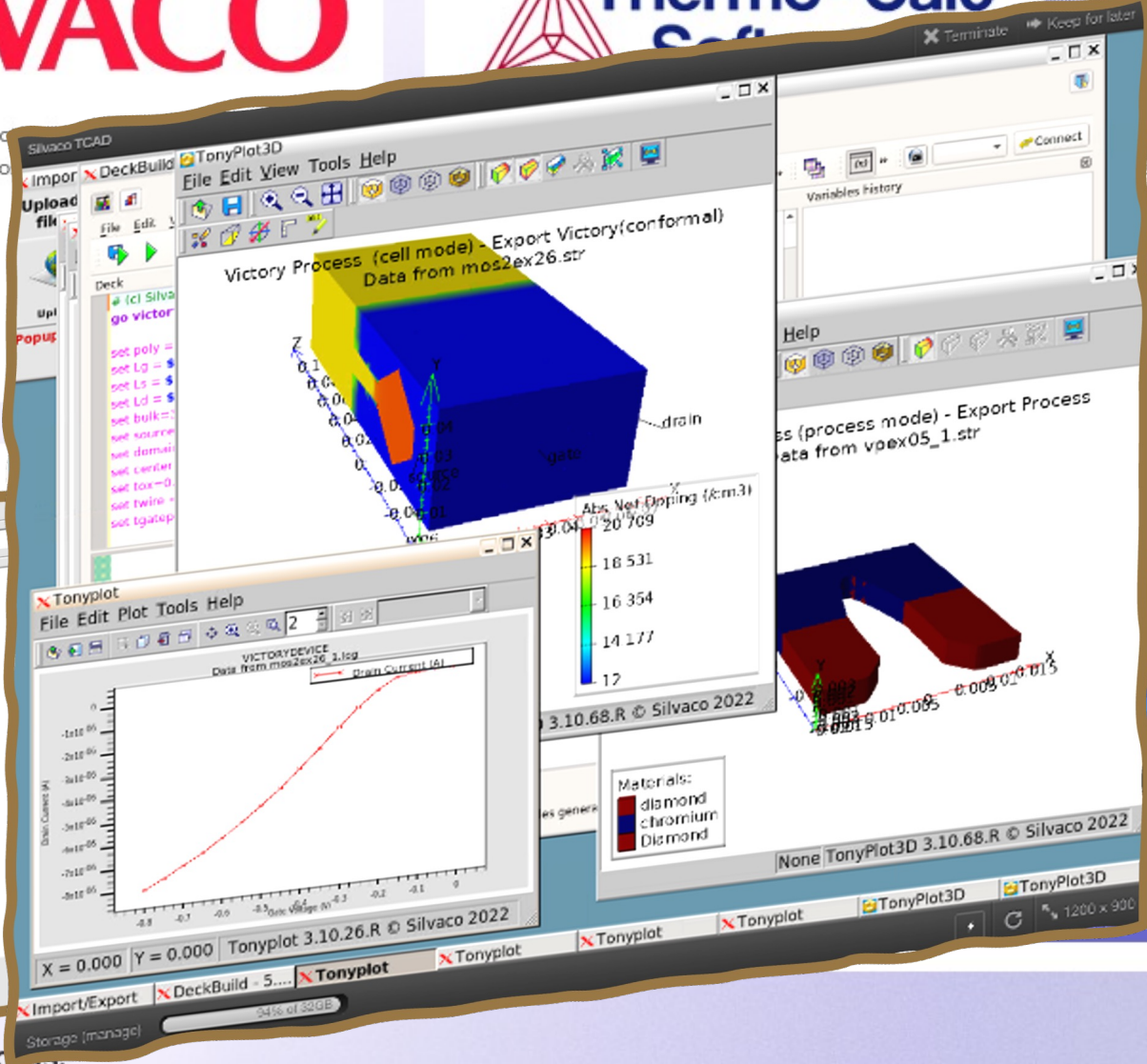
# Thermo-Calc



# Schrödinger

Schrödinger's Materials Science platform integrates predictive physics-based simulation with machine learning techniques to accelerate materials design and Schrödinger's AutoQSAR for Machine Learning educational tool is implemented on nanoHUB.

```
Input file: MOSFET
title MOSFET - NMOS
MESH RECT NX=51 NY=51
X M N=1 LOC=0
X M N=15 LOC=0.05 RATIO=0.8
X M N=25 LOC=0.0625 RATIO=1.25
X M N=36 LOC=0.075 RATIO=0.8
X M N=36 LOC=0.125 RATIO=1.25
X M N=51 LOC=0.125 RATIO=1.25
Y M N=1 LOC=0
Y M N=25 LOC=0.068 RATIO=0.8
Y M N=36 LOC=0.0805 RATIO=1.25
Y M N=46 LOC=0.093 RATIO=0.8
Y M N=51 LOC=0.0942 RATIO=1.25
# Substrate
REGION NUM=1 ix 1-1 ix h=51 iy 1-1 iy h=25 silicon
# Source
REGION NUM=2 ix 1-1 ix h=15 iy 1-25 iy h=46 silicon
# Drain
REGION NUM=3 ix 1-36 ix h=51 iy 1-25 iy h=46 silicon
# Channel
REGION NUM=4 ix 1-15 ix h=36 iy 1-25 iy h=51 oxide
# Gate
REGION NUM=5 ix 1-15 ix h=36 iy 1-46 iy h=51 oxide
# Fillers
REGION NUM=6 ix 1-1 ix h=15 iy 1-46 iy h=51 oxide
REGION NUM=7 ix 1-36 ix h=51 iy 1-46 iy h=51 oxide
ELECT NUM=1 ix 1-1 ix h=15 iy 1-46 iy h=46
ELECT NUM=2 ix 1-36 ix h=51 iy 1-46 iy h=46
ELECT NUM=3 ix 1-15 ix h=36 iy 1-51 iy h=51
ELECT NUM=4 ix 1-1 ix h=51 iy 1-1 iy h=1
```



Forthcoming to...

cādence®

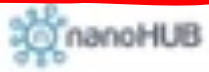
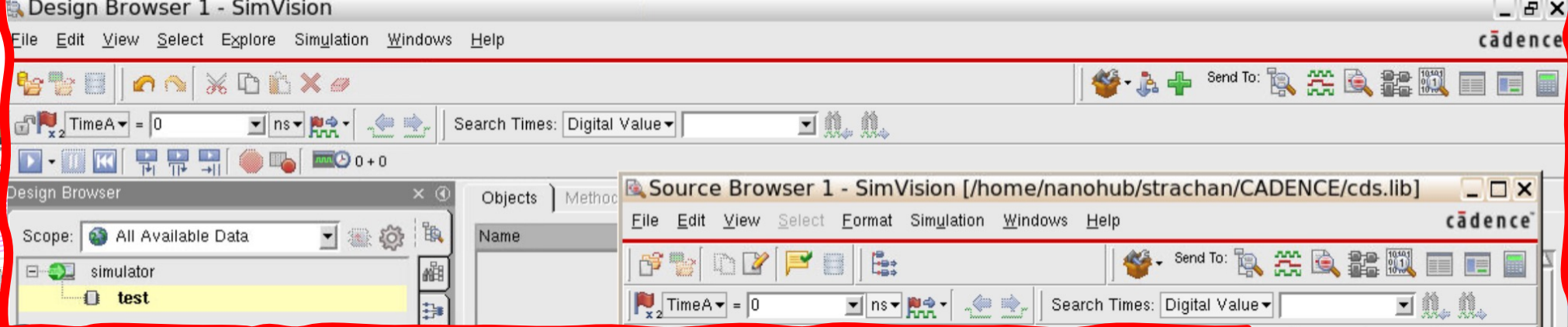
CHIPYARD

efabless.com

SYNOPTIS®

# SILVACO

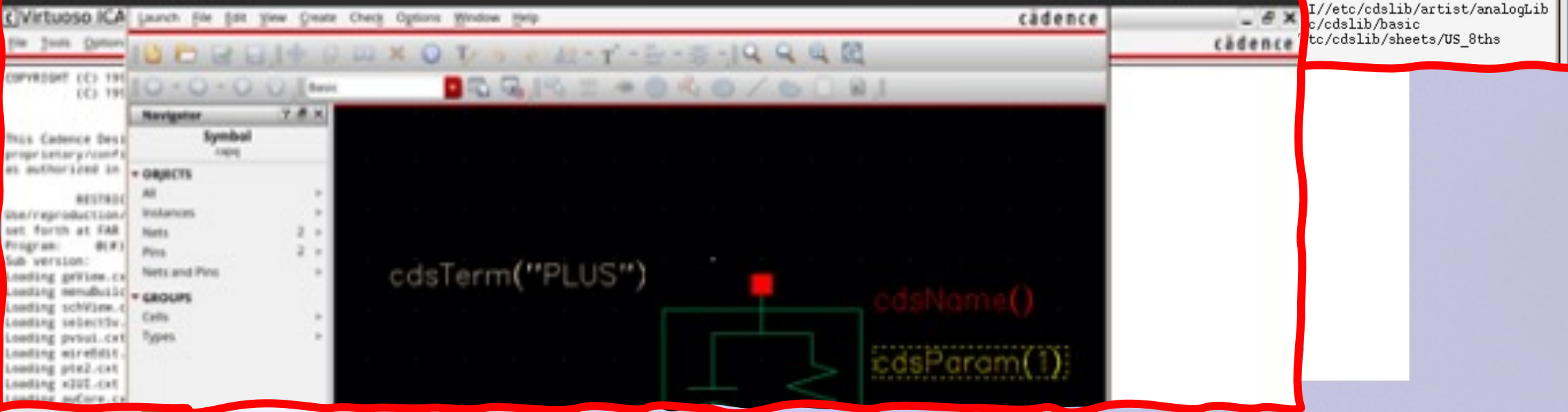
SILVACO Semiconductors  
for Educational Purposes



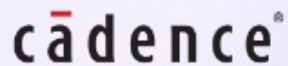
EXPLORE PUBLISH COMMUNITY ABOUT SUPPORT

Cadence analog device simulation

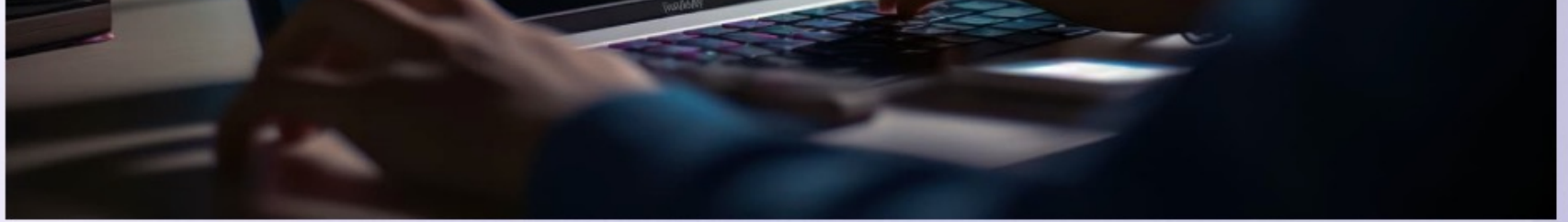
```
Input file: MOSFET
title MOSFET
MESH RECT NC=51 X
X M N=1 LOC=0
X M N=15 LOC=0 05
X M N=15 LOC=0 06
X M N=26 LOC=0 07
X M N=36 LOC=0 07
X M N=51 LOC=0 12
Y M N=1 LOC=0
Y M N=25 LOC=0 06
Y M N=36 LOC=0 07
Y M N=46 LOC=0 07
Y M N=51 LOC=0 12
# Substrate
REGION NUM=1 ix. 1
# Source
REGION NUM=2 ix. 1
# Drain
REGION NUM=3 ix. 1
# Channel
REGION NUM=4 ix. 1
# Gate
REGION NUM=5 ix. 1
# Fillers
REGION NUM=6 ix. 1
REGION NUM=7 ix. 1
ELECT NUM=1 ix. 1
ELECT NUM=2 ix. 1
ELECT NUM=3 ix. 1
ELECT NUM=4 ix. 1
```



Forthcoming tools:







## Easy to use apps to learn and explore

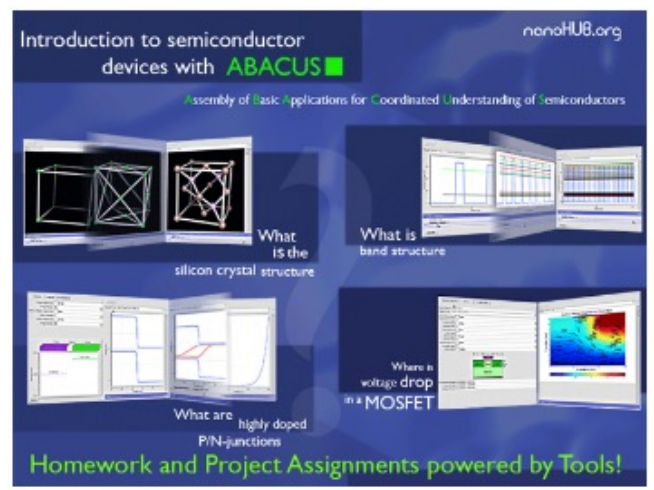
← Get started with apps



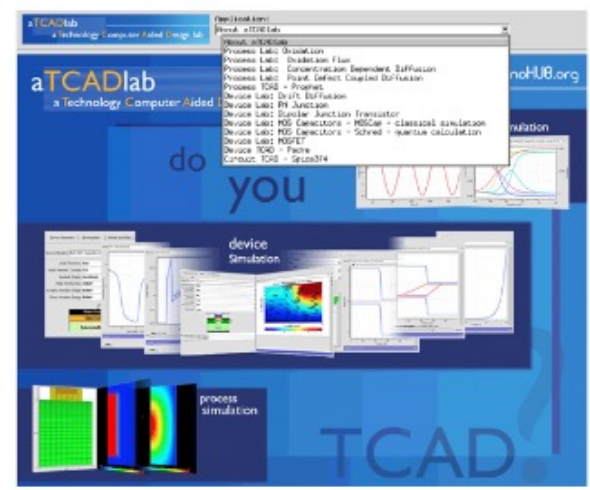


# Easy to use apps to learn and explore

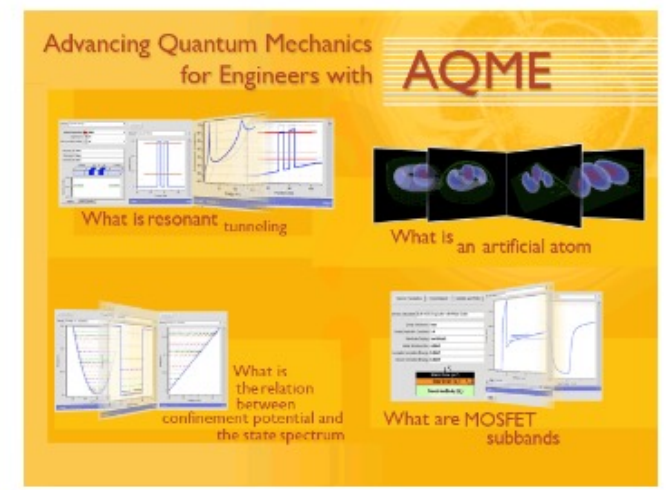
Simple apps that focus on user experience and delivery of modeling results.  
No software installation needed and a gentle learning curve.  
Used by 90,000+ students around the world.



Semiconductor Device Fundamentals with ABACUS



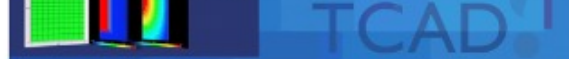
Introduction to TCAD Simulation with aTCADlab



Advancing Quantum Mechanics for Engineers with AQME

## Semiconductor Device Fundamentals with ABACUS

ABACUS is a set of tools that have been used by hundreds of classes to enable students to explore the fundamental devices that are taught in typical undergraduate and graduate level courses.



## Introduction to TCAD Simulation with aTCADlab

nanoHUB tools ranging from process simulation, over device simulation to circuit simulation.

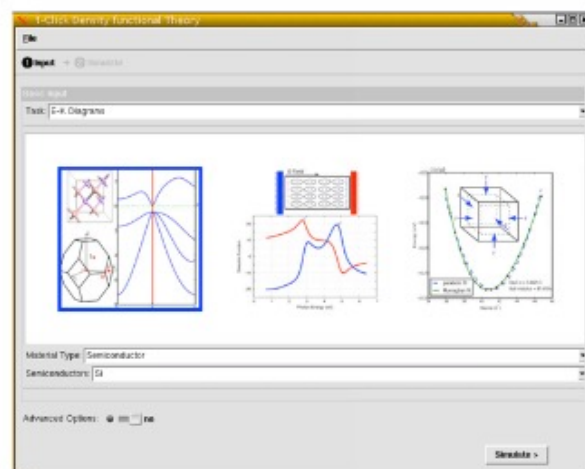
## Advancing Quantum Mechanics for Engineers with AQME

The AQME toolbox holds a set of easily employable tools appropriate for teaching a quantum mechanics class in either engineering or physics.



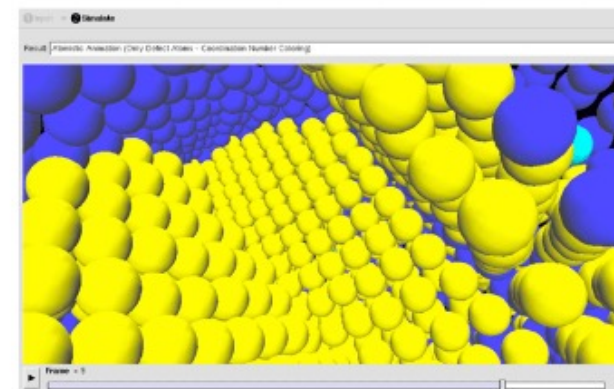
## Virtual Reality Immersive Learning in vFabLab™

nanoHUB is partnering with vFabLab™ to enable students at all educational levels to learn about real semiconductor device processing tools. Currently vFabLab™ users have to sign up separately from a nanoHUB account.



## DFT Material Properties Simulator

Materials modeling provides a cost and time efficient method for studying their properties, especially in nanotechnology where length and time scales are not accessible experimentally. The tool relies on density functional theory (DFT) calculations to compute specific properties for a wide range of materials including semiconductors, insulators, and metals. The tool can compute electronic band structures, density of states, bulk modulus, dielectric constants and other properties of the material. The user can select from various pre-set materials or create one of their own by specifying the atomic structure.



## Nanomaterial Mechanics Explorer

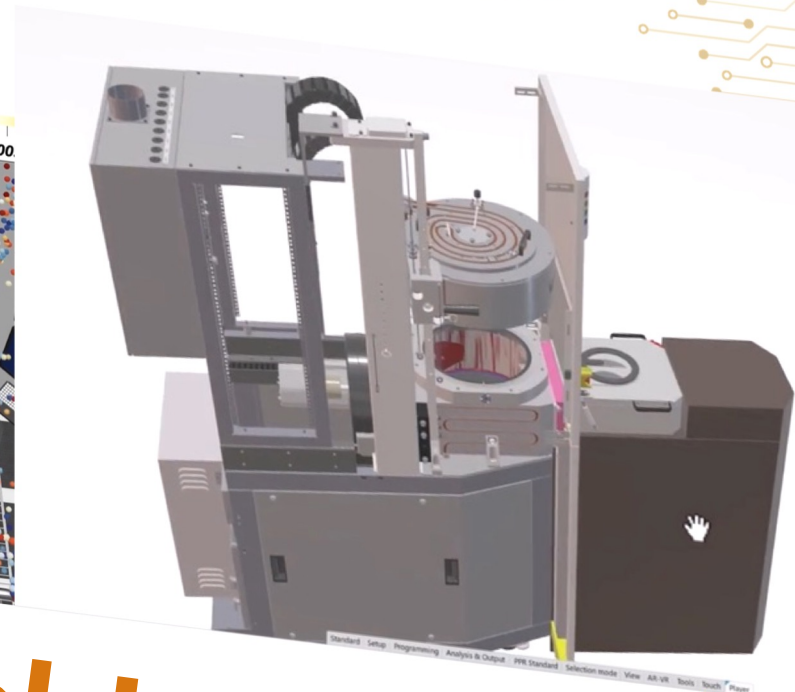
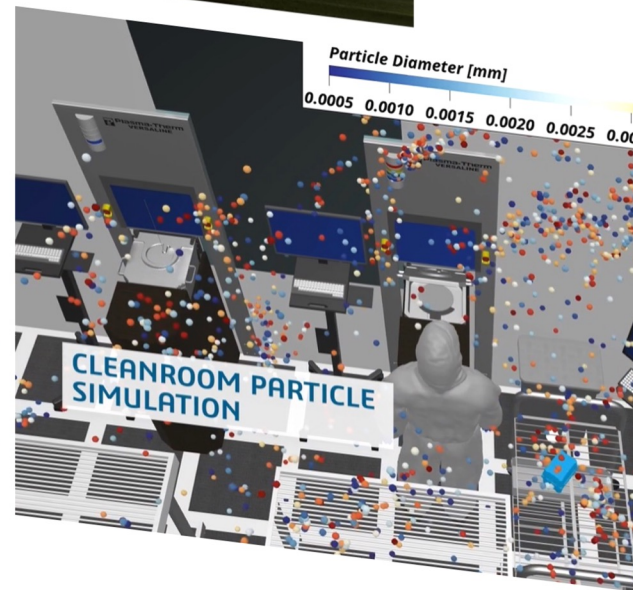
This tool enables users to explore properties of materials from the atomistic scale including dislocation motion, crack propagation, plastic deformation, melting, and martensitic transformation. The tool uses molecular dynamics simulations with pre-built examples and full control of individual simulation parameters for experienced users within advanced options. The tool runs the LAMMPS molecular dynamics code and connects to OpenKIM, a database of interatomic models, enabling simulation of over 30 elements and 50 alloys from more than 180 models, primarily of the embedded-atom method type.

ABACUS is a...  
classes to en...  
that are taug...  
courses.

# Virtualization of Birck Nanotechnology Center



nanoHUB is...  
educational...  
processing...  
separately fro...



# Video at Lunch!



## Free courses and textbooks

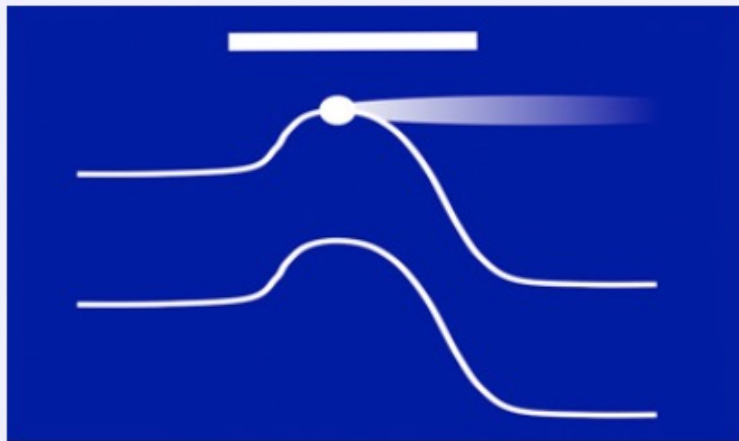
Explore courses [→](#)



# Free courses and textbooks

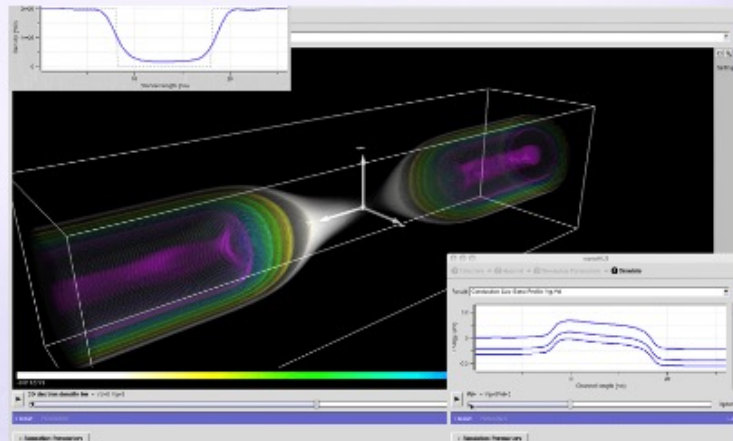
Millions of users annually access our open courseware and experience the next generation of textbooks from leading faculty through a partnership with World Scientific Publishing.

## Open courses



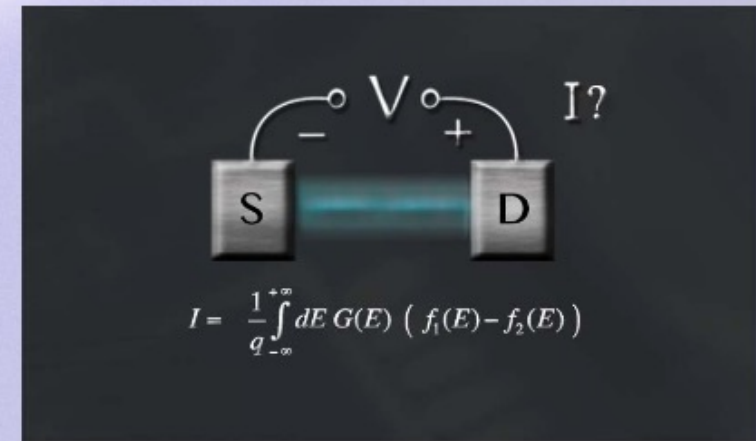
### Fundamentals of Nanotransistors, 2nd Edition

by [Mark Lundstrom](#)



### Solid State Devices I

by [Gerhard Klimeck](#)



### Fundamentals of Nanoelectronics - Part A: Basic Concepts, 2nd Edition

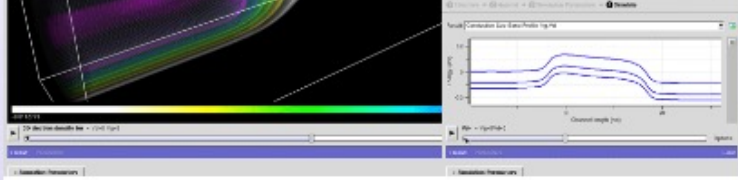
by [Supriyo Datta](#)



## Fundamentals of Nanotransistors, 2nd Edition

by [Mark Lundstrom](#)

Nanotransistors is a self-paced nanoHUB-U offering by Prof. Mark Lundstrom. This course features video lectures, quizzes, and exams. Prof. Lundstrom also provides background resources on the essential physics of nanoscale transistors.



## Solid State Devices I

by [Gerhard Klimeck](#)

Semiconductors are everywhere in human activities, from your credit card to space exploration. This graduate-level introduction brings aspects of physics, chemistry, and engineering together to understand, analyze, and design transistors and solar cells.

$$I = \frac{1}{q} \int_{-\infty}^{+\infty} dE G(E) (f_1(E) - f_2(E))$$

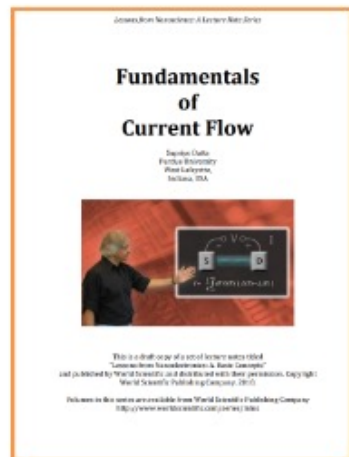
## Fundamentals of Nanoelectronics - Part A: Basic Concepts, 2nd Edition

by [Supriyo Datta](#)

Basic Concepts presents key concepts in nanoelectronics and mesoscopic physics and relates them to the traditional view of electron flow in solids.

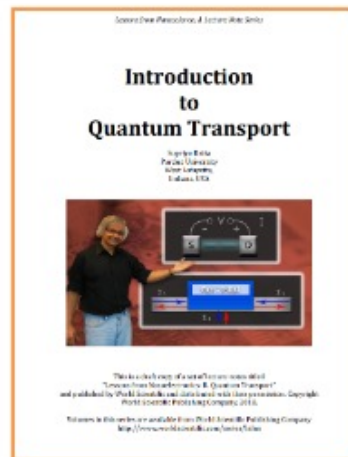
[More courses](#)

## Downloadable textbooks



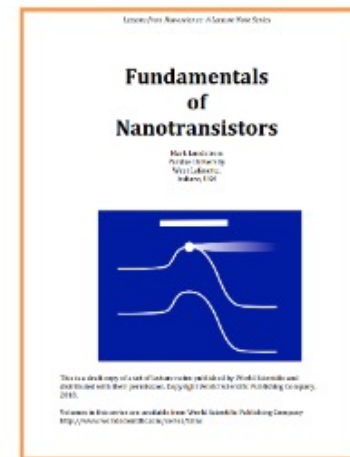
## Fundamentals of Current Flow

by [Supriyo Datta](#)



## Introduction to Quantum Transport

by [Supriyo Datta](#)



## Fundamentals of Nanotransistors

by [Mark Lundstrom](#)



We have ...

- ... 700+ tools and Apps.
- ... 170+ courses, 6500+ content items

# The future of chip design and manufacturing is here

We ...

- ... enable new groups of researchers!
- ... use research tools in education!
- ... publish data & tools in a new way!
- ... changed expectations and approaches!
- ... built a global community!







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## We are not done yet. We need ...

- ... deeper support



- ... PDK vendor engagement



- ... scalable licensing management

- ... tape out partners & "white glove"



- ... commercial cloud partners





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- ... history / background:  


- ... PDK vendor engagement  
 ~1996 Software Portals Emerge  
 Serving small expert groups  
 Not reaching "different" users  
 => begin to have a bad reputation
- ... scalable licensing management  
 2002 NSF funds nanoHUB  
 2005 nanoHUB cloud  
 2005 nanoHUB apps  


- ... tape out partners & "white glove"  
 ... commercial cloud partners  
**Largest academic end-to-end scientific user cloud**



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We are not done yet. We need ...

So... How can we get there?

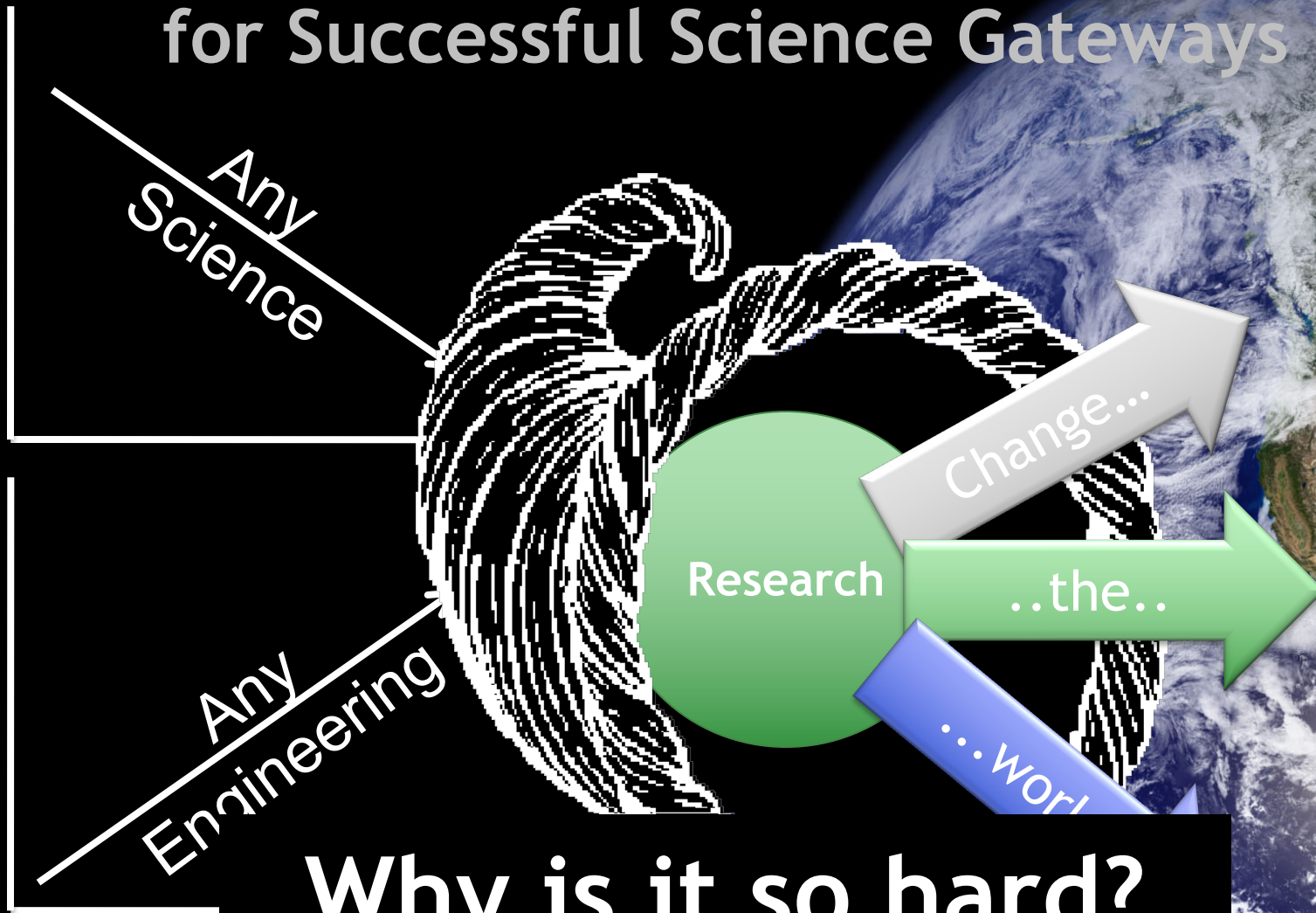
**Just hosting software is not enough!**

**7 Criteria for Successful Science Gateways**

history / background: one  
~1996 Software Portals Emerge  
Serving small expert groups  
Not reaching "different" users  
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2002 NSF funding nanoHUB  
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Largest academic end-to-end scientific user cloud

# 7 Criteria

for Successful Science Gateways



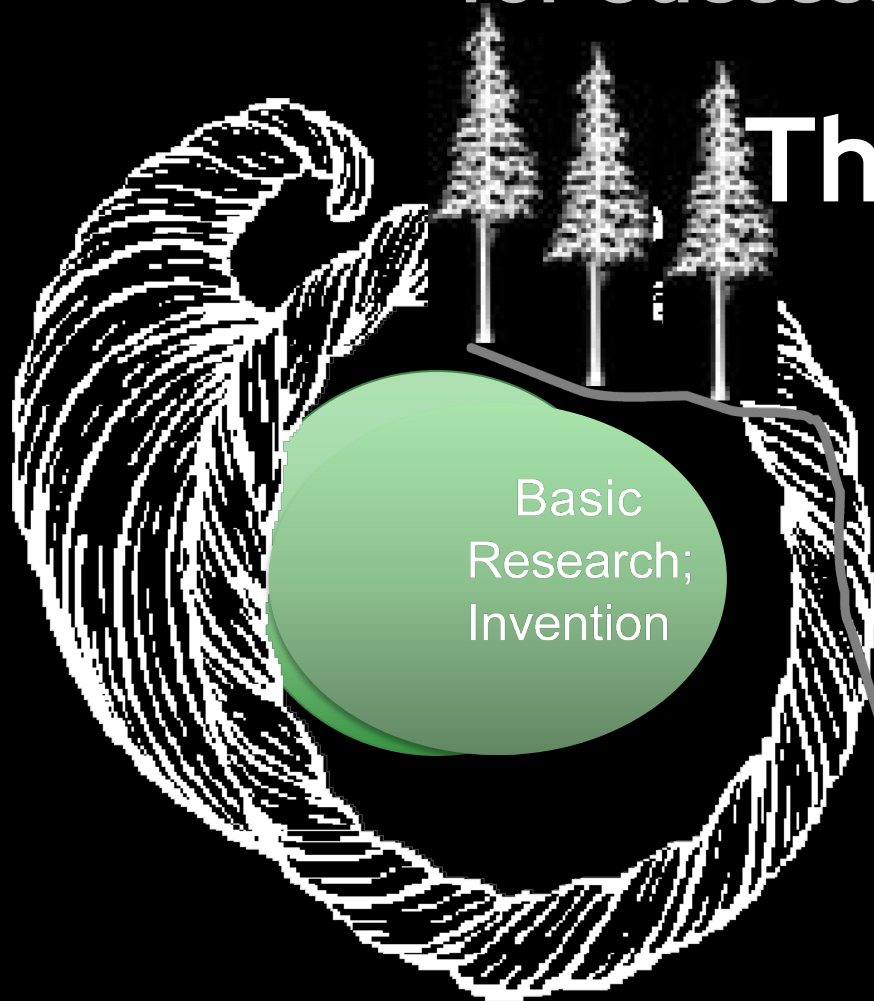
Why is it so hard?

Any Science Gateway's Dream

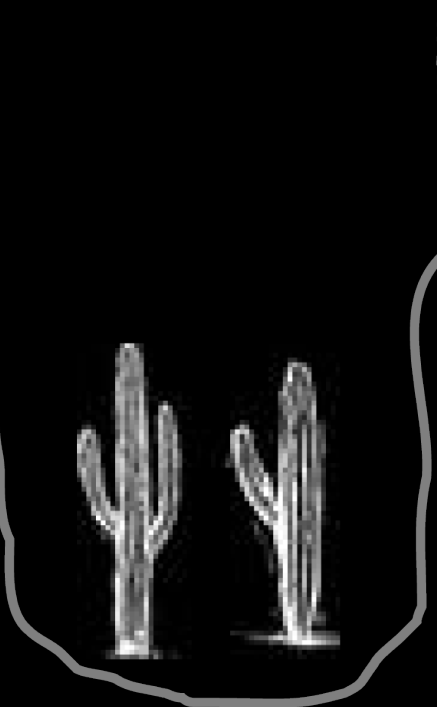
# 7 Criteria

for Successful Science Gateways

There are worlds  
between...



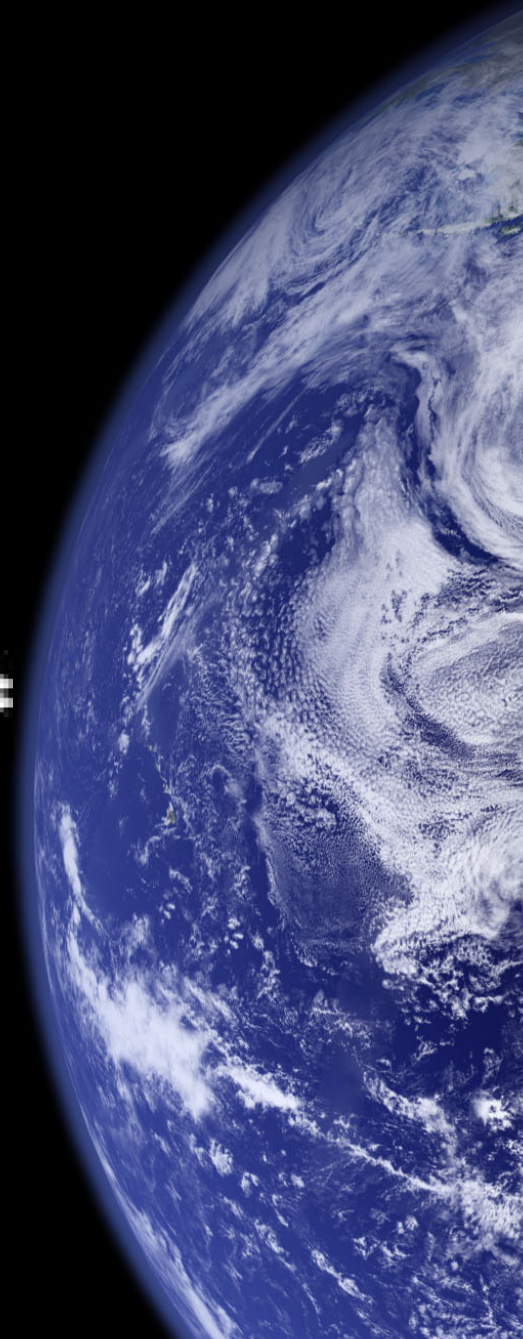
Basic  
Research;  
Invention



"Valley of Death"

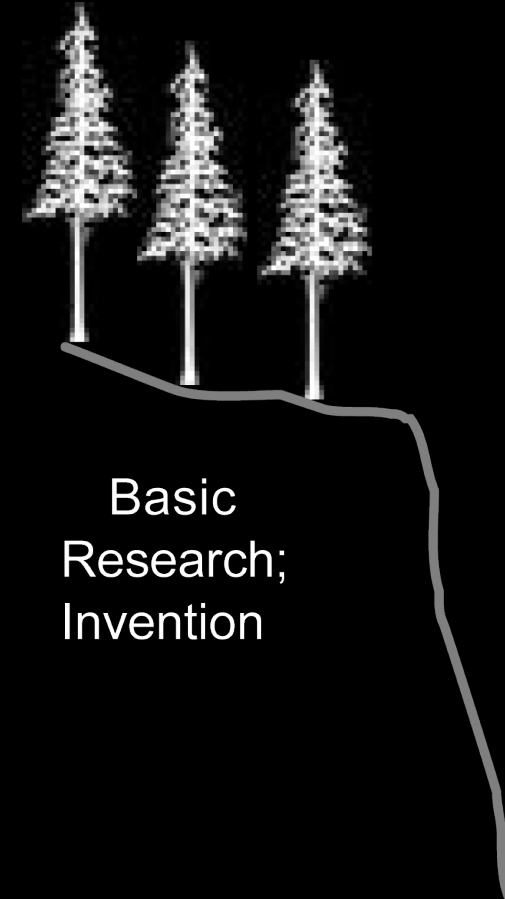
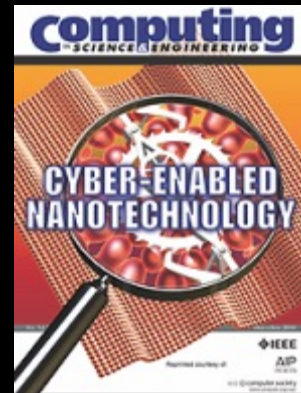
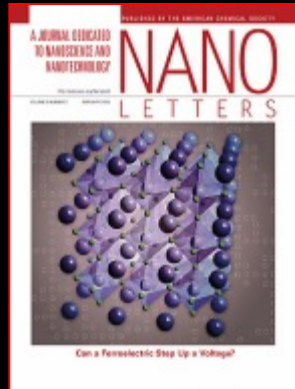


Applied  
Research;  
Innovation



# 1: Outstanding Science / Quality

“Stuff the world wants”



Leveraged Research

**\$5.1M**

Basic  
Research;  
Invention



2011 Data

“Stuff you would use yourself!”

# 2: Commitment to Dissemination

“faculty that want to give it away”

## Building Faculty Incentives

46 faculty

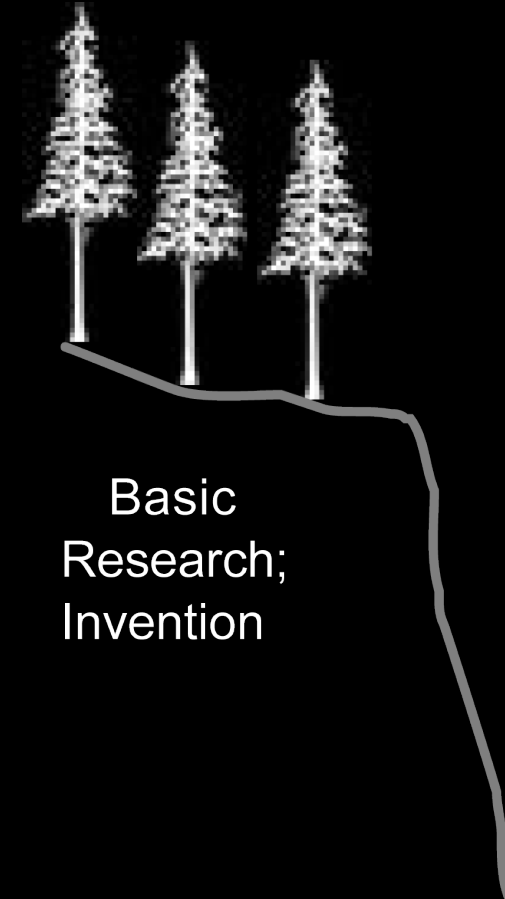


+ 6 site leads

106 grad students



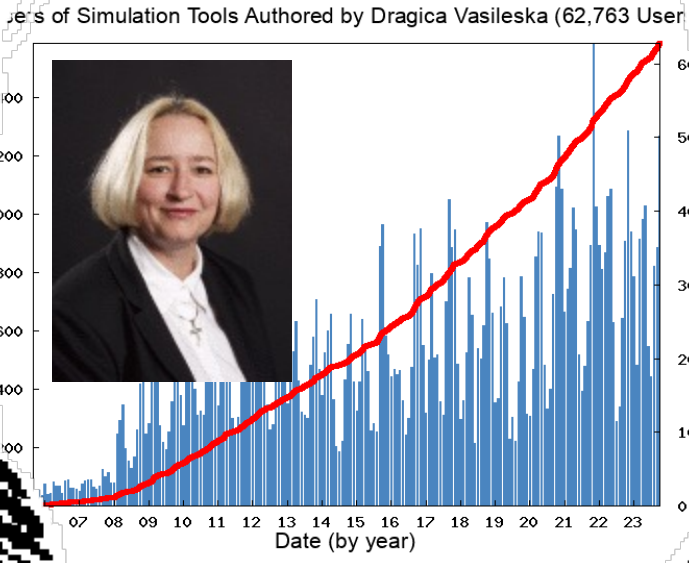
2011 Data



# Faculty Incentives

Tool Usage  $\approx$  reading papers

Dragica Vasileska

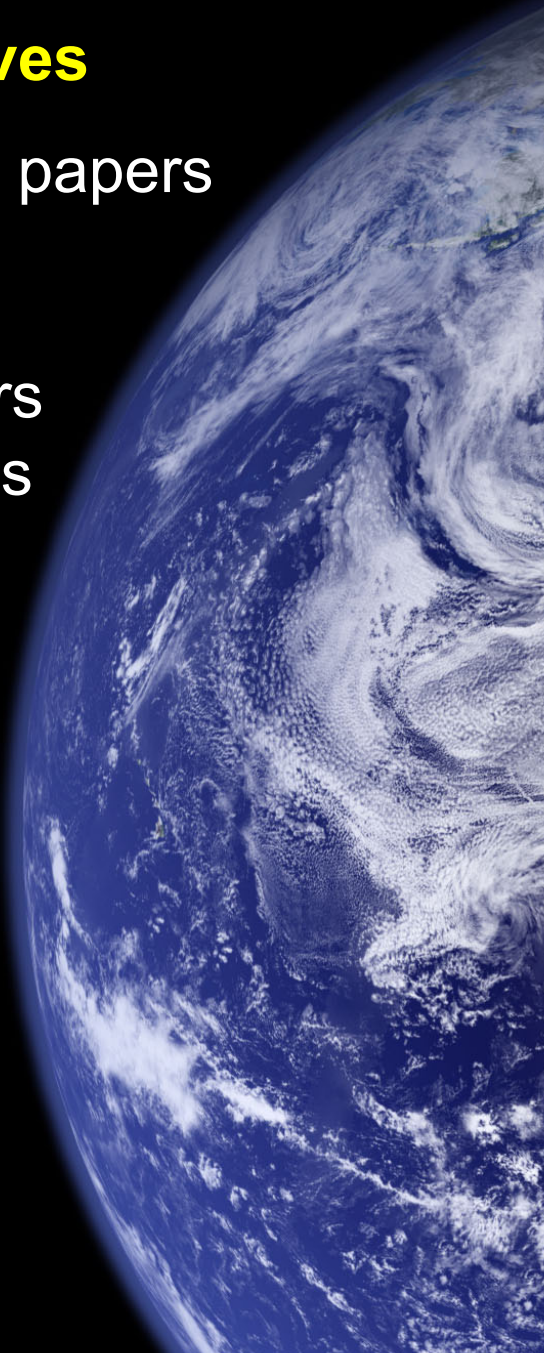


**20 tools**

→ 62,763 users

→ 192 citations

Proof of Impact!  
Great in Proposals!





# Next Generation Faculty:

Usage at SIUC

1/2006 1/2007 1/2008 1/2009 1/2010

Post Doc Faculty at SIUC

Purdue

- Infused nanoHUB into existing classes
- Built a new nanoelectronics curriculum
- Used nanoHUB for research

Shaikh Ahmed

of Simulation Tools Authored by Shaikh S. Ahmed (27,947 Users)

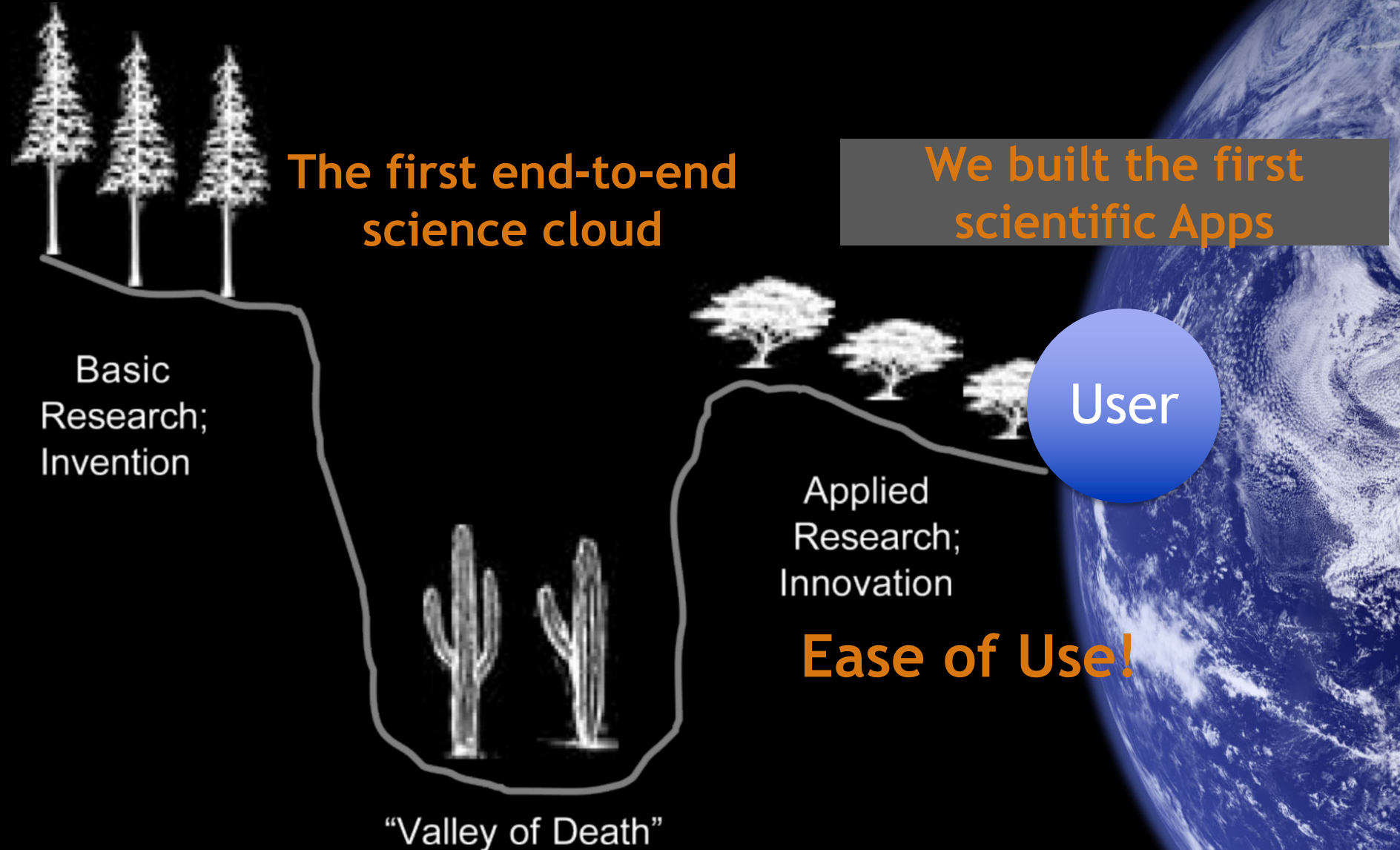


27,947 users  
14 tools

WEB OF SCIENCE

Early Tenure Promotion

# 3: Technology for Dissemination



# 3: Technology for Dissemination

“simple and utterly dependable”  
Less than 20 hours downtime  
last year!

The first end-to-end  
science cloud

We built the first  
scientific Apps



Basic  
Research;  
Invention



Applied  
Research;  
Innovation



\$2M/year  
operation and  
bridge building

Ease of Use!

“Valley of Death”



# 4: Tech Transfer Processes

~~“dedicated technical site leads”~~

~~Consultants -~~

Support

Geek



User



Basic Research; Invention



site leads

Content Creation and Support

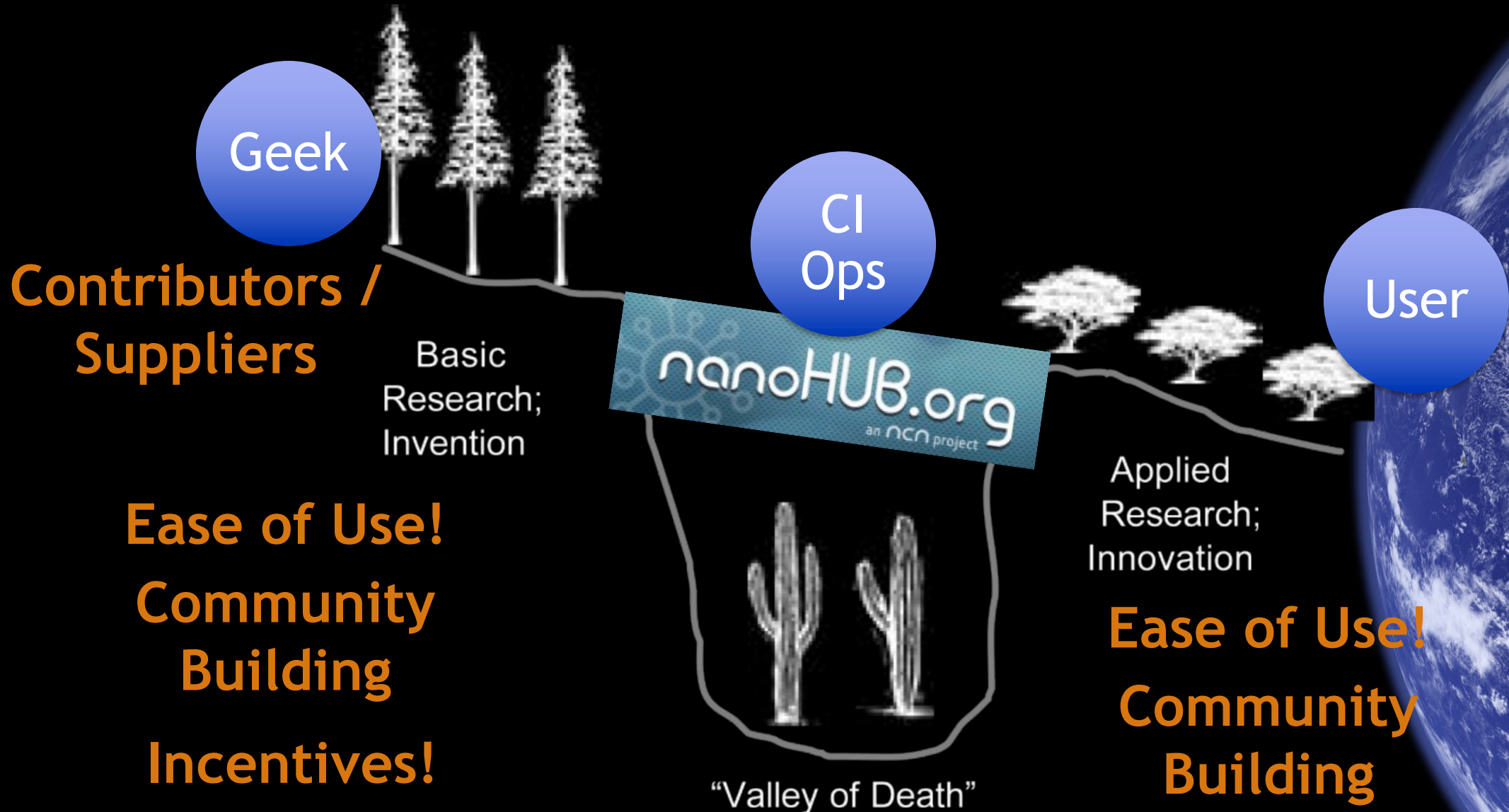
~~\$2.2M~~

Significant portion of budget

Applied Research; Innovation

“Valley of Death”

# 5: Understanding Stakeholders



# 6: Open Assessment / Incentives

“gather, understand, disseminate stats”

Access,  
Use,  
Impact



Basic  
Research;  
Invention



“Valley of Death”

Applied  
Research;  
Innovation



Users of Simulation Tools Authored by Dragica Vasileska (7,835 Users)

Year	Cumulative Users
2006	0
2007	~100
2008	~200
2009	~400
2010	~7000

# 7: Business Model

**Research:  
Sustained Academic Funding**

**Product Development:  
Real Business Plans**



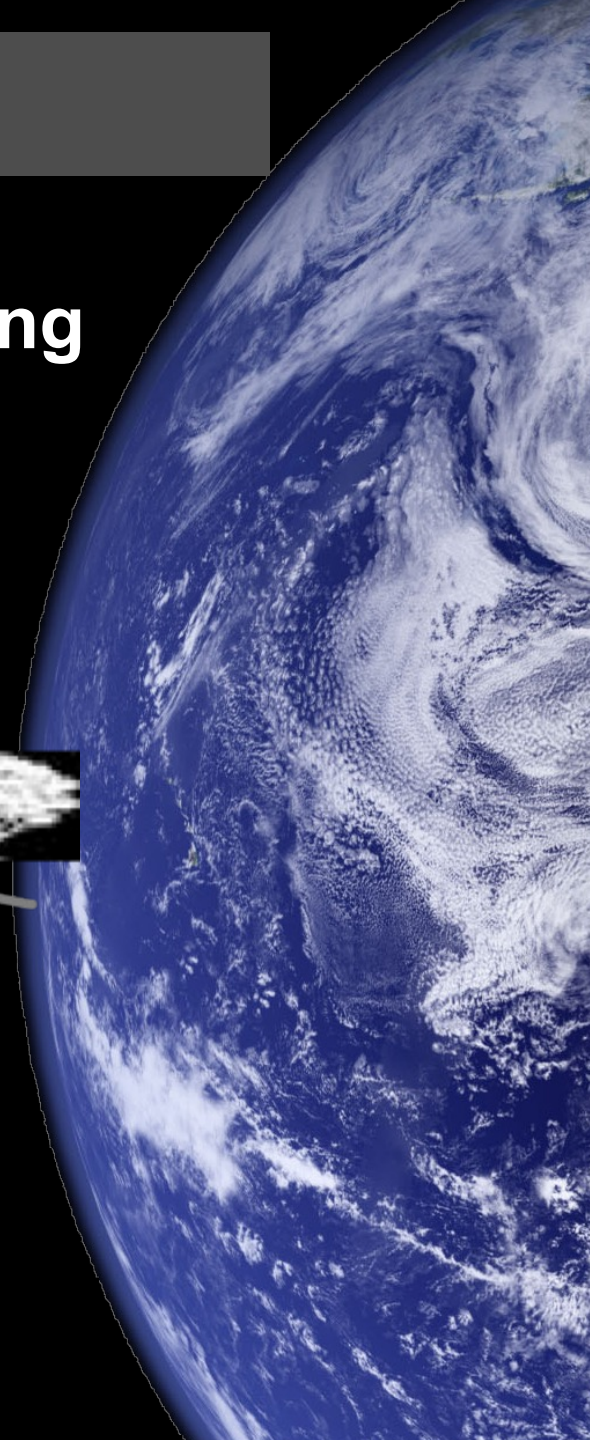
Basic  
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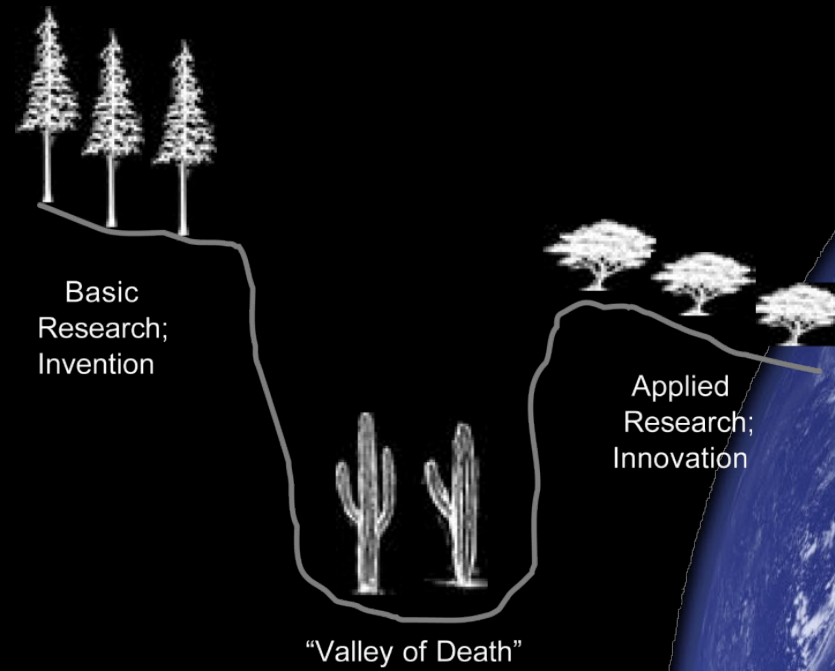


“Valley of Death”



# 7 Criteria for Successful Science Gateways

- 1: Outstanding Science / Quality
- 2: Commitment to Dissemination
- 3: Technology for Dissemination
- 4: Tech Transfer Processes
- 5: Understanding Stakeholders
- 6: Open Assessment / Incentives
- 7: Business Model



**Just hosting expert  
software is not enough!**



12,000 students using tools each year in classes!

16 % at MSIs

Just hosting expert software is not enough!

The future of chip design and manufacturing is here

Public on Ratemyprofessor

....I'm in the military so I have weird, long work hours

... group projects--which were HIGHLY valuable, and are why the class has been so meaningful to me, 10/10 would recommend!

We work with partners ...



We re-envision access to tools...

- We mimic industrial implementations!
- Across the whole stack
- Apps for freshmen and
- Scripts for optimization
- Lectures and tutorials

for everyone

From class to Lab to Fab

Thank You!